1.8V, 2G/4G-bit NAND Flash Memory

MX30UFxG26(28)AB

Contents

1. FEATURES

- 2G-bit/4G-bit SLC NAND Flash
  - Bus: x8, x16
  - Page size: (2048+112) byte for x8 bus, (1024+56) word for x16 bus
  - Block size: (128K+7K) byte for x8 bus, (64K+3.5K) word for x16 bus
  - Plane size:
    1024-block/plane x 2 for 2Gb
    2048-block/plane x 2 for 4Gb
- **ONFI 1.0 compliant**
- **Multiplexed Command/Address/Data**
- **User Redundancy**
  - 112-byte attached to each page
- **Fast Read Access**
  - Latency of array to register: 25us
  - Sequential read: 25ns
- **Cache Read Support**
- **Page Program Operation**
  - Page program time: 320us (typ.)
- **Cache Program Support**
- **Block Erase Operation**
  - Block erase time: 1ms (typ.)
- **Single Voltage Operation:**
  - VCC: 1.7 ~ 1.95V
- **Low Power Dissipation**
  - Max. 30mA (1.8V)
    Active current (Read/Program/Erase)
- **Sleep Mode**
  - 50uA (Max) standby current
- **Hardware Data Protection:** WP# pin
- **Device Status Indicators**
  - Ready/Busy (R/B#) pin
  - Status Register
- **Chip Enable Don't Care**
  - Simplify System Interface
- **Unique ID Read support (ONFI)**
- **Secure OTP support**
- **Electronic Signature (5 Cycles)**
- **High Reliability**
  - Endurance: typical 100K cycles (with 8-bit ECC per (512+28) Byte)
  - Data Retention: 10 years
- **Wide Temperature Operating Range**
  -40°C to +85°C
- **Package:**
  1) 48-TSOP(I) (12mm x 20mm)
  2) 63-ball 9mmx11mm VFBGA
  All packaged devices are RoHS Compliant and Halogen-free.

2. GENERAL DESCRIPTIONS

The MX30UFxG26(28)AB are 2Gb to 4Gb SLC NAND Flash memory devices. Its standard NAND Flash features and reliable quality of typical P/E cycles 100K (with ECC), which make it most suitable for embedded system code and data storage.

The product family requires 8-bit ECC per 540B.

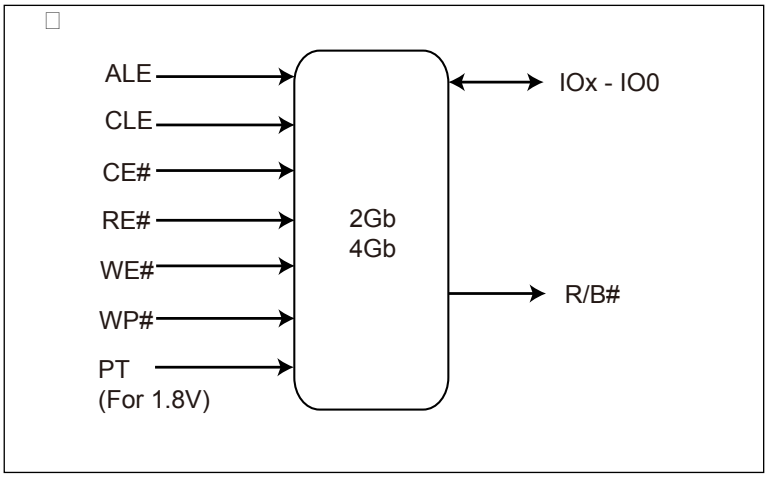
This device is typically accessed in pages of 2,160 bytes (x8) or 1080 words (x16), both for read and for program operations.

The device's array is organized as thousands of blocks, which is composed by 64 pages of (1024+32) words in two NAND strings structure with 32 serial connected cells in each string. Each page has an additional 56 words for ECC and other purposes. The device has an on-chip buffer of 2160 bytes or 1080 words (x16) for data load and access.

The Cache Read Operation of the MX30UFxG26(28)AB enables first-byte read-access latency of 25us and sequential read of 25ns and the latency time of next sequential page will be shorten from tR to tRCBSY.

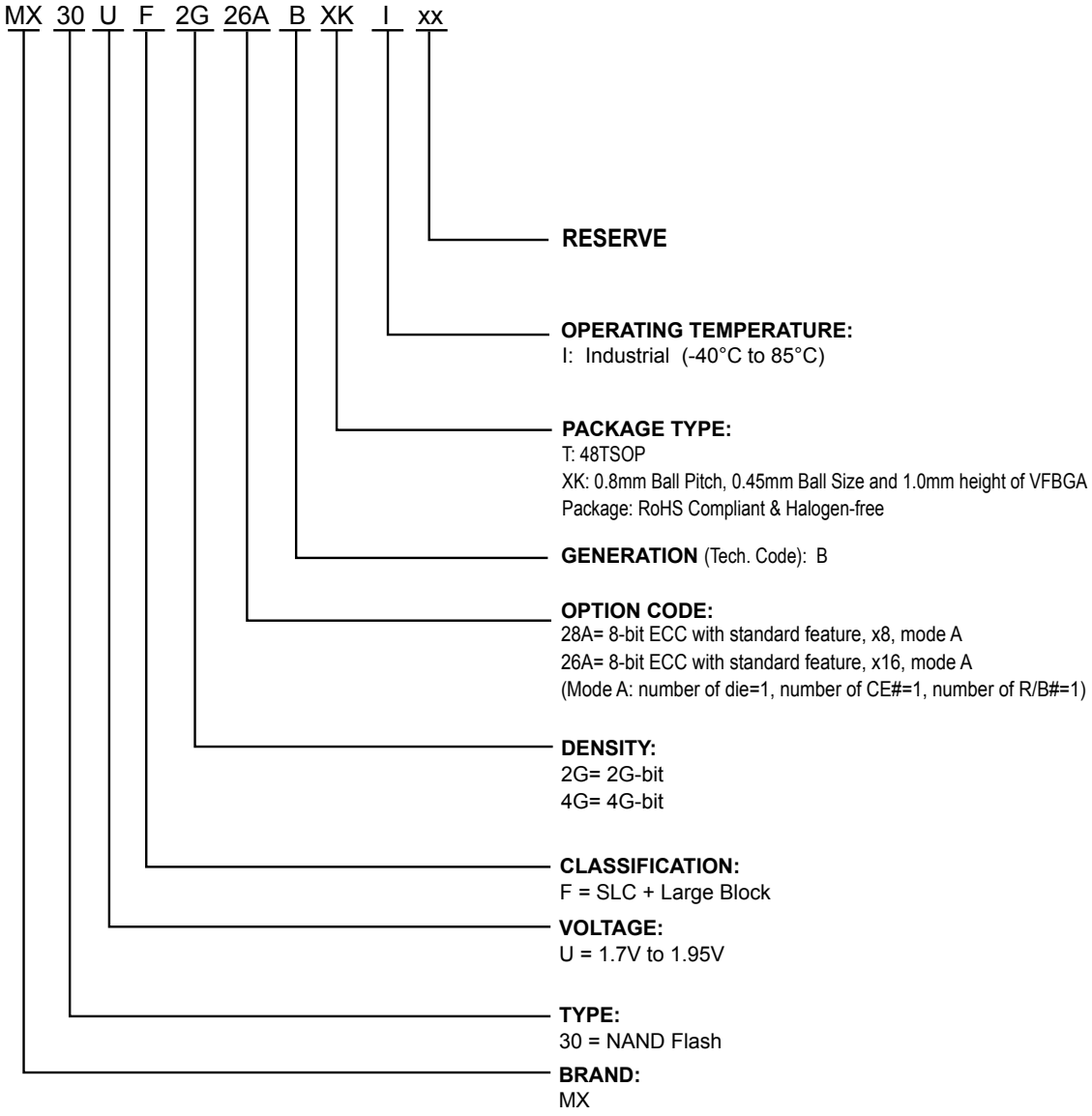
The MX30UFxG26(28)AB power consumption is 30mA during all modes of operations (Read/Program/Erase), and 50uA in standby mode.

Figure 1. Logic Diagram



2-1. ORDERING INFORMATION

Part Name Description

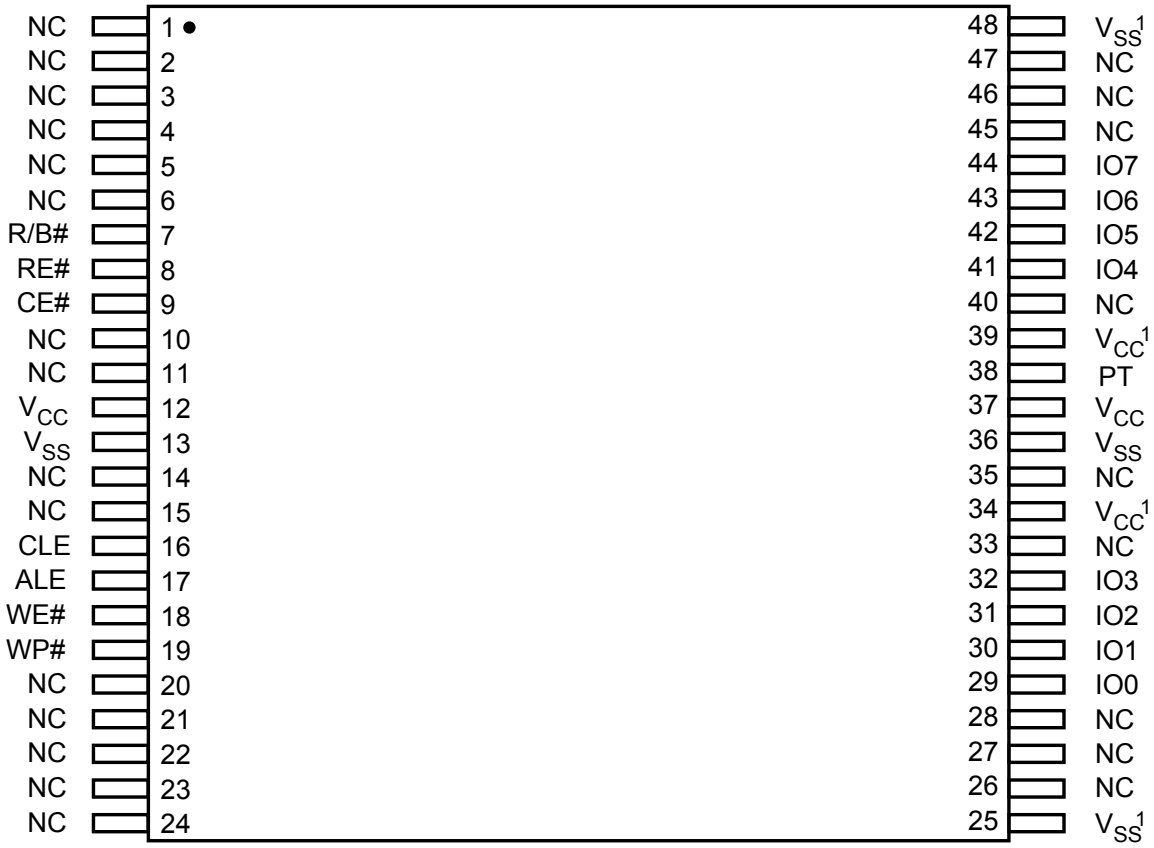


Please contact our regional sales for the latest product selection and available form factors.

Part Number	Density	Organization	VCC Range	Package	Temperature Grade
MX30UF2G28AB-XKI	2Gb	x8	1.8V	63-VFBGA	Industrial
MX30UF2G26AB-XKI	2Gb	x16	1.8V	63-VFBGA	Industrial
MX30UF2G28AB-TI	2Gb	x8	1.8V	48-TSOP	Industrial
MX30UF4G28AB-XKI	4Gb	x8	1.8V	63-VFBGA	Industrial
MX30UF4G26AB-XKI	4Gb	x16	1.8V	63-VFBGA	Industrial
MX30UF4G28AB-TI	4Gb	x8	1.8V	48-TSOP	Industrial

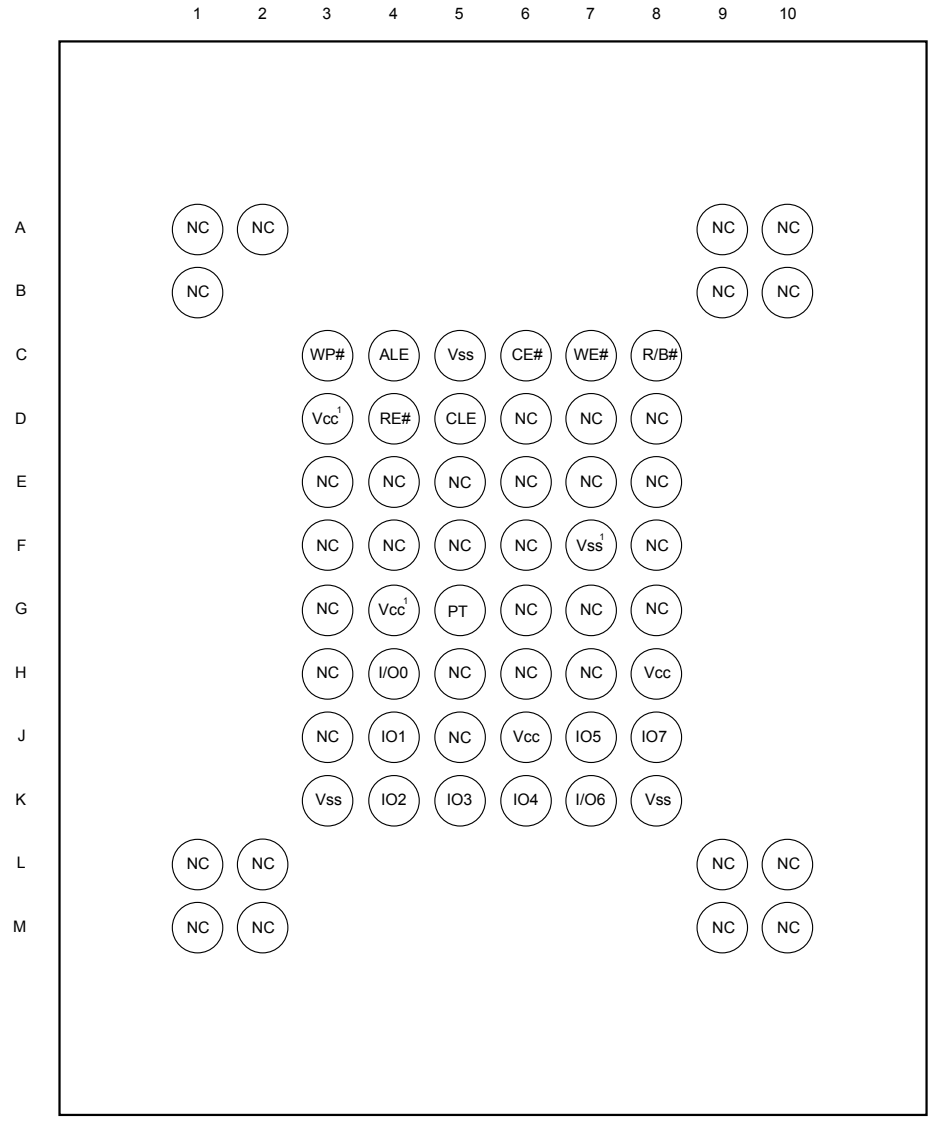
3. PIN CONFIGURATIONS

48-TSOP



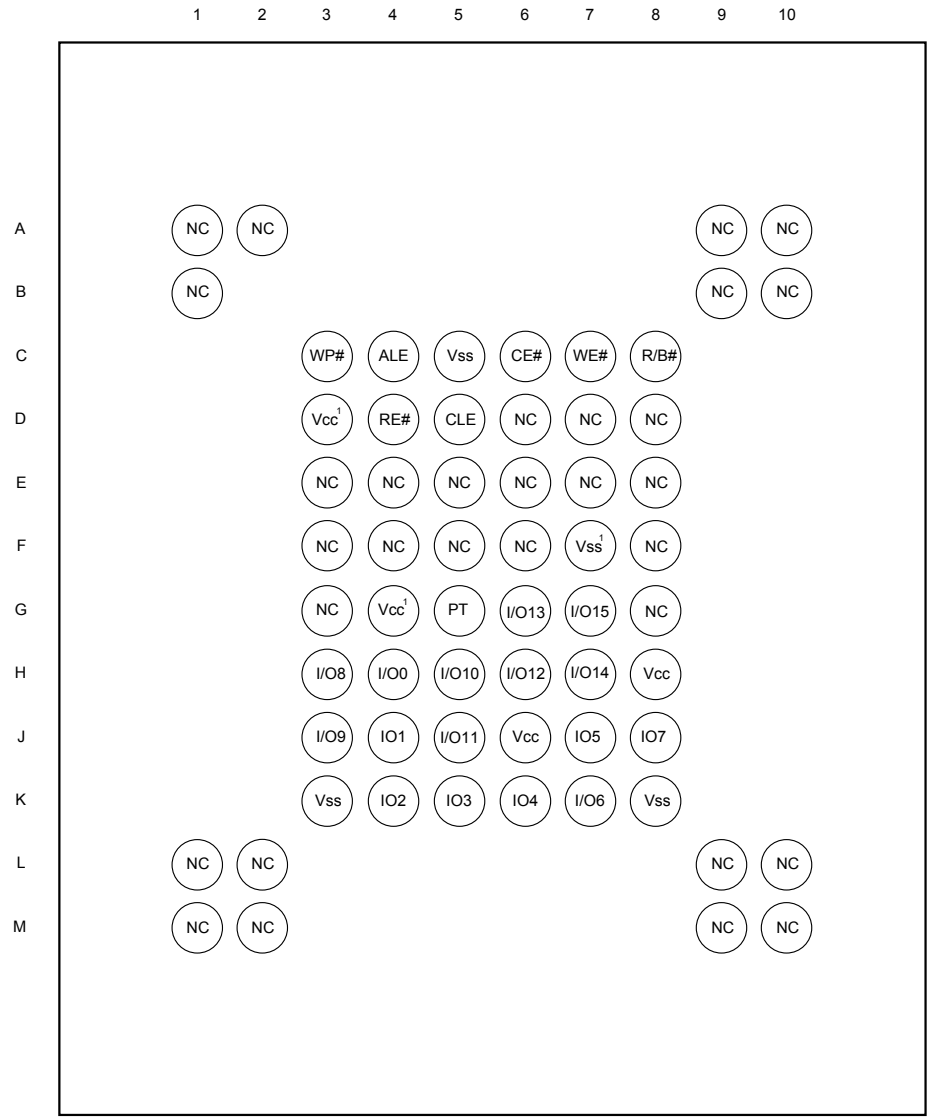
Note 1. *These pins might not be connected internally. However, it is recommended to connect these pins to power(or ground) as designated for ONFI compatibility.*

63-ball 9mmx11mm VFBGA (x8)



Note 1. *These pins might not be connected internally; however, it is recommended to connect these pins to power (or ground) as designated for ONFI compatibility.*

63-ball 9mmx11mm VFBGA (x16)



Note 1. *These pins might not be connected internally; however, it is recommended to connect these pins to power (or ground) as designated for ONFI compatibility.*

3-1. PIN DESCRIPTIONS

SYMBOL	PIN NAME
IOx - IO0	Data I/O port: IO7-IO0 for x8 device, IO15-IO0 for x16 device
CE#	Chip Enable (Active Low)
RE#	Read Enable (Active Low)
WE#	Write Enable (Active Low)
CLE	Command Latch Enable
ALE	Address Latch Enable
WP#	Write Protect (Active Low)
R/B#	Ready/Busy (Open Drain)
PT	Protection (Active High) for entire chip protection. A weak pull-down internally
VSS	Ground
VCC	Power Supply for Device Operation
NC	Not Connected Internally

PIN FUNCTIONS

The MX30UFxG26(28)AB device is a sequential access memory that utilizes multiplexing input of Command/Address/Data.

I/O PORT: IOx - IO0

The IOx to IO0 pins are for address/command input and data output to/from the device. IO7-IO0 pins are for x8 device, IO15-IO0 pins are for x16 device.

CHIP ENABLE: CE#

The device goes into low-power Standby Mode when CE# goes high during a read operation and not at busy stage.

The CE# goes low to enable the device to be ready for standard operation. When the CE# goes high, the device is deselected. However, when the device is at busy stage, the device will not go to standby mode when CE# pin goes high.

READ ENABLE: RE#

The RE# (Read Enable) allows the data to be output by a tREA time after the falling edge of RE#. The internal address counter is automatically increased by one at the falling edge of RE#.

WRITE ENABLE: WE#

When the WE# goes low, the address/data/command are latched at the rising edge of WE#.

COMMAND LATCH ENABLE: CLE

The CLE controls the command input. When the CLE goes high, the command data is latched at the rising edge of the WE#.

ADDRESS LATCH ENABLE: ALE

The ALE controls the address input. When the ALE goes high, the address is latched at the rising edge of WE#.

WRITE PROTECT: WP#

The WP# signal keeps low and then the memory will not accept the program/erase operation. It is recommended to keep WP# pin low during power on/off sequence. Please refer to the waveform of "Power On/Off Sequence".

READY/Busy: R/B#

The R/B# is an open-drain output pin. The R/B# outputs the ready/busy status of read/program/erase operation of the device. When the R/B# is at low, the device is busy for read or program or erase operation. When the R/B# is at high, the read/program/erase operation is finished.

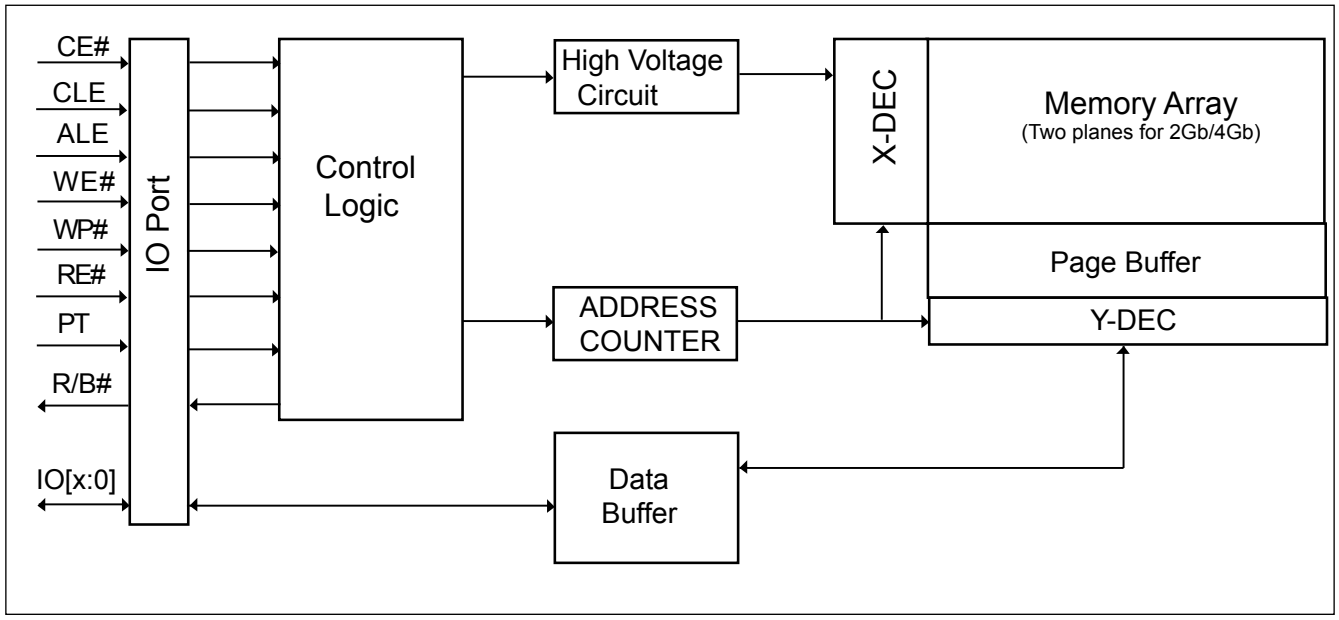
Please refer to **Section 9-1** for details.

PROTECTION: PT

The PT pin is the hardware method to protect the whole chip from program/erase operation. When the PT pin is at high at power-on, the whole chip is protected even the WP# is at high; the un-protect command and procedure is necessary before any program/erase operation. When the PT pin is connected to low or floating, the Protection function is disabled.

Please refer to **Section - Block Protection** for details.

4. BLOCK DIAGRAM



5. SCHEMATIC CELL LAYOUT AND ADDRESS ASSIGNMENT

The device is divided into two planes for 2Gb and 4Gb, which is composed by 64 pages of (2,048+112)-byte in two NAND strings structure with 32 serial connected cells in each string. Each page has an additional 112 bytes for ECC and other purposes. The device has an on-chip buffer of 2,160 bytes for data load and access. Each 2K-Byte page has the two area, one is the main area which is 2048-bytes and the other is spare area which is 112-byte.

There are five (for 2Gb/4Gb) address cycles for the address allocation, please refer to the lable below.

Table 1-1. Address Allocation (for x8): MX30UFxG28AB

Addresses	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Column address - 1st cycle	A7	A6	A5	A4	A3	A2	A1	A0
Column address - 2nd cycle	L	L	L	L	A11	A10	A9	A8
Row address - 3rd cycle	A19	A18[1]	A17	A16	A15	A14	A13	A12
Row address - 4th cycle	A27	A26	A25	A24	A23	A22	A21	A20
Row address - 5th cycle	L	L	L	L	L	L	A29[2]	A28

Notes:

1. *A18 is the plane selection for 2Gb/4Gb.*
2. *A28 is for 2Gb and 4Gb.*
3. *A29 is for 4Gb, "L" (Low) for 2Gb.*
4. *The 5th cycle is for the 2Gb/4Gb.*

Table 1-2. Address Allocation (for x16): MX30UFxG26AB

Addresses	IO15-IO8	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Column address - 1st cycle	L	A7	A6	A5	A4	A3	A2	A1	A0
Column address - 2nd cycle	L	L	L	L	L	L	A10	A9	A8
Row address - 3rd cycle	L	A18	A17[1]	A16	A15	A14	A13	A12	A11
Row address - 4th cycle	L	A26	A25	A24	A23	A22	A21	A20	A19
Row address - 5th cycle[4]	L	L	L	L	L	L	L	A28[3]	A27[2]

Notes:

1. *A17 is the plane selection for 2Gb/4Gb.*
2. *A27 is for 2Gb and 4Gb.*
3. *A28 is for 4Gb, "L" (Low) for 2Gb.*
4. *The 5th cycle is for the 2Gb/ 4Gb.*

6. DEVICE OPERATIONS

6-1. Address Input/Command Input/Data Input

Address input bus operation is for address input to select the memory address. The command input bus operation is for giving command to the memory. The data input bus is for data input to the memory device.

Figure 2. AC Waveforms for Command / Address / Data Latch Timing

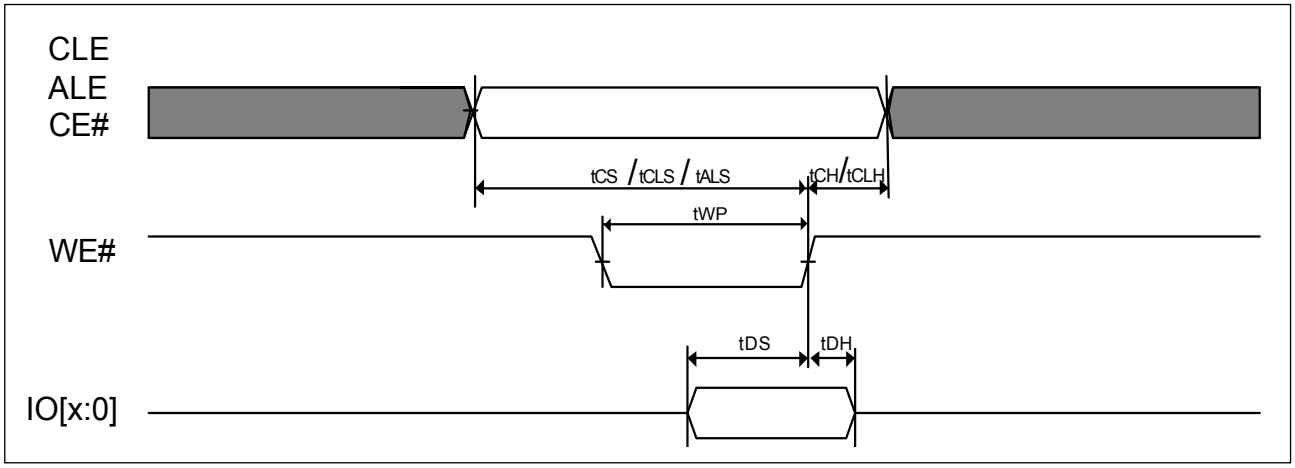


Figure 3. AC Waveforms for Address Input Cycle

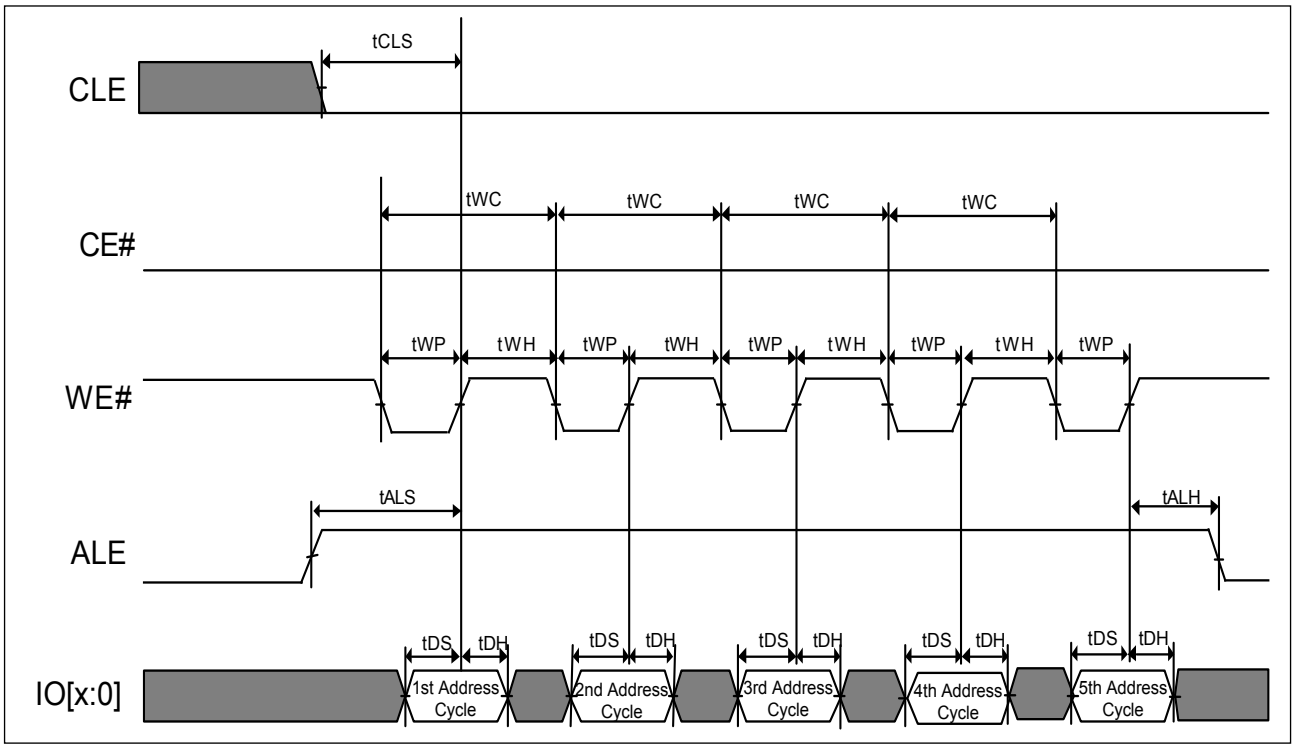


Figure 4. AC Waveforms for Command Input Cycle

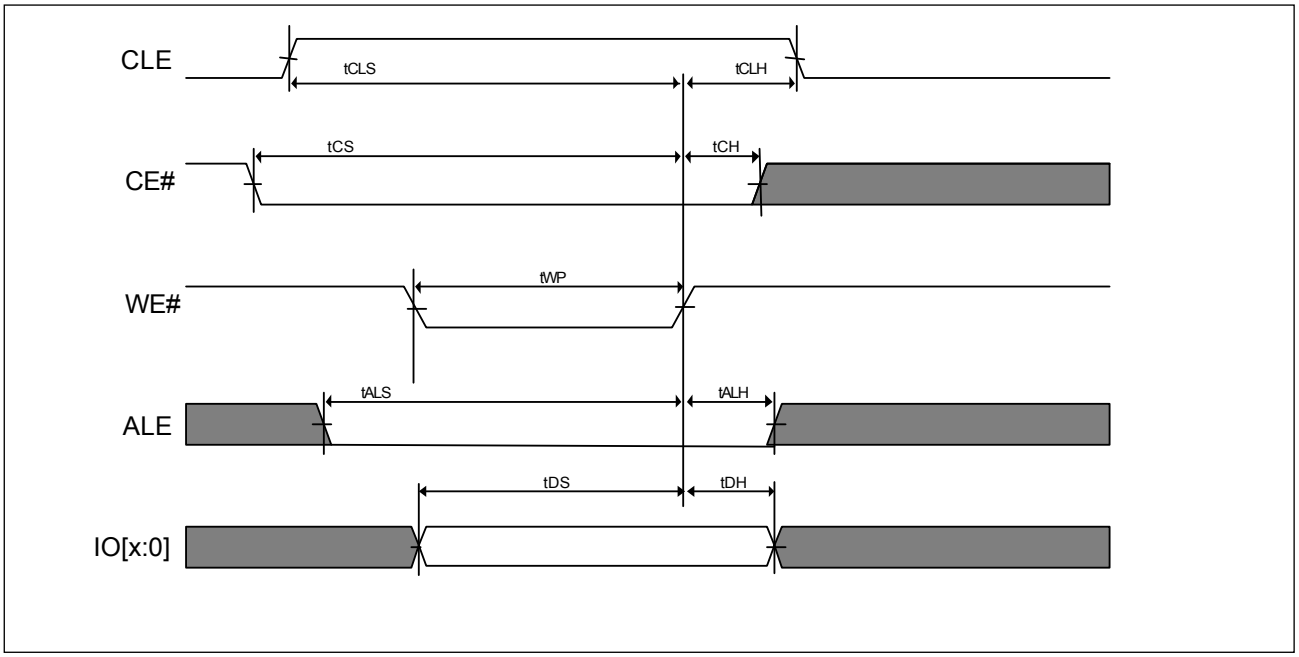
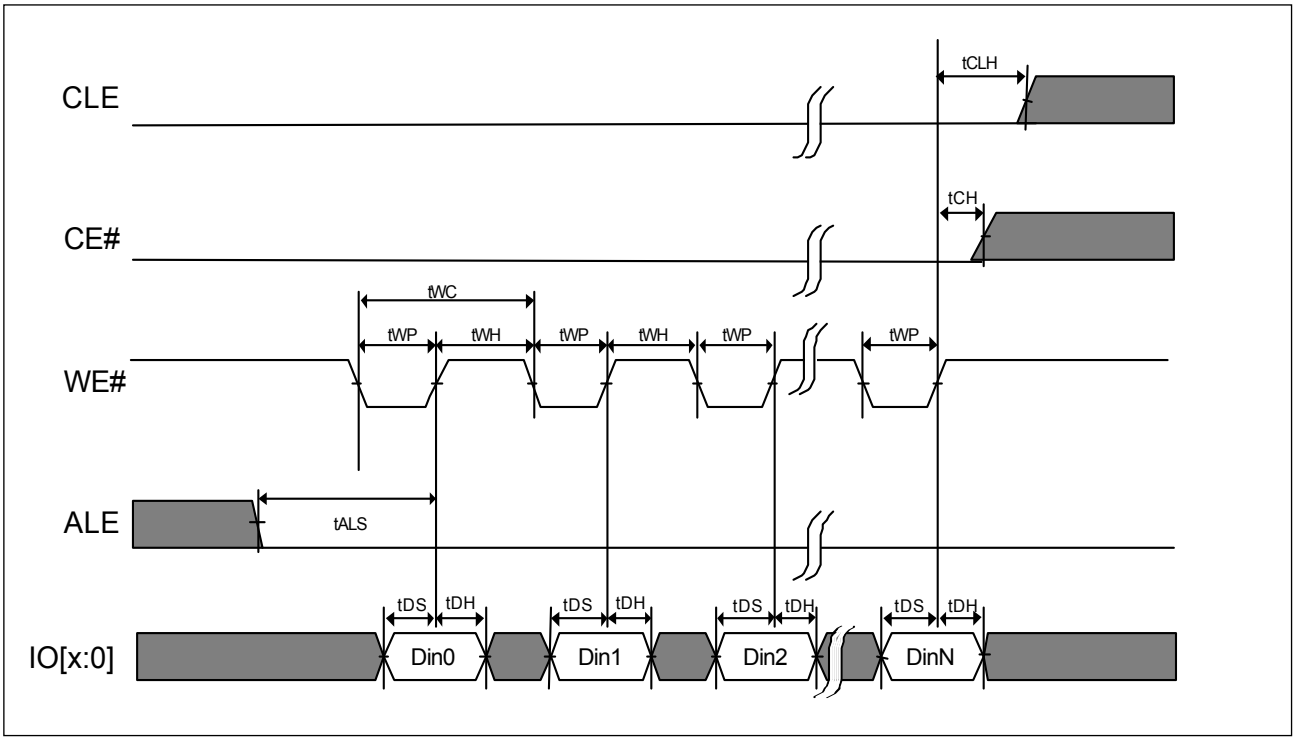


Figure 5. AC Waveforms for Data Input Cycle



6-2. Page Read

The MX30UFxG26(28)AB array is accessed in Page of 2160 bytes or 1,080 words. External reads begins after the R/B# pin goes to READY.

The Read operation may also be initiated by writing the 00h command and giving the address (column and row address) and being confirmed by the 30h command, the device begins the internal read operation and the chip enters busy state. The data can be read out in sequence after the chip is ready. Refer to the waveform for Read Operation as below.

If the host side uses a sequential access time (tRC) of less than 30ns, the data can be latched on the next falling edge of RE# as the waveform of EDO mode (**Figure 9-2**).

To access the data in the same page randomly, a command of 05h may be written and only column address following and then confirmed by E0h command.

Figure 6. AC Waveforms for Read Cycle

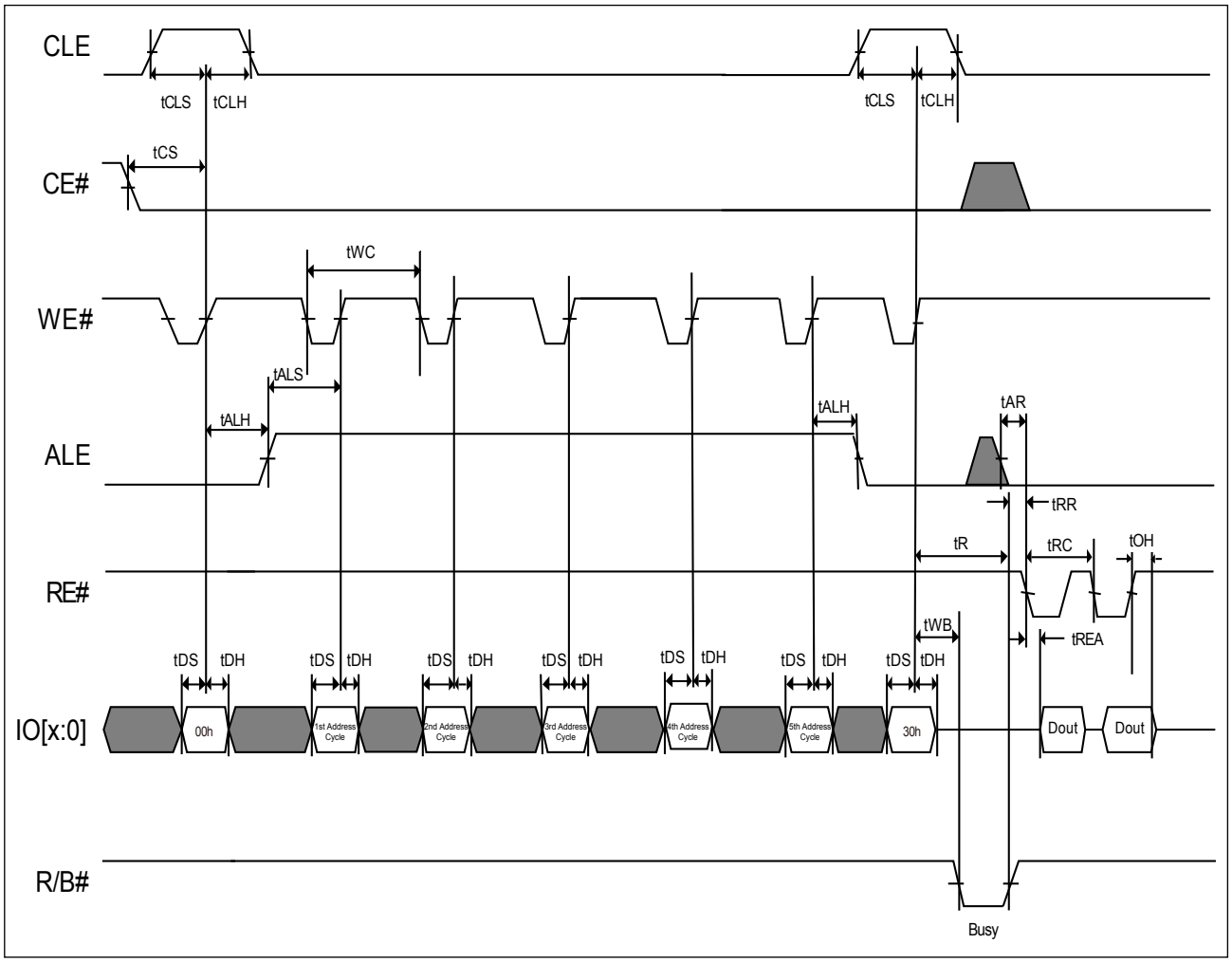


Figure 7. AC Waveforms for Read Operation (Intercepted by CE#)

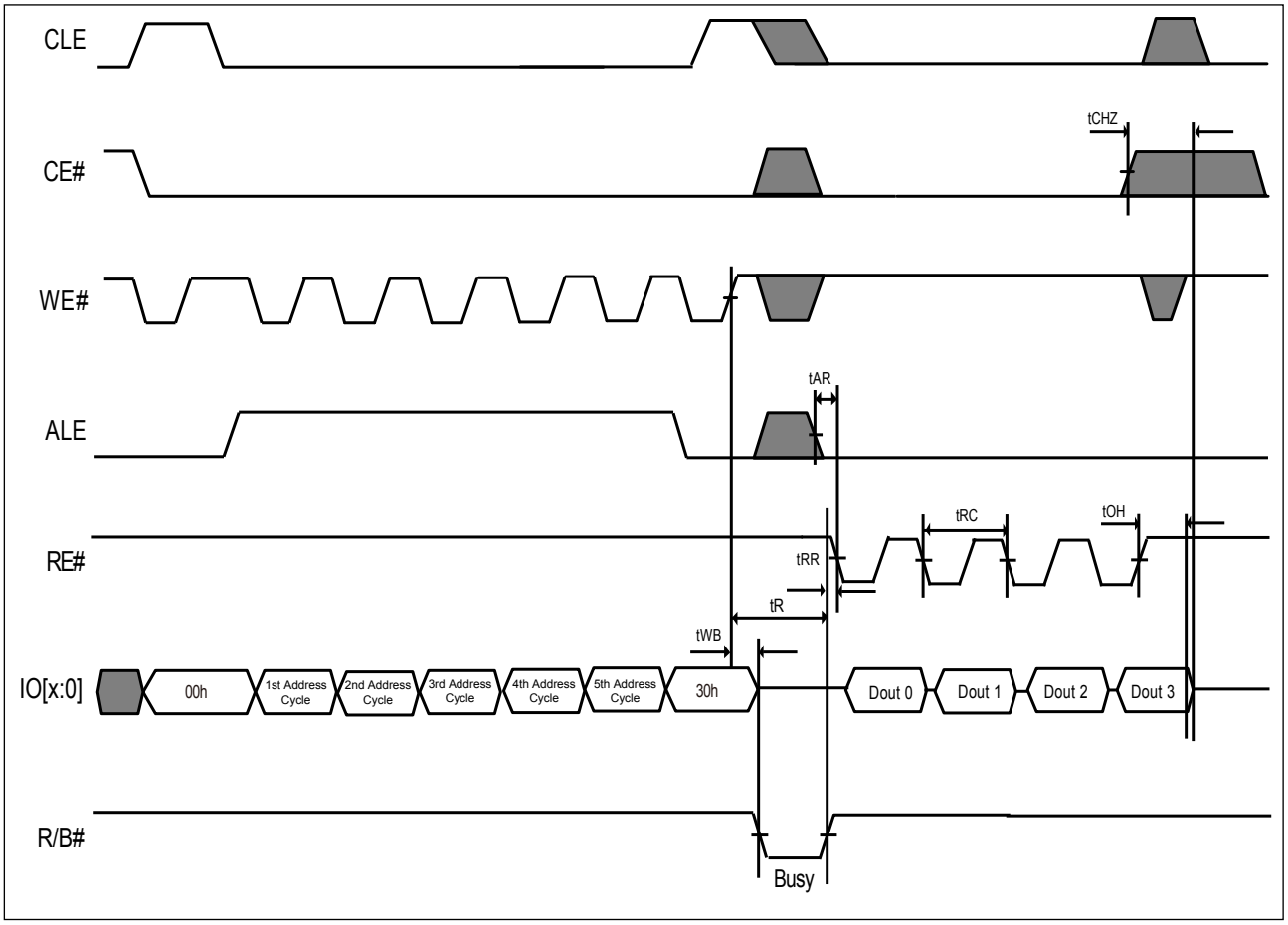
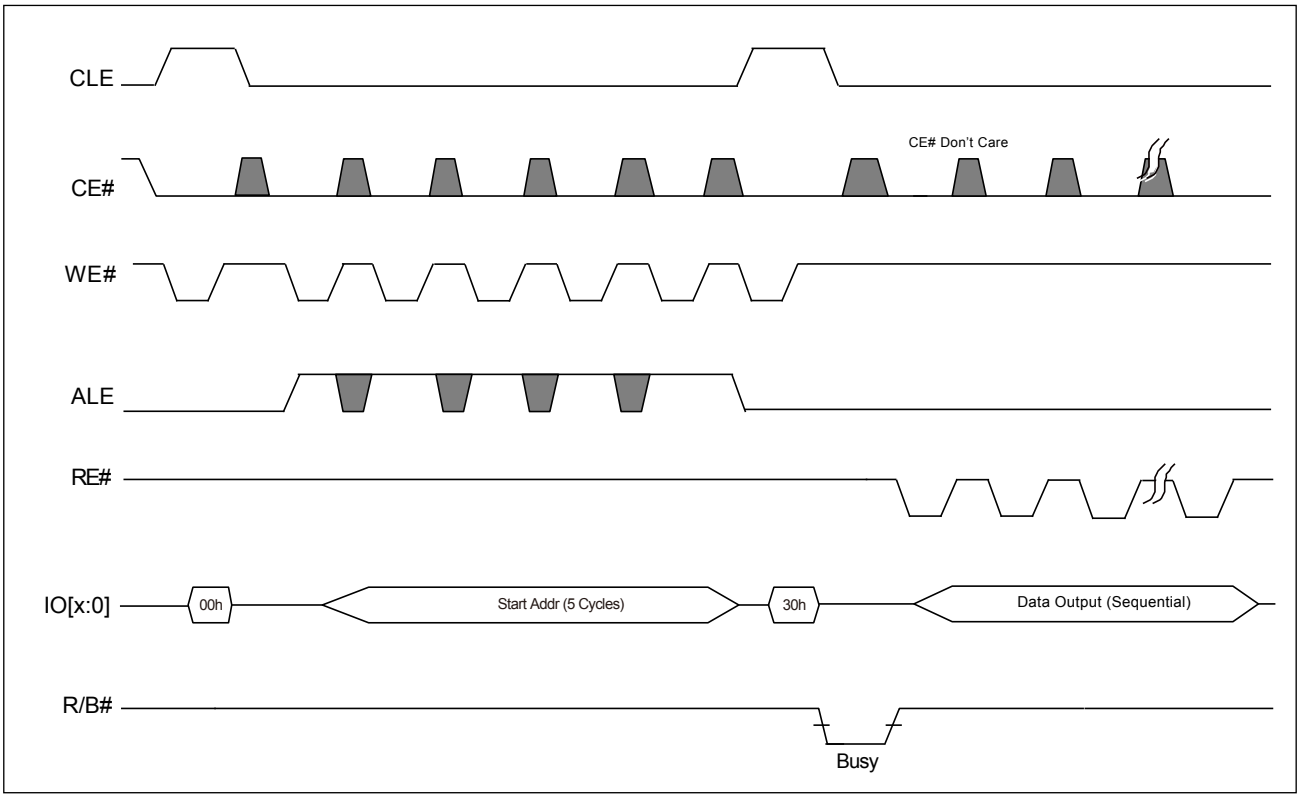


Figure 8. AC Waveforms for Read Operation (with CE# Don't Care)



Note: *The CE# "Don't Care" feature may simplify the system interface, which allows controller to directly download the code from flash device, and the CE# transitions will not stop the read operation during the latency time.*

Figure 9-1. AC Waveforms for Sequential Data Out Cycle (After Read)

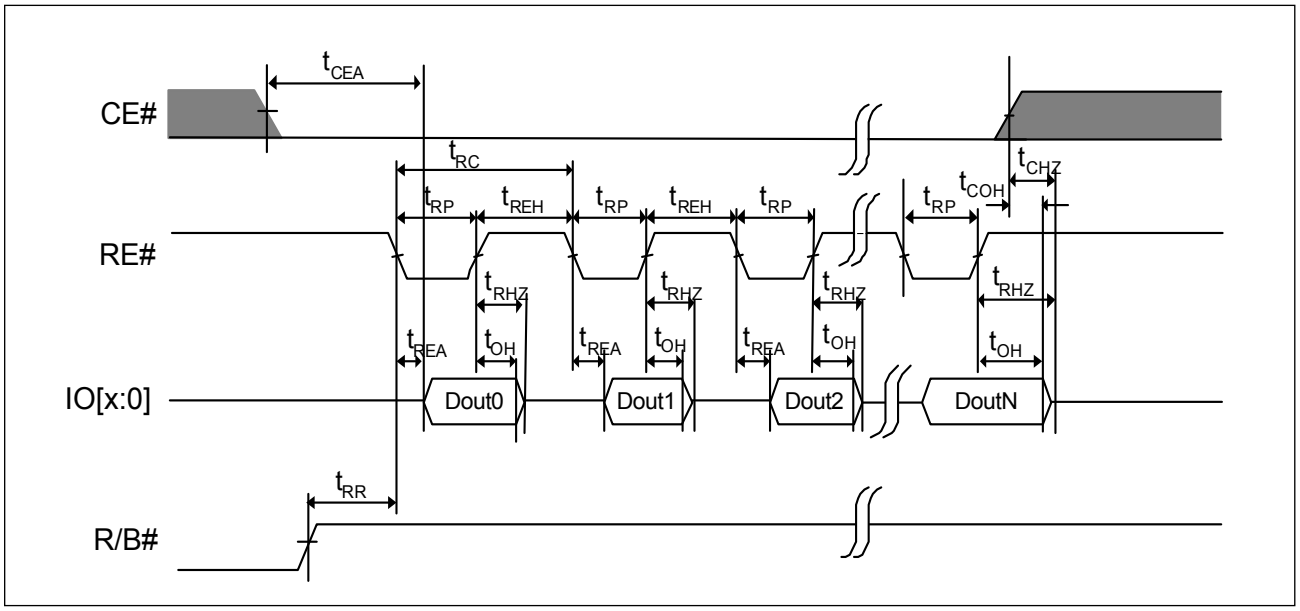


Figure 9-2. AC Waveforms for Sequential Data Out Cycle (After Read) - EDO Mode

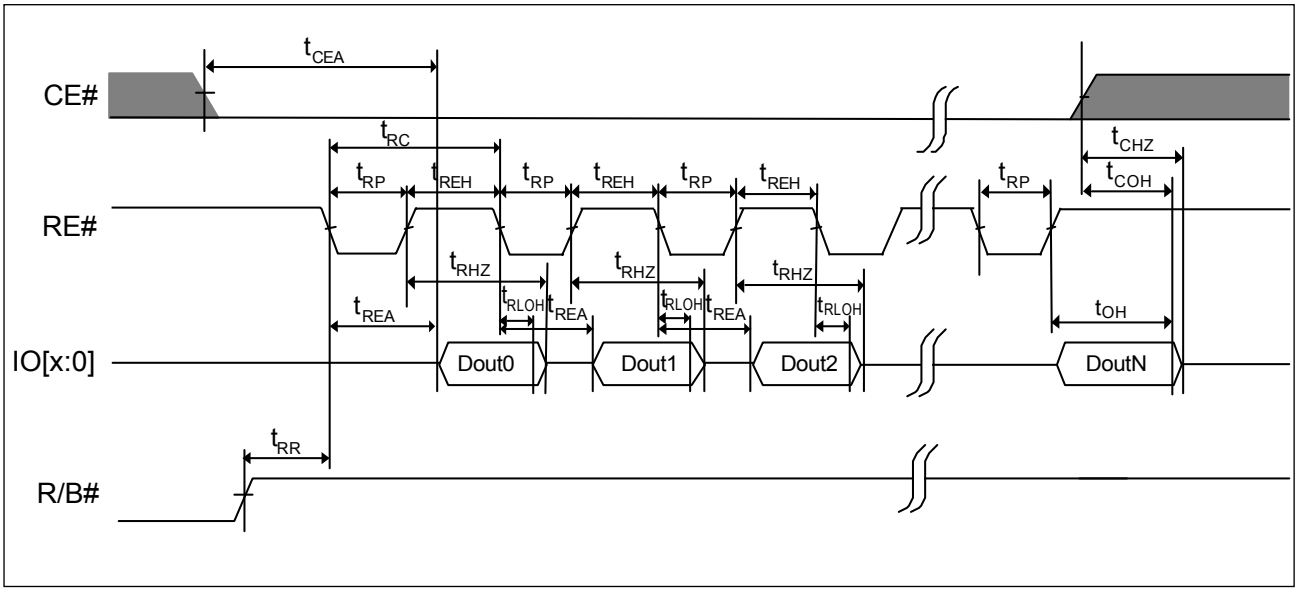
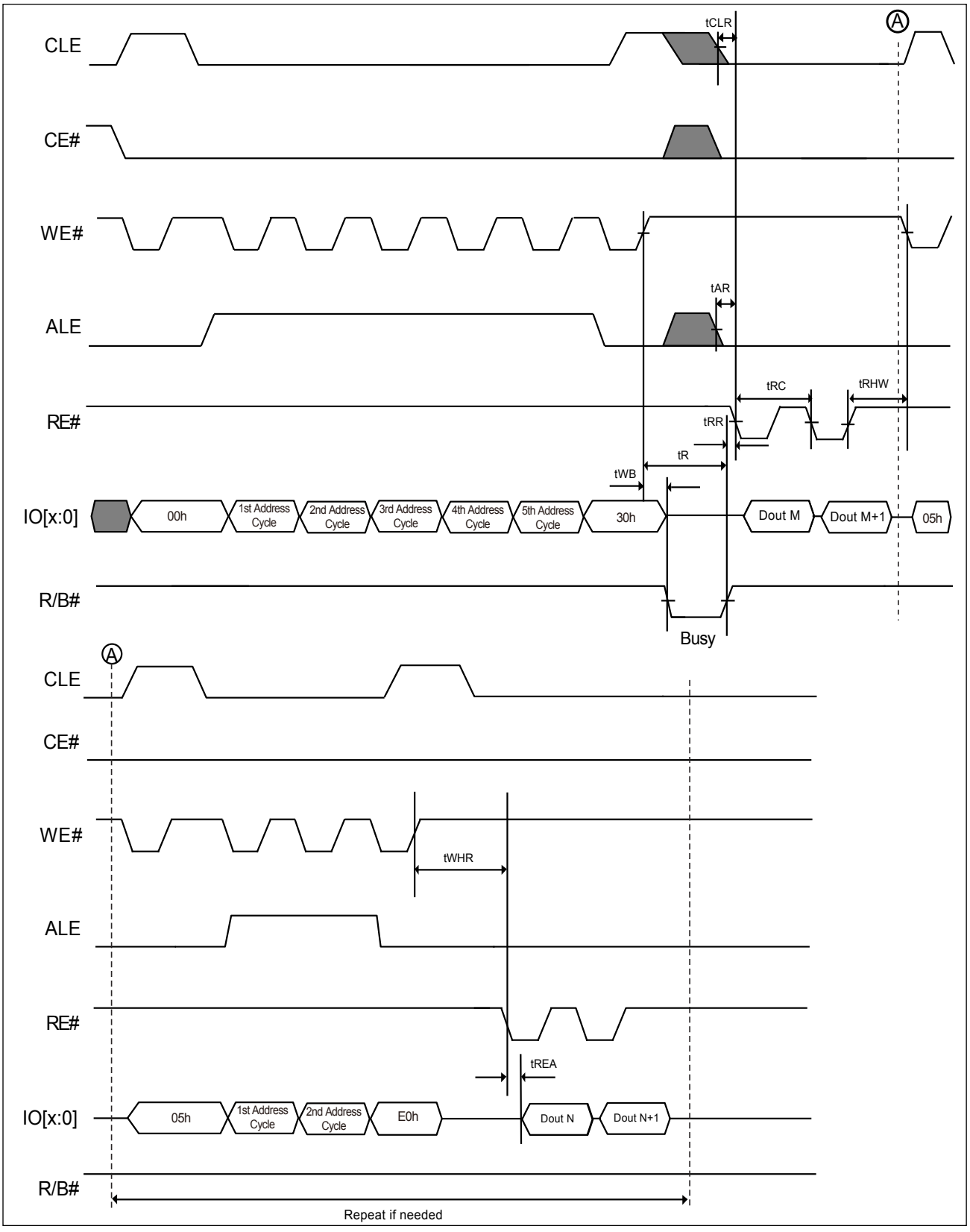


Figure 10. AC Waveforms for Random Data Output



6-3. Cache Read Sequential

The cache read sequential operation is for throughput enhancement by using the internal cache buffer. It allows the consecutive pages to be read-out without giving next page address, which reduces the latency time from tR to tRCBSY between pages or blocks. While the data is read out on one page, the data of next page can be read into the cache buffer.

After writing the 00h command, the column and row address should be given for the start page selection, and followed by the 30h command for address confirmation. After that, the CACHE READ operation starts after a latency time tR and following a 31h command with the latency time of tRCBSY, the data can be read-out sequentially from 1st column address (A[11:0]=00h) without giving next page address input. The 31h command is necessary to confirm the next cache read sequential operation and followed by a tRCBSY latency time before next page data is necessary. The CACHE READ SEQUENTIAL command is also valid for the consecutive page cross block.

The random data out (05h-E0h) command set is available to change the column address of the current page data in the cache register.

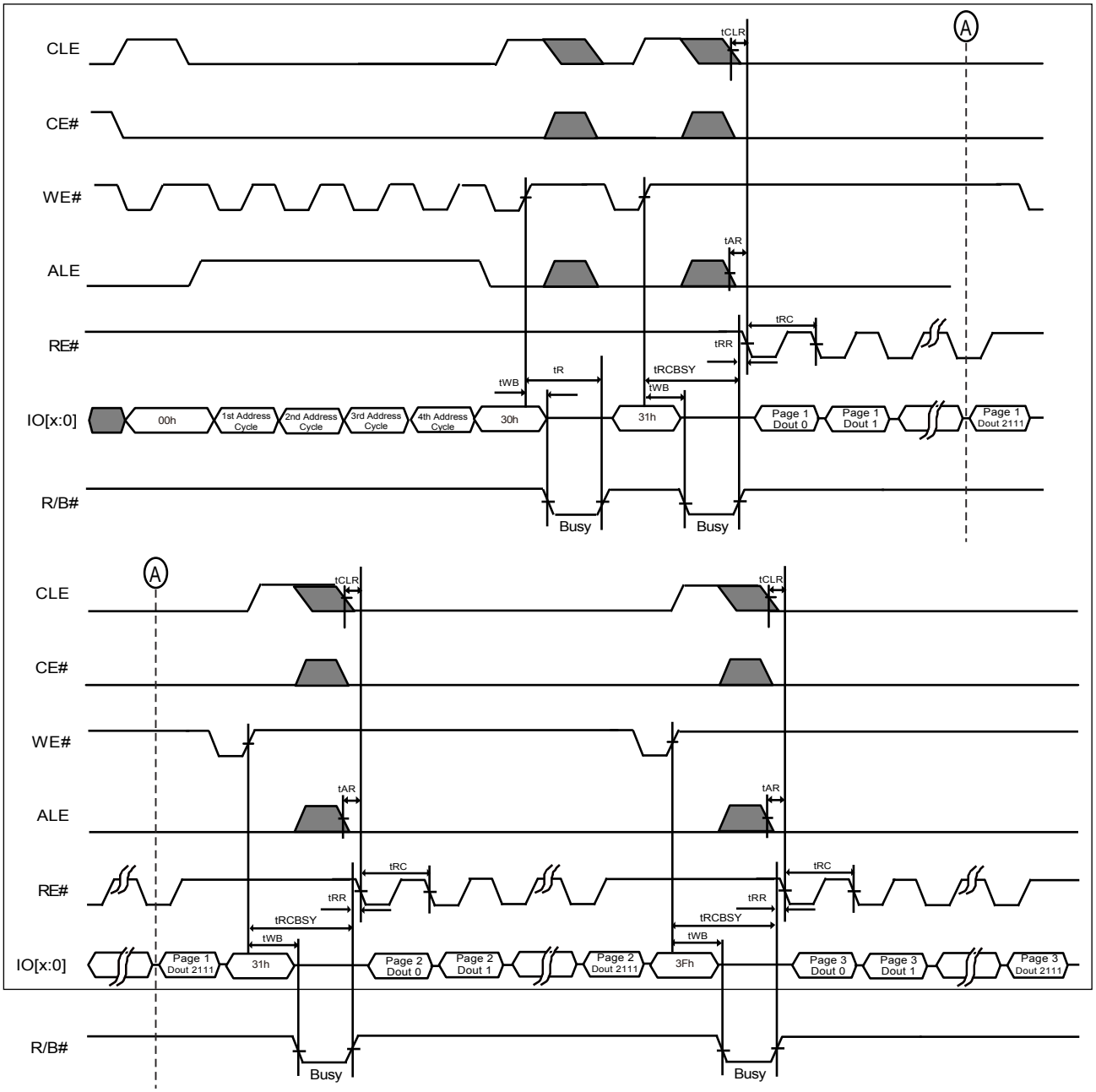
The user can check the chip status by the following method:

- R/B# pin ("0" means the data is not ready, "1" means the user can read the data)

- Status Register (SR[6] functions the same as R/B# pin, SR[5] indicates the internal chip operation, "0" means the chip is in internal operation and "1" means the chip is idle.) Status Register can be checked after the Read Status command (70h) is issued. Command 00h should be given to return to the cache read sequential operation.

To confirm the last page to be read-out during the cache read sequential operation, a 3Fh command is needed to replace the 31h command prior to the last data-out.

Figure 11-1. AC Waveforms for Cache Read Sequential



6-4. Cache Read Random

The main difference from the Cache Read Sequential operation is the Cache Read Random operation may allow the random page to be read-out with cache operation not just for the consecutive page only.

After writing the 00h command, the column and row address should be given for the start page selection, and followed by the 30h command for address confirmation. The column address is ignored in the cache read random operation. And then, the CACHE READ RANDOM operation starts after a latency time tR and following a 00h command with the selected page address and following a 31h command, the data can be read-out after the latency time of tRCBSY. After the previous selected page data out, a new selected page address can be given by writing the 00h-31h command set again. The CACHE READ RANDOM command is also valid for the consecutive page cross block.

The random data out (05h-E0h) command set is available to change the column address of the current page data in the cache register.

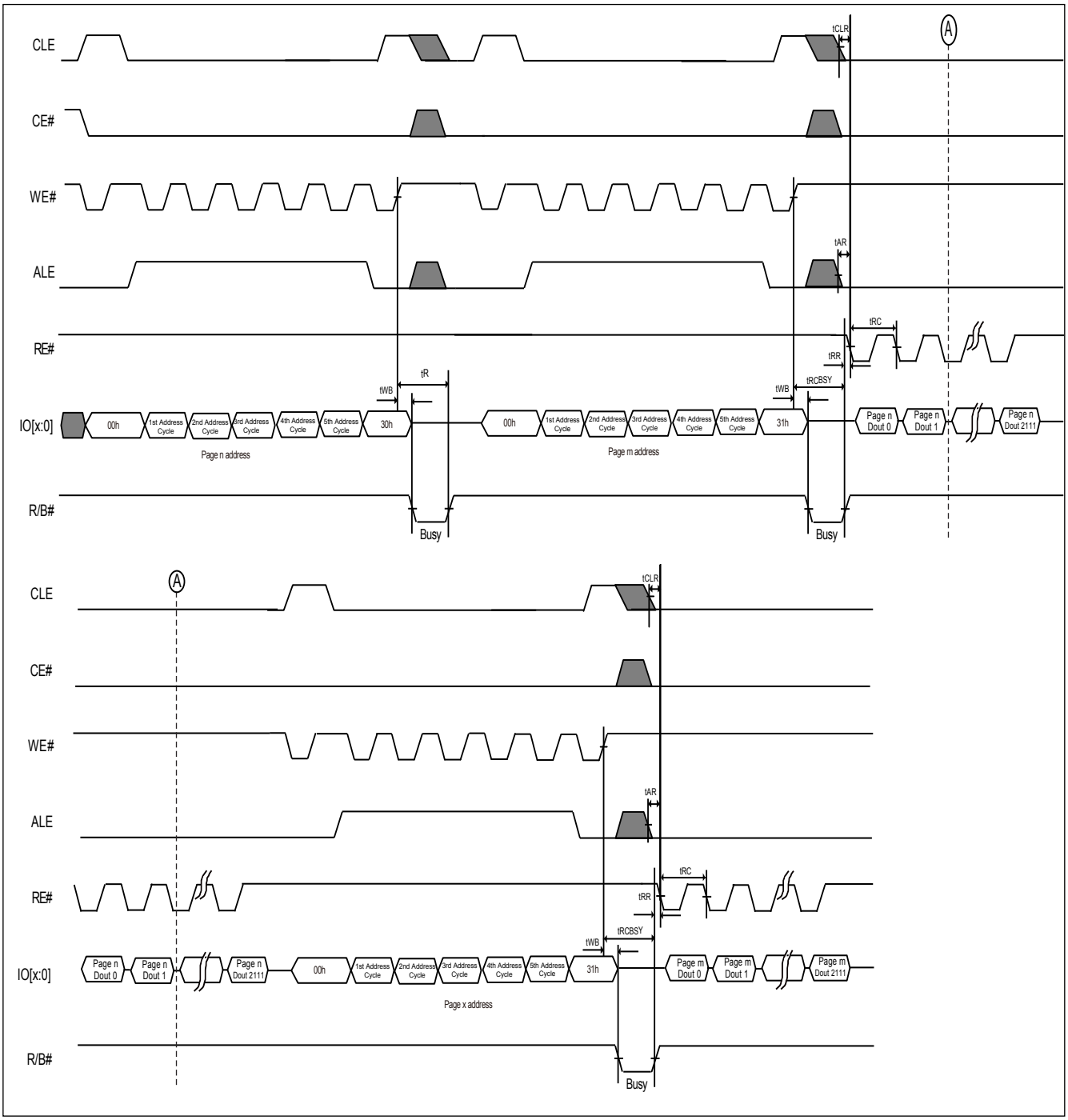
The user can check the chip status by the following method:

- R/B# pin ("0" means the data is not ready, "1" means the user can read the data)

- Status Register can be checked after the Read Status command (70h) is issued. (SR[6] behaves the same as R/B# pin, SR[5] indicates the internal chip operation, "0" means the chip is in internal operation and "1" means the chip is idle.) Command 00h should be given to return to the cache read operation.

To confirm the last page to be read-out during the cache read operation, a 3Fh command is needed to replace the 31h command prior to the last data-out.

Figure 11-2. AC Waveforms for Cache Read Random



6-5. Page Program

The memory is programmed by page, which is 2,160 bytes, or 1080 words. After Program load command (80h) is issued and the row and column address is given, the data will be loaded into the chip sequentially. Random Data Input command (85h) allows multi-data load in non-sequential address. After data load is complete, program confirm command (10h) is issued to start the page program operation. The page program operation in a block should start from the low address to high address. Partial program in a page is allowed up to 4 times. However, the random data input mode for programming a page is allowed and number of times is not limited.

The status of the program completion can be detected by R/B# pin or Status register bit SR[6].

The program result is shown in the chip status bit (SR[0]). SR[0] = 1 indicates the Page Program is not successful and SR[0] = 0 means the program operation is successful.

During the Page Program progressing, only the read status register command and reset command are accepted, others are ignored.

Figure 12. AC Waveforms for Program Operation after Command 80H

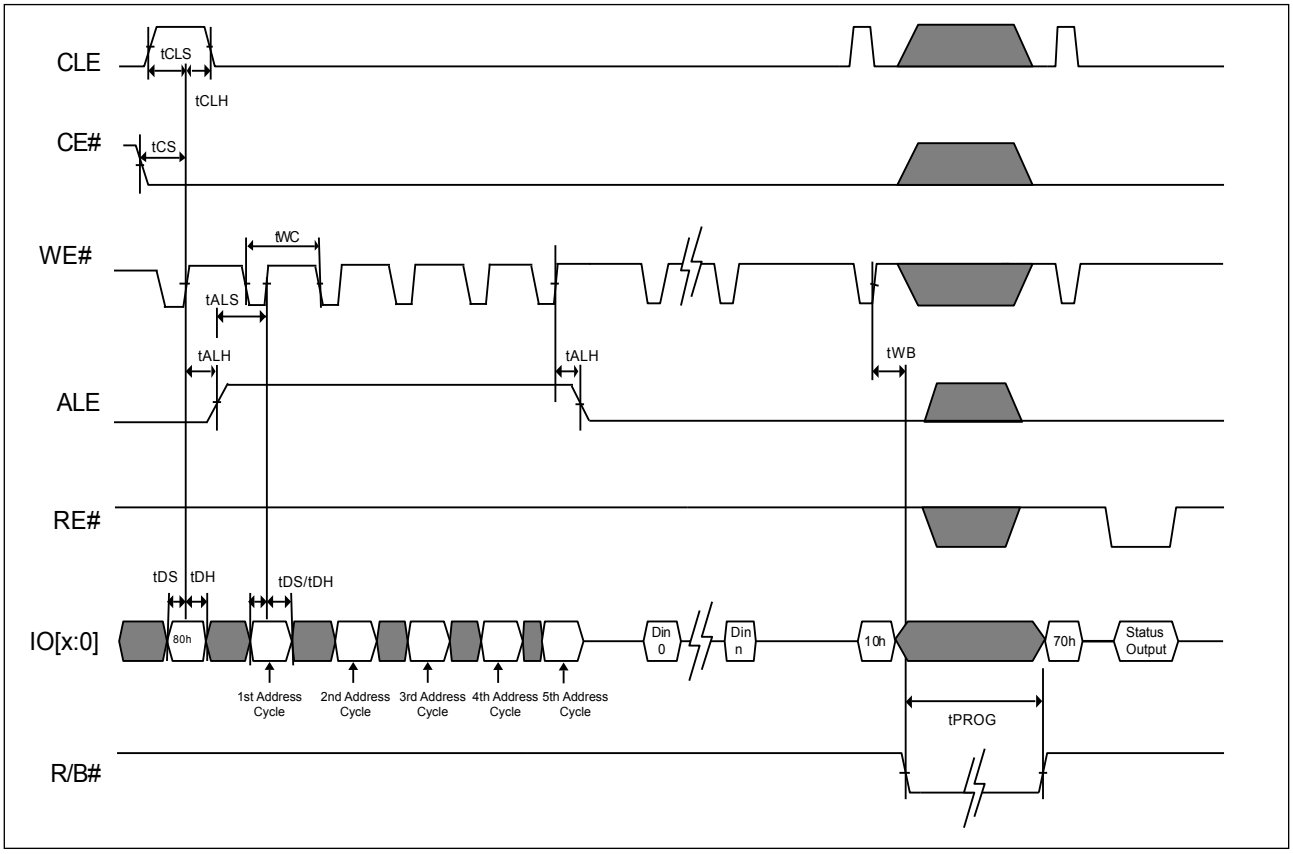
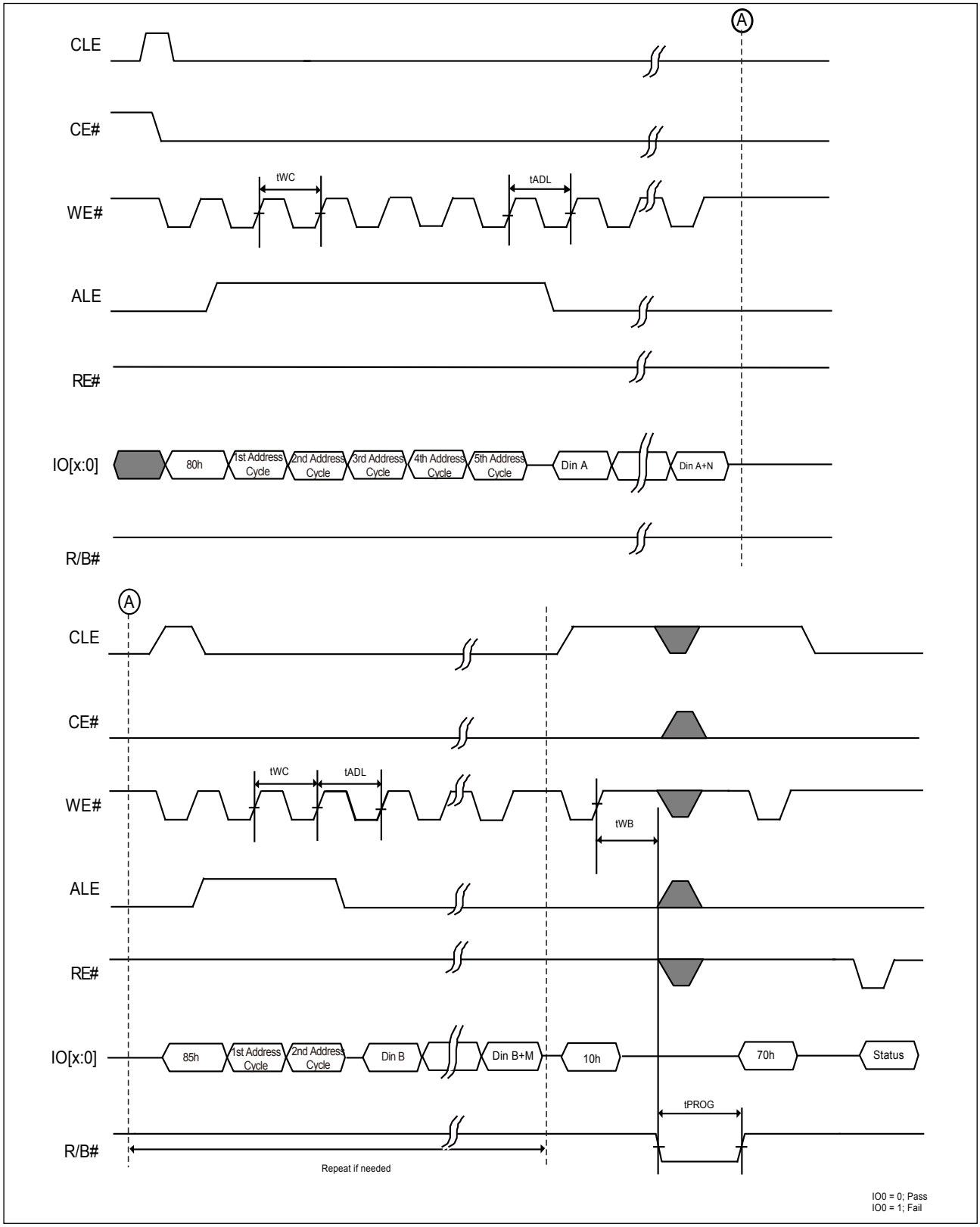
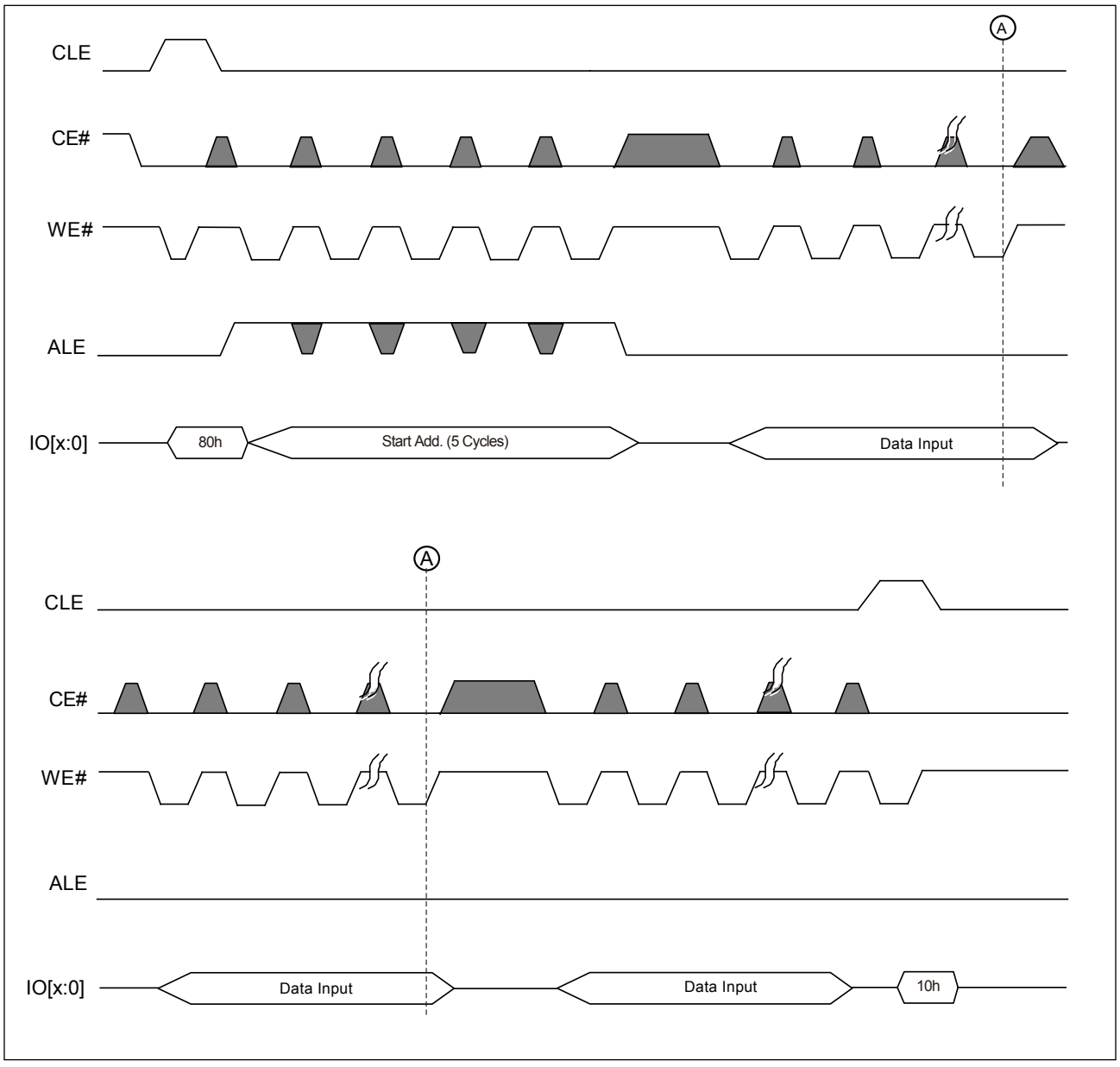


Figure 13. AC Waveforms for Random Data In (For Page Program)



Note: *Random Data In is also supported in cache program.*

Figure 14. AC Waveforms for Program Operation with CE# Don't Care



Note: *The CE# "Don't Care" feature may simplify the system interface, which allows the controller to directly write data into flash device, and the CE# transitions will not stop the program operation during the latency time.*

6-6. Cache Program

The cache program feature enhances the program performance by using the cache buffer of 2,160-byte or 1080 words. The serial data can be input to the cache buffer while the previous data stored in the buffer are programming into the memory cell. Cache Program command sequence is almost the same as page program command sequence. Only the Program Confirm command (10h) is replaced by cache Program command (15h).

After the Cache Program command (15h) is issued. The user can check the status by the following methods.

- R/B# pin

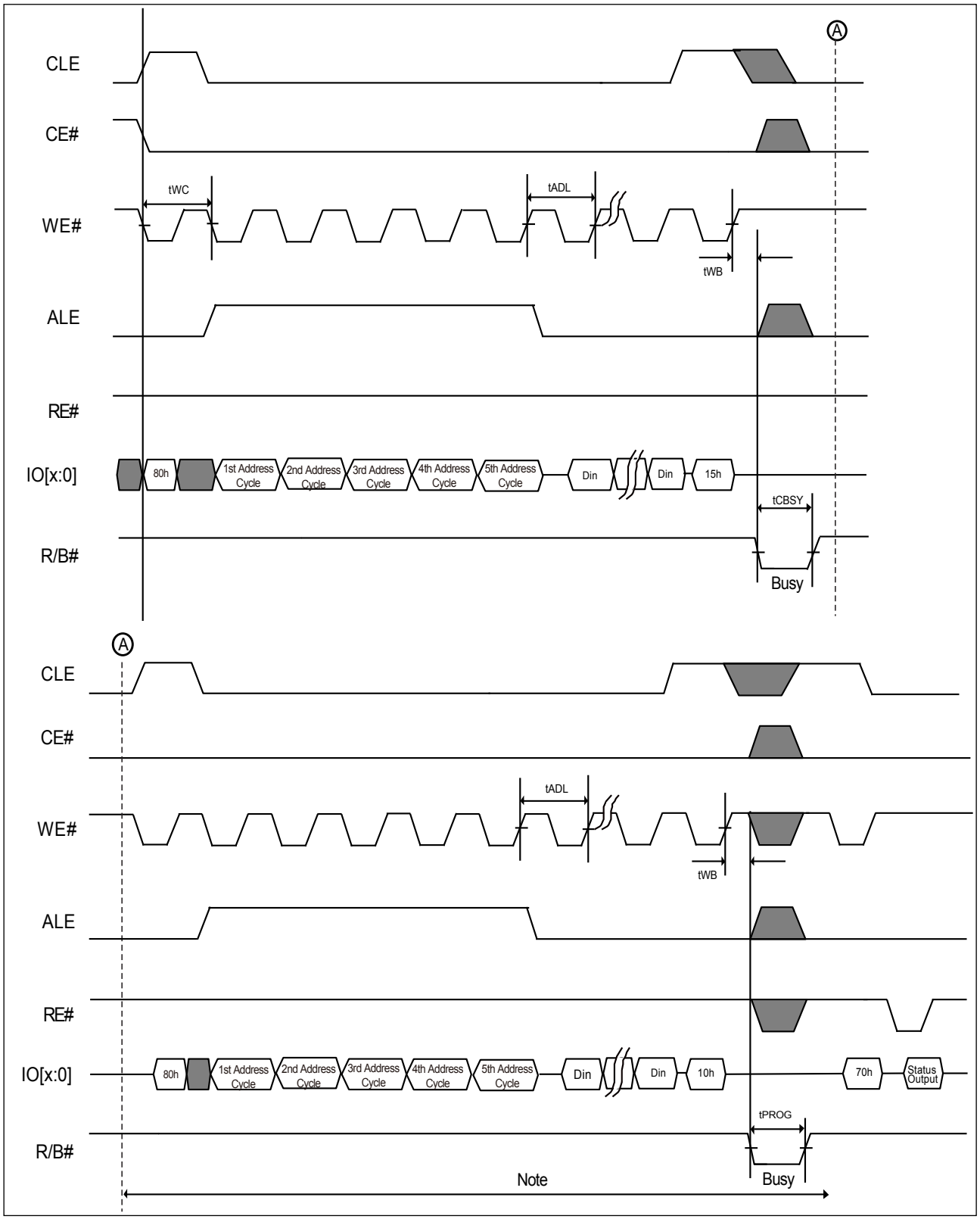
- Cache Status Bit (SR[6] = 0 indicates the cache is busy; SR[6] = 1 means the cache is ready).

The user can issue another Cache Program Command Sequence after the Cache is ready. The user can always monitor the chip state by Ready/Busy Status Bit (SR[5]). The user can issues either program confirm command (10h) or cache program command (15h) for the last page if the user monitor the chip status by issuing Read Status Command (70h).

However, if the user only monitors the R/B# pin, the user needs to issue the program confirm command (10h) for the last page.

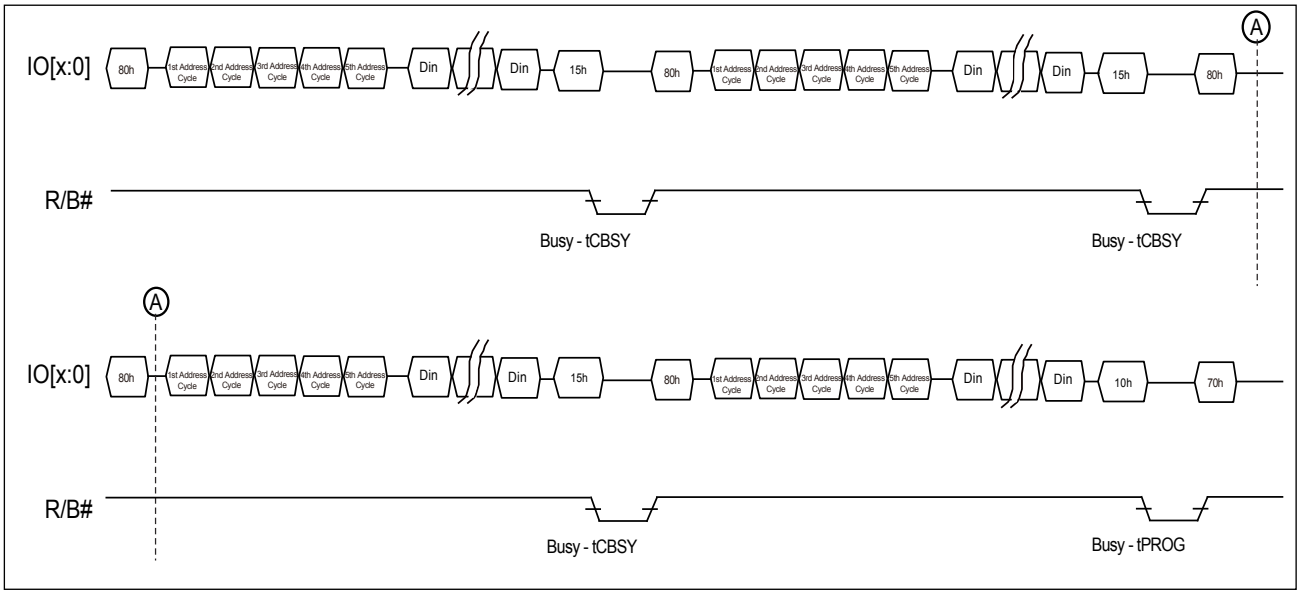
The user can check the Pass/Fail Status through P/F Status Bit (SR[0]) and Cache P/F Status Bit (SR[1]). SR[1] represents Pass/Fail Status of the previous page. SR[1] is updated when SR[6] change from 0 to 1 or Chip is ready. SR[0] shows the Pass/Fail status of the current page. It is updated when SR[5] change from "0" to "1" or the end of the internal programming. For more details, please refer to the related waveforms.

Figure 15-1. AC Waveforms for Cache Program



Note: *It indicates the last page Input & Program.*

Figure 15-2. AC Waveforms for Sequence of Cache Program



Note: *tPROG = Page($_{Last}$) programming time + Page ($_{Last-1}$) programming time - Input cycle time of command & address - Data loading time of page ($_{Last}$).*

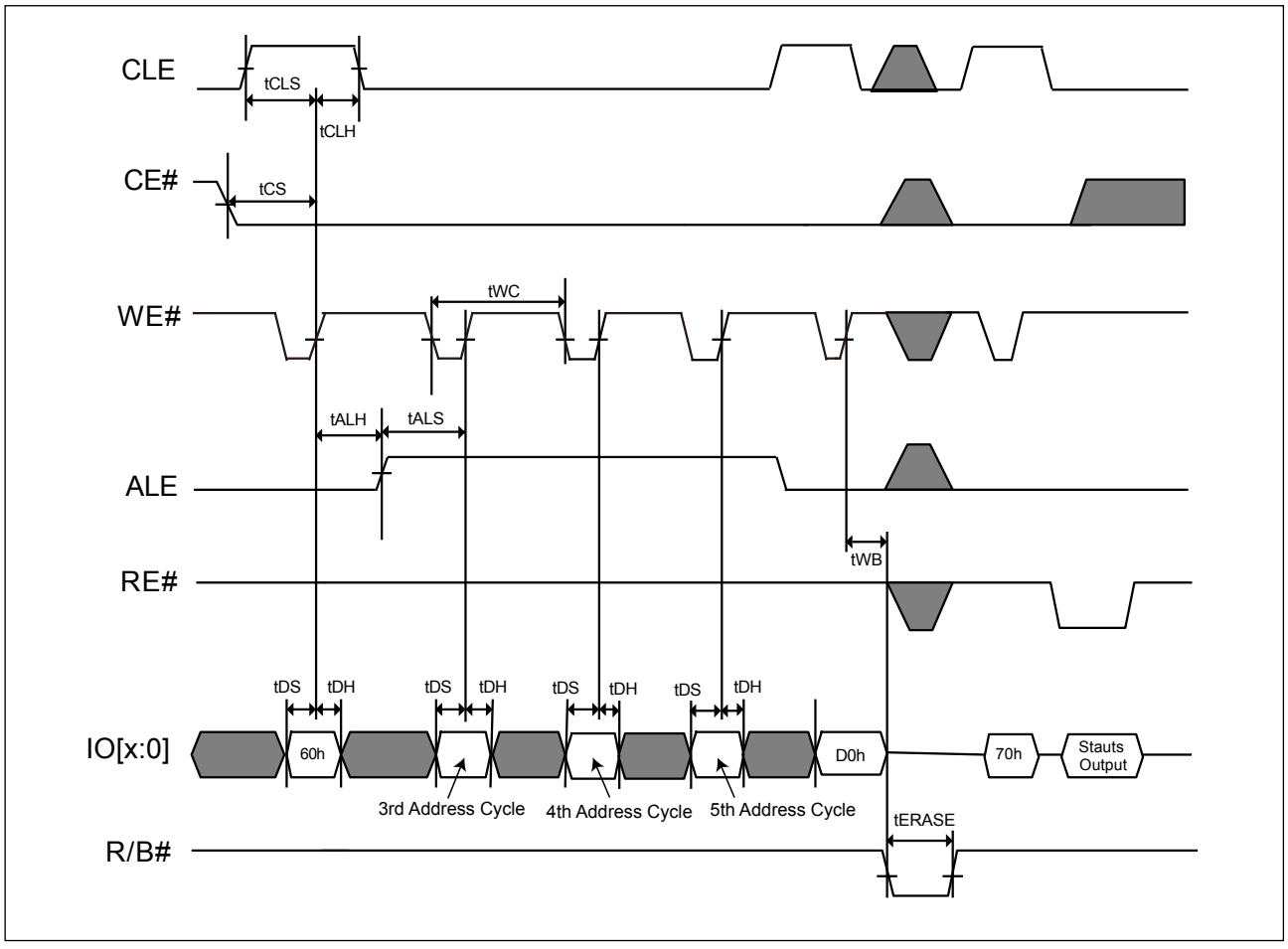
6-7. Block Erase

The MX30UFxG26(28)AB supports a block erase command. This command will erase a block of 64 pages associated with the most significant address bits.

The completion of the erase operation can be detected by R/B# pin or Status register bit (IO6). Recommend to check the status register bit IO0 after the erase operation completes.

During the erasing process, only the read status register command and reset command can be accepted, others are ignored.

Figure 16. AC Waveforms for Erase Operation



6-8. ID Read

The device contains ID codes that identify the device type and the manufacturer. The ID READ command sequence includes one command Byte (90h), one address byte (00h). The Read ID command 90h may provide the manufacturer ID (C2h) of one-byte and device ID (AAh for 2Gb, x8; BAh for 2Gb, X16; ACh for 4Gb, X8; BCh for 4Gb, X16) of one-byte, also Byte2, Byte3, and Byte4 ID code are followed.

The device support ONFI Parameter Page Read, by sending the ID Read (90h) command and following one byte address (20h), the four-byte data returns the value of 4Fh-4Eh-46h-49h for the ASCII code of "O"-"N"-"F"-"I" to identify the ONFI parameter page.

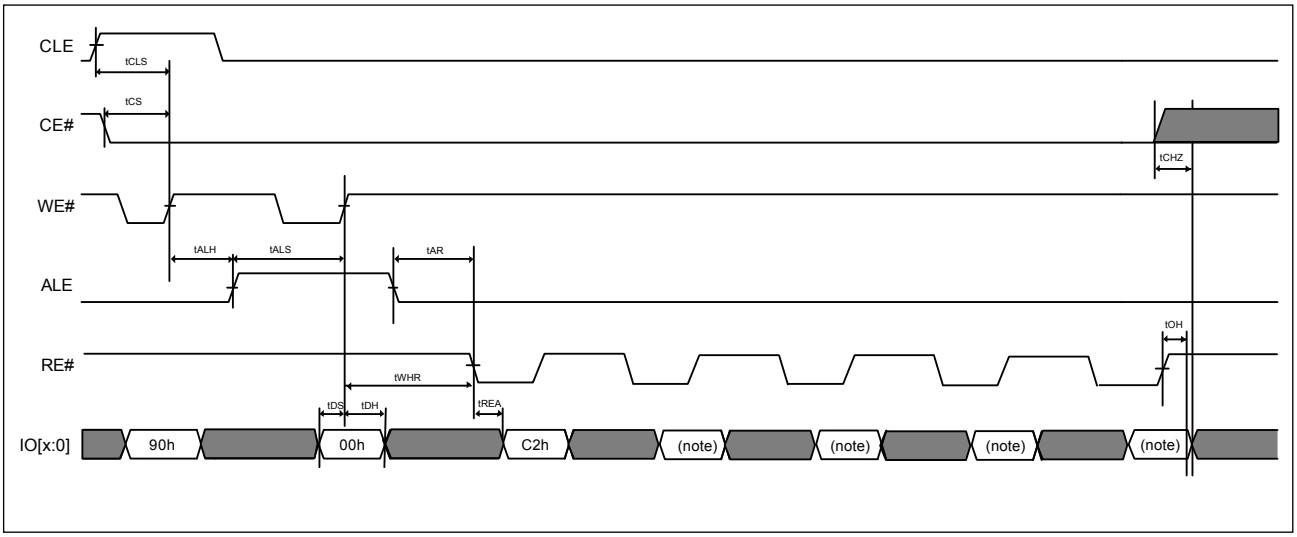
Table 2. ID Codes Read Out by ID Read Command 90H

2Gb	**2Gb, x8, 1.8V**	**2Gb, x16, 1.8V**
Byte0-Manufacturer	C2h	C2h
Byte1: Device ID	AAh	BAh
Byte2	90h	90h
Byte3	15h	55h
Byte4	07h	07h
4Gb	**4Gb, x8, 1.8V**	**4Gb, x16, 1.8V**
Byte0-Manufacturer	C2h	C2h
Byte1: Device ID	ACh	BCh
Byte2	90h	90h
Byte3	15h	55h
Byte4	57h	57h

Table 3. The Definition of Byte2~Byte4 of ID Table

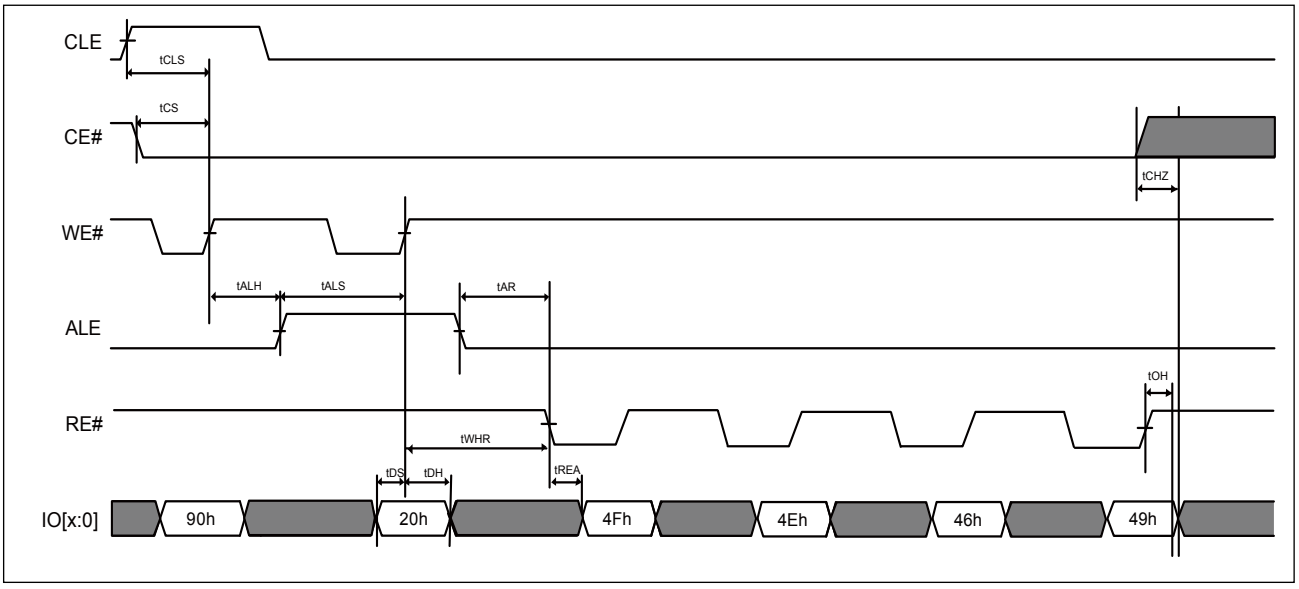
Terms	Description	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Byte 2									
Die# per CE	1							0	0
	2							0	1
Cell type	SLC					0	0		
# of Simultaneously Programmed page	1			0	0				
	2			0	1				
Interleaved operations between Multiple die	Not supported		0						
Cache Program	Supported	1							
Byte 3									
Page size	2KB							0	1
Spare area size	28B						1		
Block size (without spare)	128KB			0	1				
Organization	x8		0						
Sequential access (min.)	25ns	0				0			
	20ns	1				0			
Byte 4									
ECC level requirement	8-bit ECC/540B							1	1
#Plane per CE	1					0	0		
	2					0	1		
	4					1	0		
Plane size	1Gb		0	0	0				
	2Gb		1	0	1				
Reserved		0							

Figure 17-1. AC Waveforms for ID Read Operation



Note: *See also* ***Table 2. ID Codes Read Out by ID Read Command 90H***.

Figure 17-2. AC Waveforms for ID Read (ONFI Identifier) Operation



6-9. Status Read

The MX30UFxG26(28)AB provides a status register that outputs the device status by writing a command code 70h, and then the IO pins output the status at the falling edge of CE# or RE# which occurs last. Even though when multiple flash devices are connecting in system and the R/B#pins are common-wired, the two lines of CE# and RE# may be checked for individual devices status separately.

The status read command 70h will keep the device at the status read mode unless next valid command is issued. The resulting information is outlined in **Table 4** as below.

Table 4. Status Output

Pin	Status	Related Mode	Value	
SR[0]	Chip Status	Page Read, Cache Read, Page Program, Cache Program (Page N), Block Erase	0: Passed	1: Failed
SR[1]	Cache Program Result	Cache Program (Page N-1)	0: Passed	1: Failed
SR[2-4]	Not Used			
SR[5]	Ready / Busy (For P/E/R Controller)	Cache Program/Cache Read operation, other Page Program/Block Erase/Read are same as IO6 (Note 1)	0: Busy	1: Ready
SR[6]	Ready / Busy	Page Program, Block Erase, Cache Program, Read, Cache Read (Note 2)	0: Busy	1: Ready
SR[7]	Write Protect	Page Program, Block Erase, Cache Program, Read	0: Protected	1: Unprotected

Notes:

1. *During the actual programming operation, the SR[5] is "0" value; however, when the internal operation is completed during the cache mode, the SR[5] returns to "1".*
2. *The SR[6] returns to "1" when the internal cache is available to receive new data. The SR[6] value is consistent with the R/B#.*

The following is an example of a HEX data bit assignment:

Figure 18. Bit Assignment (HEX Data)

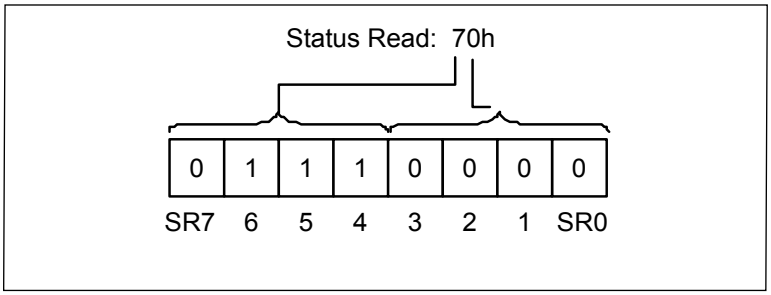
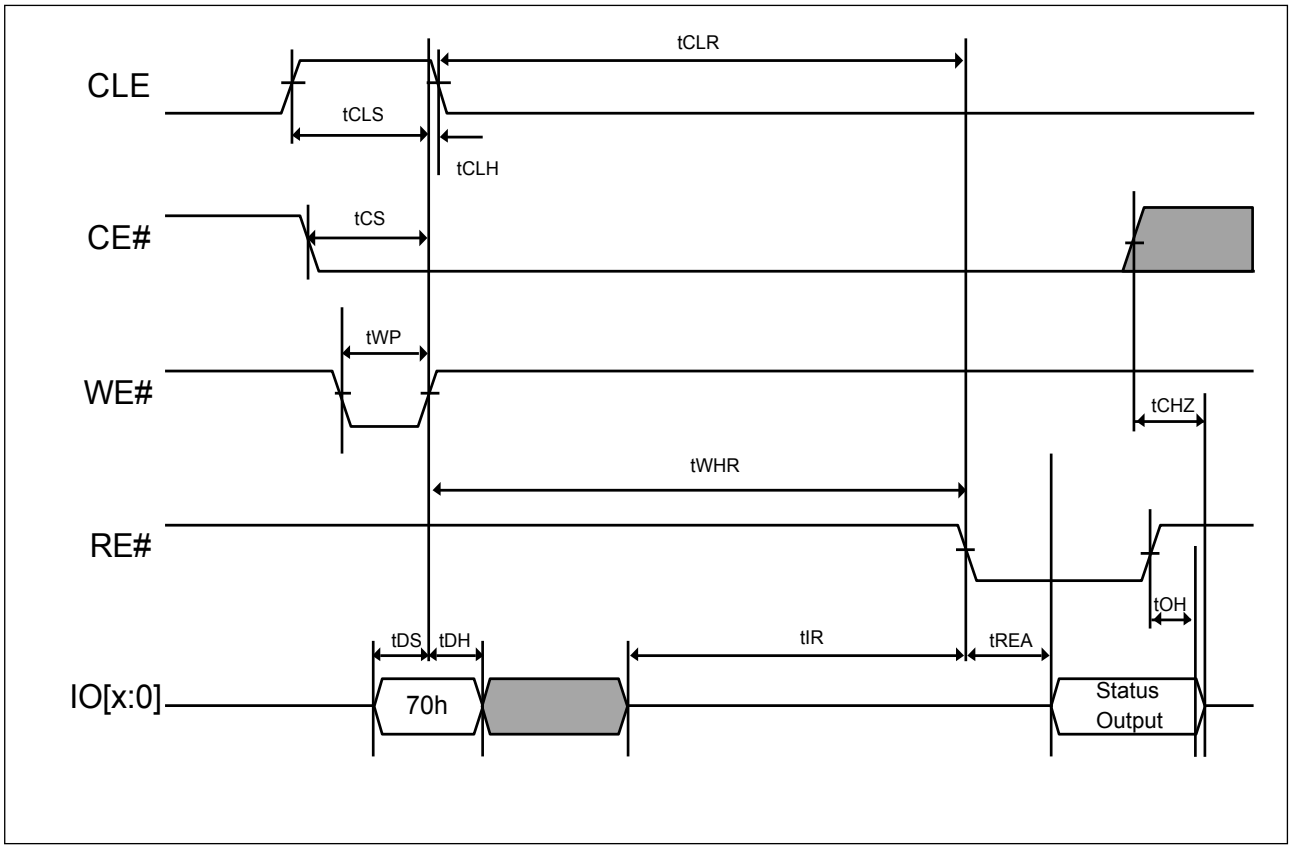


Figure 19. AC Waveforms for Status Read Operation

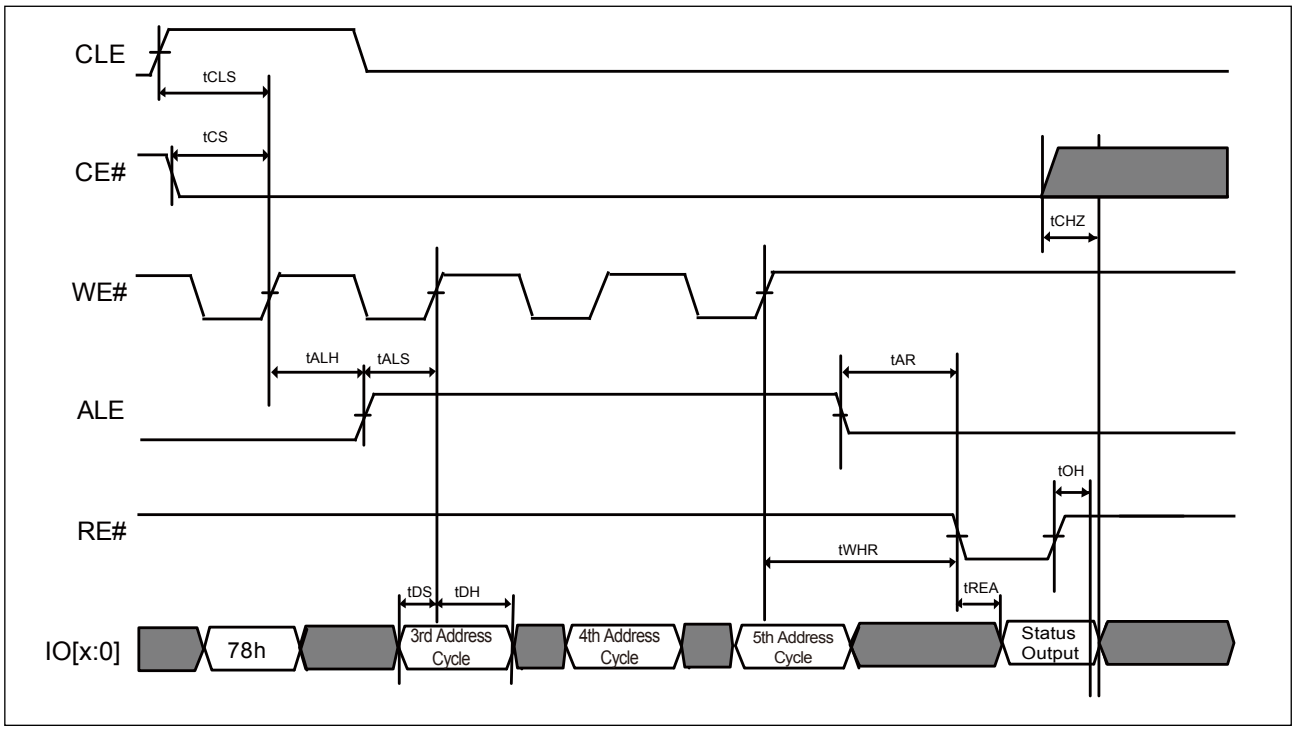


6-10. Status Enhance Read

The 2Gb and 4Gb support the two-plane operation, the Status Enhanced Read command (78h) offers the alternative method besides the Status Read command to get the status of specific plane in the same NAND Flash device.

The [SR]6 and SR[5] bits are shared with all planes. However, the SR[0], SR[1], SR[3], SR[4] are for the status of specific plane in the row address. The Status Enhanced Read command is not allowed at power-on Reset (FFh) command, OTP enabled operation.

Figure 20. AC Waveforms for Status Enhance Operation

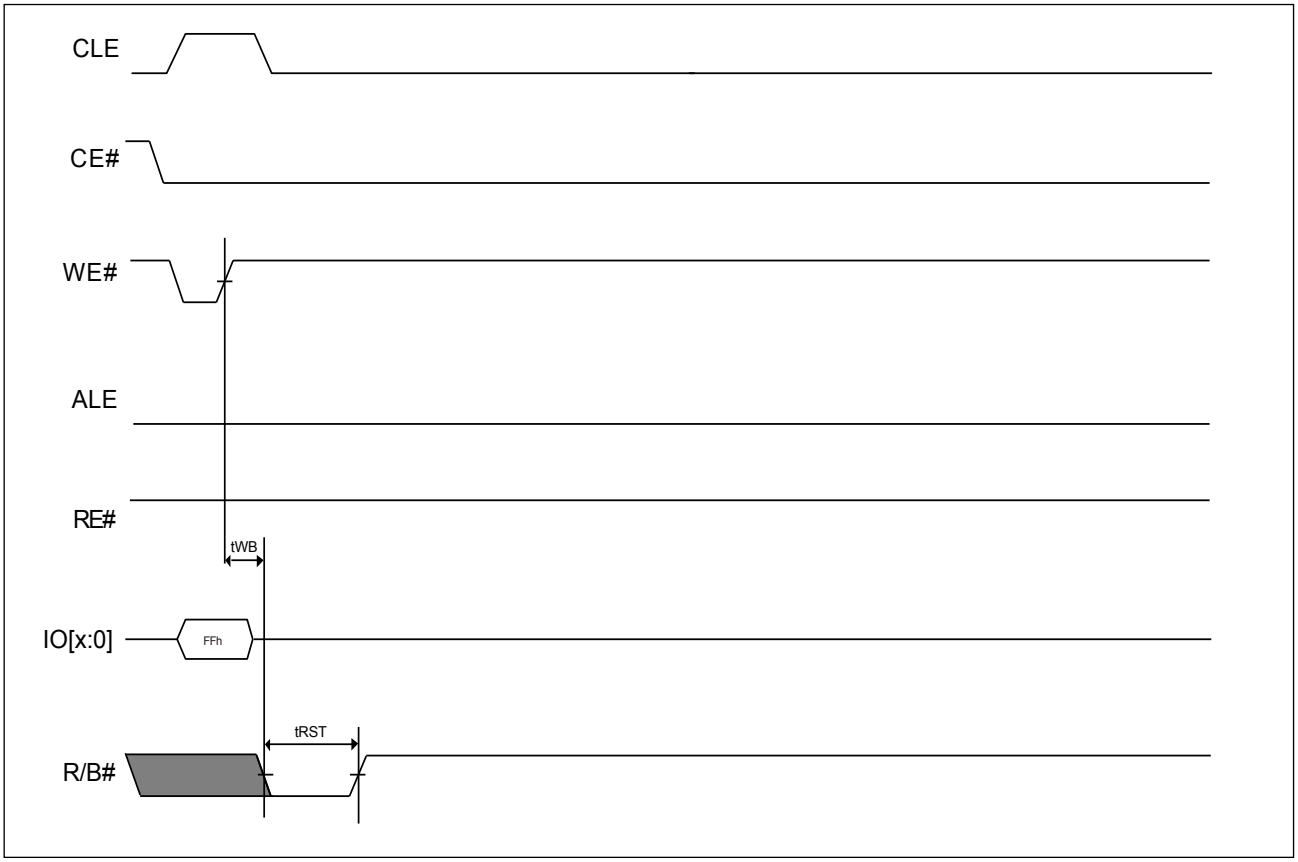


6-11. Reset

The reset command FFh resets the read/program/erase operation and clear the status register to be E0h after chip returns to ready state (when WP# is high). The reset command during the program/erase operation will result in the content of the selected locations(perform programming/erasing) might be partially programmed/ erased.

If the Flash memory has already been set to reset stage with reset command, the additional new reset command is invalid.

Figure 21. AC waveforms for Reset Operation



6-12. Parameter Page Read (ONFI)

The NAND Flash device support ONFI Parameter Page Read and the parameter can be read out by sending the command of ECh and giving the address 00h. The NAND device information may refer to the table of parameter page(ONFI), there are three copies of 256-byte data and additional redundant parameter pages.

Once sending the ECh command, the NAND device will remain in the Parameter Page Read mode until next valid command is sent.

The Random Data Out command set (05h-E0h) can be used to change the parameter location for the specific parameter data random read out.

The Status Read command (70h) can be used to check the completion with a following read command (00h) to enable the data out.

Figure 22. AC waveforms for Parameter Page Read (ONFI) Operation

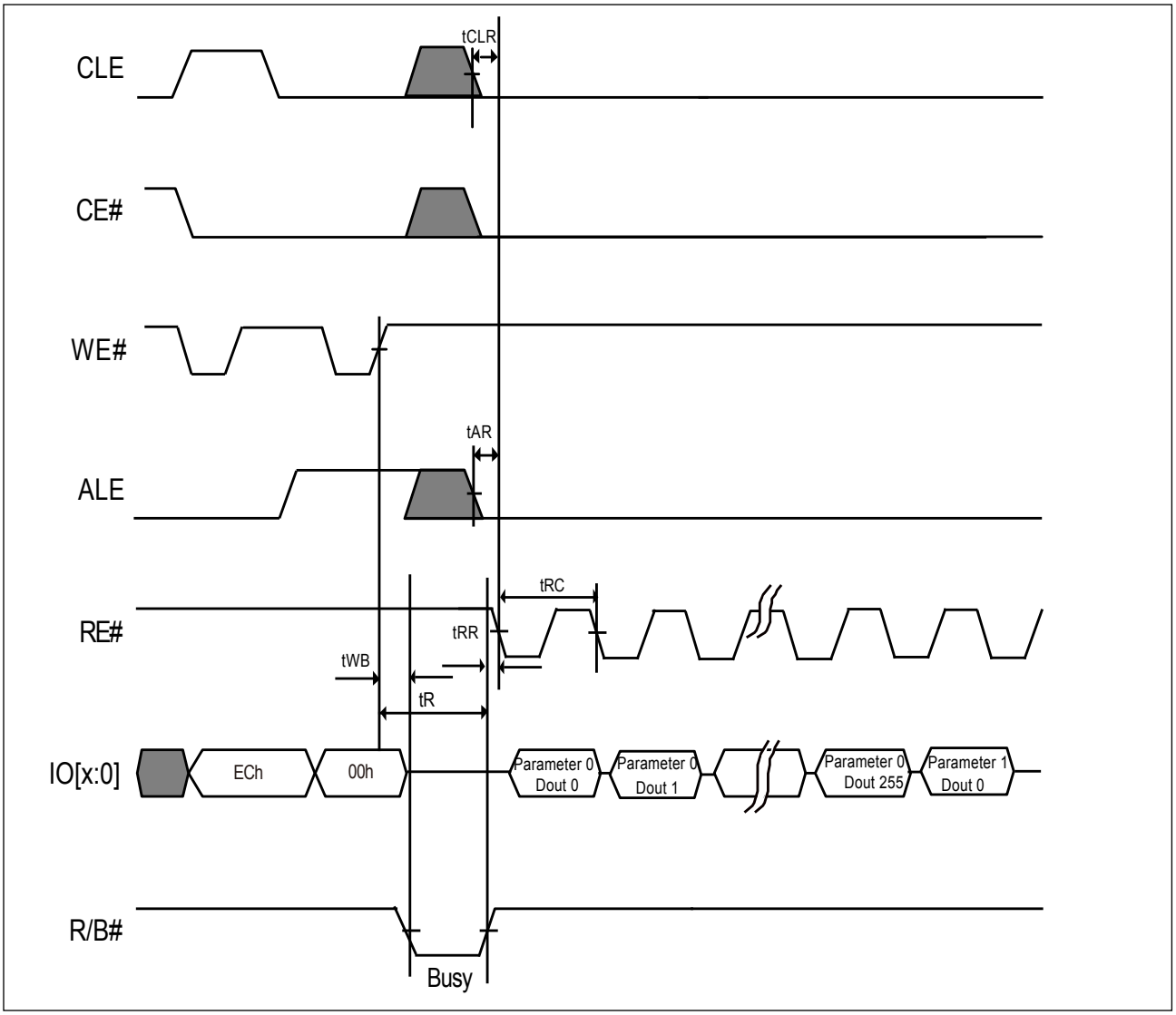


Figure 23. AC Waveforms for Parameter Page Read (ONFI) Random Operation (For 05h-E0h)

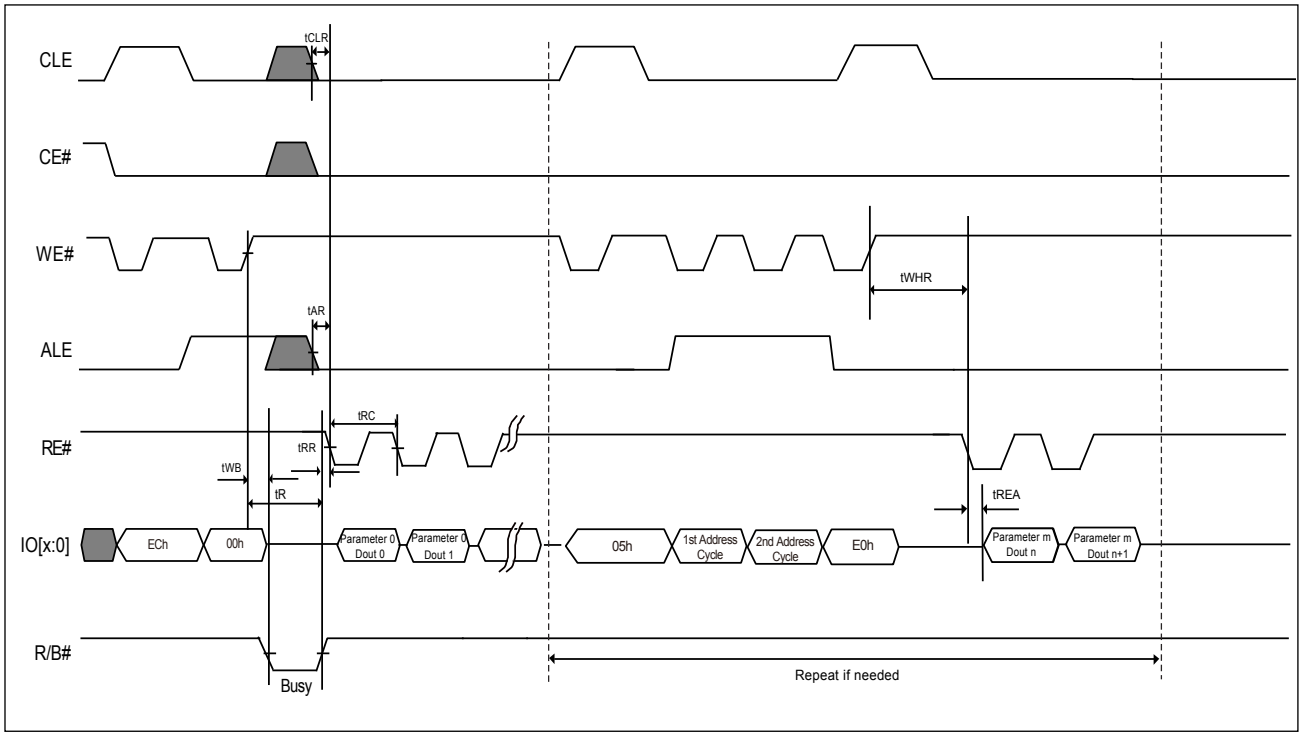


Table 5. Parameter Page (ONFI)

	Revision Information and Features Block		
Byte#	**Description**		**Data**
0-3	**Parameter Page Signature**		4Fh, 4Eh, 46h, 49h
4-5	**Revision Number**		02h, 00h
6-7	**Features Supported**	2Gb, x8	18h, 00h
		2Gb, x16	19h, 00h
		4Gb, x8	18h, 00h
		4Gb, x16	19h, 00h
8-9	**Optional Commands Supported**	2Gb	3Fh, 00h
		4Gb	3Fh, 00h
10-31	**Reserved**		00h
	Manufacturer Information Block		
Byte#	**Description**		**Data**
32-43	**Device Manufacturer (12 ASCII characters)**		4Dh,41h,43h,52h,4Fh,4Eh,49h,58h, 20h,20h,20h,20h
44-63	**Device Model (20 ASCII Characters)**	MX30UF2G28AB	4Dh,58h,33h,30h,55h,46h,32h,47h, 32h,38h,41h,42h,20h,20h,20h,20h,2 0h,20h,20h,20h,
		MX30UF2G26AB	4Dh,58h,33h,30h,55h,46h,32h,47h, 32h,36h,41h,42h,20h,20h,20h,20h,2 0h,20h,20h,20h,
		MX30UF4G28AB	4Dh,58h,33h,30h,55h,46h,34h,47h, 32h,38h,41h,42h,20h,20h,20h,20h,2 0h,20h,20h,20h,
		MX30UF4G26AB	4Dh,58h,33h,30h,55h,46h,34h,47h,3 2h,36h,41h,42h,20h,20h,20h,20h,20 h,20h,20h,20h,
64	**JEDEC Manufacturer ID**		C2h
65-66	**Date Code**		00h, 00h
67-79	**Reserved**		00h

Memory Organization Block			
Byte#	**Description**		**Data**
80-83	Number of Data Bytes per Page	2048-byte	00h,08h,00h,00h
84-85	Number of Spare Bytes per Page	112-byte	70h,00h
86-89	Number of Data Bytes per Partial Page	512-byte	00h,02h,00h,00h
90-91	Number of Spare Bytes per Partial Page	28-byte	1Ch,00h
92-95	Number of Pages per Block		40h,00h,00h,00h
96-99	Number of Blocks per Logical Unit	2Gb	00h,08h,00h,00h
		4Gb	00h,10h,00h,00h
100	Number of Logical Units (LUNs)		01h
101	Number of Address Cycles	2Gb	23h
		4Gb	23h
102	Number of Bits per Cell		01h
103-104	Bad Blocks Maximum per LUN	2Gb	28h,00h
		4Gb	50h,00h
105-106	Block endurance		01h, 05h
107	Guarantee Valid Blocks at Beginning of Target		01h
108-109	Block endurance for guaranteed valid blocks		01h, 03h
110	Number of Programs per Page		04h
111	Partial Programming Attributes		00h
112	Number of Bits ECC Correctability		08h
113	Number of Interleaved Address Bits	2Gb	01h
		4Gb	01h
114	Interleaved Operation Attributes	2Gb	0Eh
		4Gb	0Eh
115-127	Reserved		00h

Electrical Parameters Block			
Byte#	**Description**		**Data**
128	I/O Pin Capacitance		0Ah
129-130	Timing Mode Support	25ns	1Fh,00h
131-132	Program Cache Timing Mode Support	25ns	1Fh,00h
133-134	tPROG Maximum Page Program Time (uS)	600us	58h,02h
135-136	tBERS(tERASE) Maximum Block Erase Time (uS)	3,500us	ACh,0Dh
137-138	tR Maximum Page Read Time (uS)	25us	19h,00h
139-140	tCCS Minimum Change Column Setup Time (ns)	80ns	50h,00h
141-163	Reserved		00h

Vendor Blocks		
Byte#	**Description**	**Data**
164-165	Vendor Specific Revision Number	00h
166-253	Vendor Specific	00h
254-255	Integrity CRC	Set at Test ***(Note)***
Redundant Parameter Pages		
Byte#	**Description**	**Data**
256-511	Value of Bytes 0-255	
512-767	Value of Bytes 0-255	
768+	Additional Redundant Parameter Pages	

Note: *The Integrity CRC (Cycling Redundancy Check) field is used to verify that the contents of the parameters page were transferred correctly to the host. Please refer to ONFI 1.0 specifications for details.*

The CRC shall be calculated using the following 16-bit generator polynomial:

$G(X) = X_{16} + X_{15} + X_2 + 1$

6-13. Unique ID Read (ONFI)

The unique ID is 32-byte and with 16 copies for back-up purpose. After writing the Unique ID read command (EDh) and following the one address byte (00h), the host may read out the unique ID data. The host need to XOR the 1st 16-byte unique data and the 2nd 16-byte complement data to get the result, if the result is FFh, the unique ID data is correct; otherwise, host need to repeat the XOR with the next copy of Unique ID data.

Once sending the EDh command, the NAND device will remain in the Unique ID read mode until next valid command is sent.

To change the data output location, it is recommended to use the Random Data Out command set (05h-E0h).

The Status Read command (70h) can be used to check the completion. To continue the read operation, a following read command (00h) to re-enable the data out is necessary.

Figure 24. AC waveforms for Unique ID Read Operation

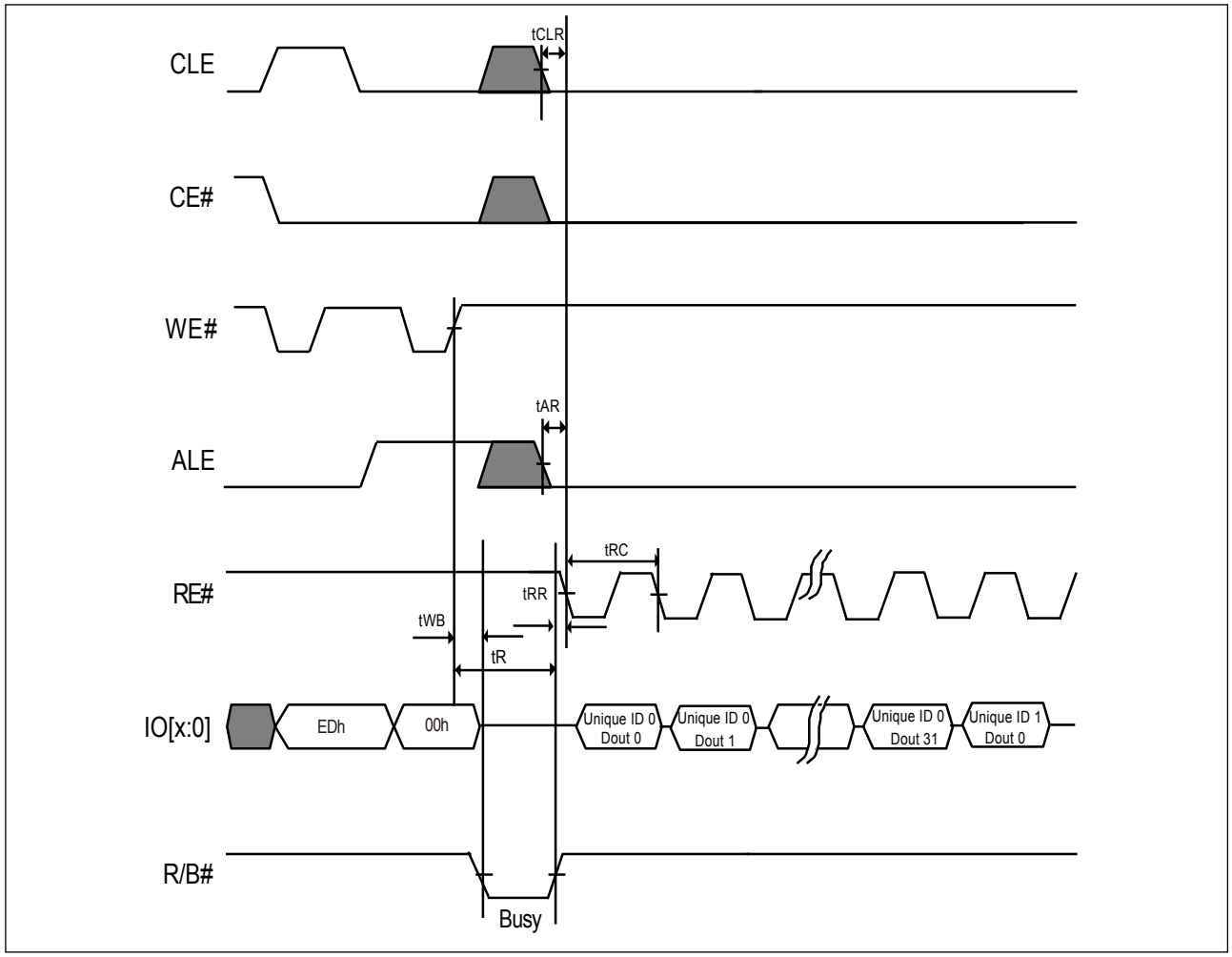
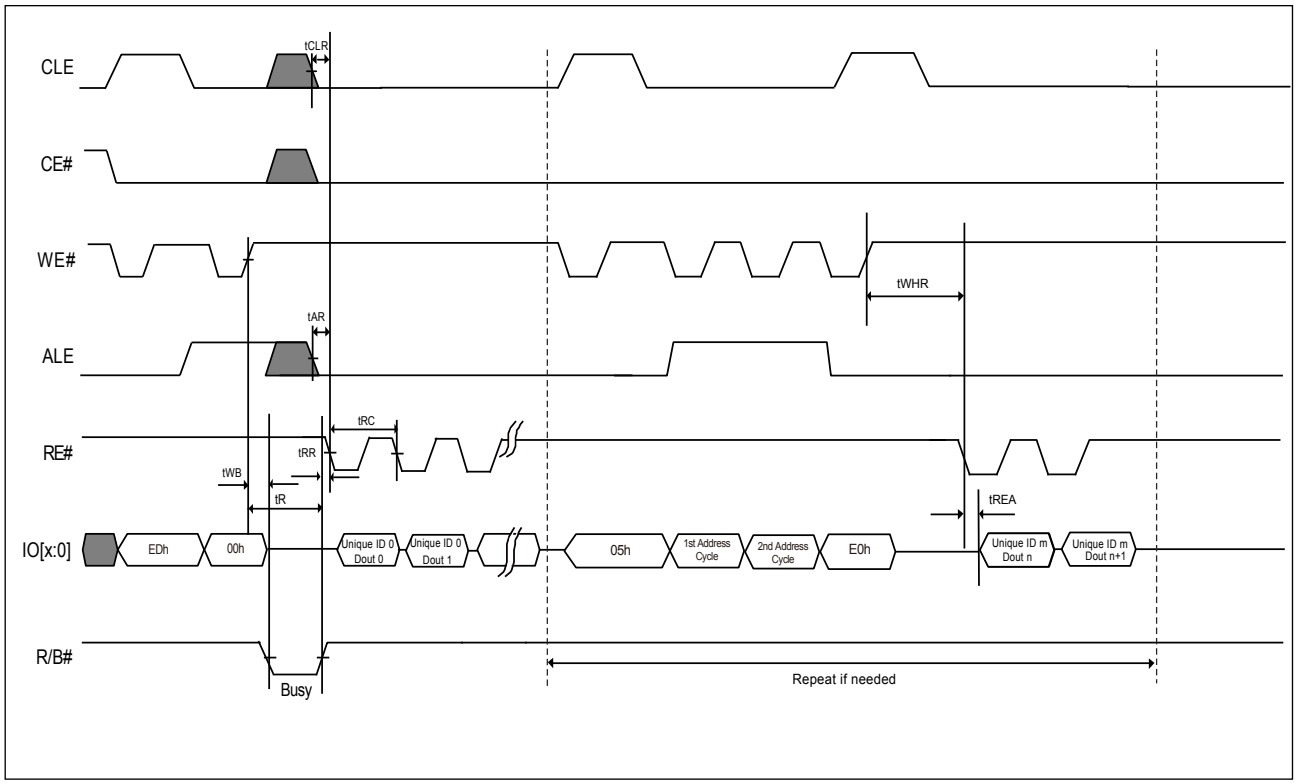


Figure 25. AC waveforms for Unique ID Read Operation (For 05h-E0h)



6-14. Feature Set Operation (ONFI)

The Feature Set operation is to change the default power-on feature sets by using the Set Feature and Get Feature command and writing the specific parameter data (P1-P4) on the specific feature addresses. The NAND device may remain the current feature set until next power cycle since the feature set data is volatile. However, the reset command (FFh) can not reset the current feature set.

Table 6-1. Definition of Feature Address

Feature Address	Description
00h	Reserved
01h	Timing Mode
02h-7Fh	Reserved
80h	Programmable I/O Drive Strength
81h	Programmable R/B# pull-down Strength
82h-8Fh, 91h-FFh	Reserved
90h	Array Operation Mode

Table 6-2. Sub-Feature Parameter Table of Feature Address - 01h (Timing Mode)

Sub Feature Parameter	Definition		IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0	Values	Notes
P1	Timing Mode	Mode 0 (Default)	Reserved (0)					0	0	0	00h	1
		Mode 1						0	0	1	01h	1
		Mode 2						0	1	0	02h	1
		Mode 3						0	1	1	03h	1
		Mode 4						1	0	0	04h	1
		Mode 5						1	0	1	05h	1
P2			Reserved (0)								00h	
P3			Reserved (0)								00h	
P4			Reserved (0)								00h	

Note 1. *Please refer to ONFI standard for detail specifications on Mode 0,1,2,3,4,5.*

Table 6-3. Sub-Feature Parameter Table of Feature Address - 80h (Programmable I/O Drive Strength)

Sub Feature Parameter	Definition		IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0	Values	Notes
P1	I/O Drive Strength	Full(Default)	Reserved (0)						0	0	00h	1
		3/4							0	1	01h	
		1/2							1	0	02h	
		1/4							1	1	03h	
P2			Reserved (0)								00h	
P3			Reserved (0)								00h	
P4			Reserved (0)								00h	

Note 1. *If the I/O Drive strength is not full, the AC spec might need to be relaxed.*

Table 6-4. Sub-Feature Parameter Table of Feature Address- 81h (Programmable R/B# pull-down Strength)

Sub Feature Parameter	Definition		IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0	Values	Notes
P1	R/B# Pull-down Strength	Full (Default)	Reserved (0)						0	0	00h	
		3/4							0	1	01h	
		1/2							1	0	02h	
		1/4							1	1	03h	
P2			Reserved (0)								00h	
P3			Reserved (0)								00h	
P4			Reserved (0)								00h	

Table 6-5. Sub-Feature Parameter Table of Feature Address - 90h (Array Operation Mode)

Sub Feature Parameter	Definition		IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0	Values	Notes
P1	Array Operation Mode	Normal	Reserved (0)						0	0	0000 0000b	1
		OTP Operation	Reserved (0)				x	0	0	1	0000 x001b	
		OTP Protection	Reserved (0)				x	0	1	1	0000 x011b	
P2			Reserved (0)								0000 0000b	
P3			Reserved (0)								0000 0000b	
P4			Reserved (0)								0000 0000b	

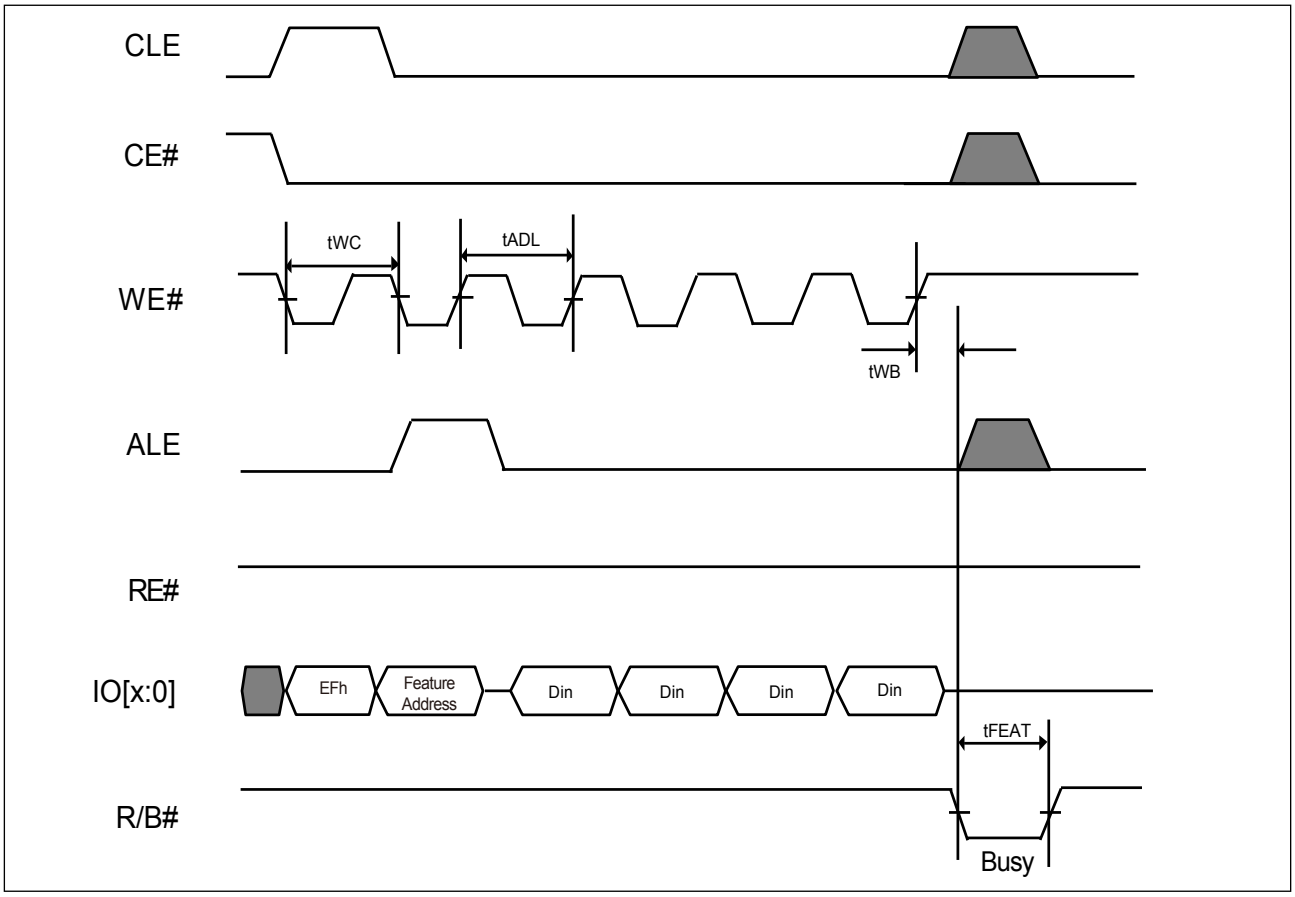
Note 1. *The value is clear to 00h at power cycle.*

6-14-1. Set Feature (ONFI)

The Set Feature command is to change the power-on default feature set. After sending the Set Feature command (EFh) and following specific feature and then input the P1-P4 parameter data to change the default power-on feature set. Once sending the EFh command, the NAND device will remain in the Set Feature mode until next valid command is sent.

The Status Read command (70h) may check the completion of the Set Feature.

Figure 26. AC Waveforms for Set Feature (ONFI) Operation



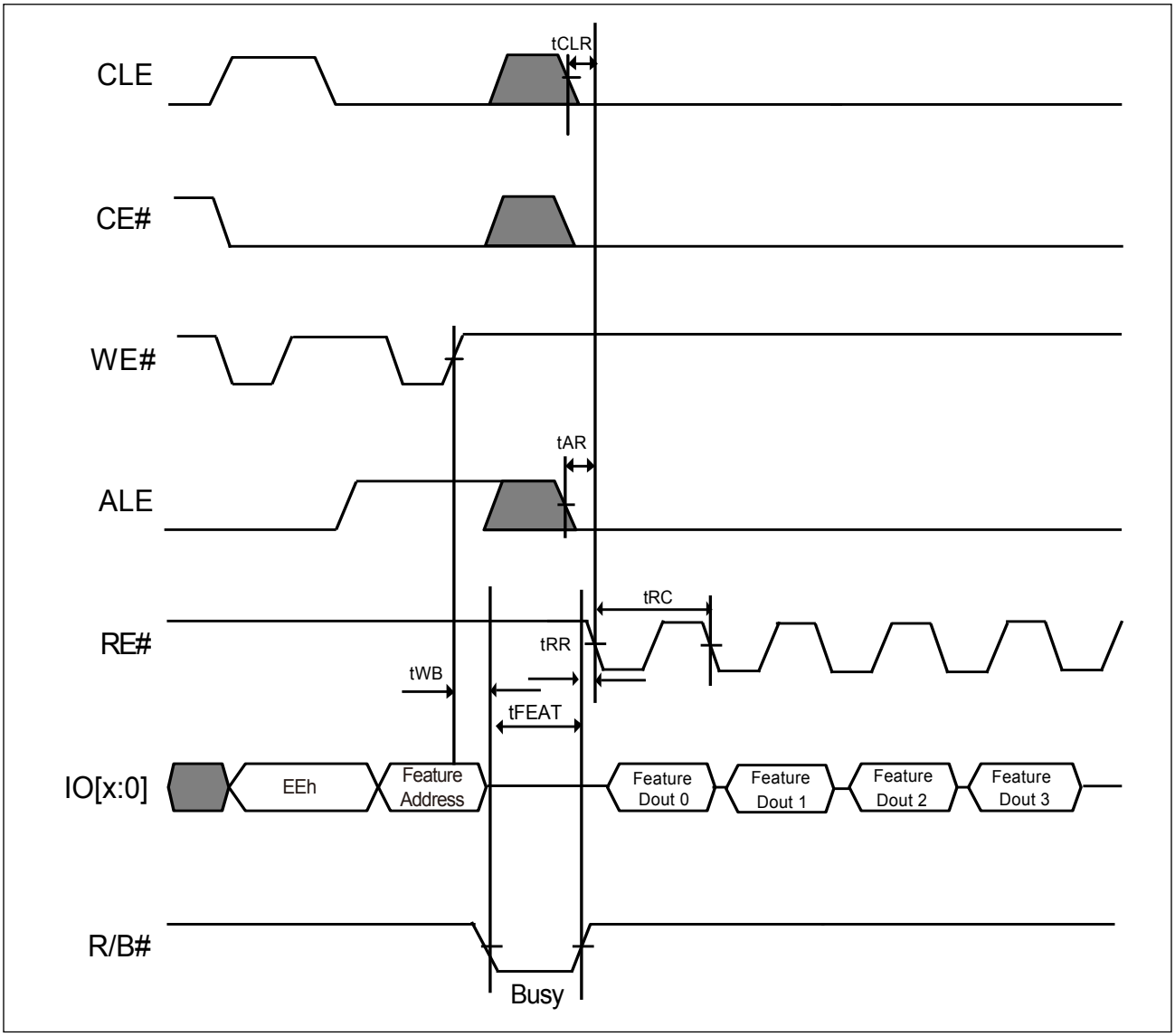
6-14-2. Get Feature (ONFI)

The Get Feature command is to read sub-feature parameter. After sending the Get Feature command (EEh) and following specific feature, the host may read out the P1-P4 sub- feature parameter data. Once sending the EEh command, the NAND device will remain in the Get Feature mode until next valid command is sent.

The Status Read command (70h) can be used to check the completion. To continue the read operation, a following read command (00h) to re-enable the data out is necessary.

Please refer to the following waveform of **Get Feature Operation** for details.

Figure 27. AC Waveforms for Get Feature (ONFI) Operation



6-14-3. Secure OTP (One-Time-Programmable) Feature

There is an OTP area which has thirty full pages (30 x 2,160-byte) guarantee to be good for system device serial number storage or other fixed code storage. The OTP area is a non-erasable and one-time-programmable area, which is default to “1” and allows whole page or partial page program to be “0”, once the OTP protection mode is set, the OTP area becomes read-only and cannot be programmed again.

The OTP operation is operated by the Set Feature/ Get Feature operation to access the OTP operation mode and OTP protection mode.

To check the NAND device is ready or busy in the OTP operation mode, either checking the R/B# or writing the Status Read command (70h) may collect the status.

To exit the OTP operation or protect mode, it can be done by writing 00h to P1 at feature address 90h.

OTP Read/Program Operation

To enter the OTP operation mode, it is by using the Set Feature command (EFh) and followed by the feature address (90h) and then input the 01h to P1 and 00h to P2-P4 of sub-Feature Parameter data(please refer to the sub-Feature Parameter table). After enter the OTP operation mode, the normal Read command (00h-30h) or Page program(80h-10h) command can be used to read the OTP area or program it. The address of OTP is located on the 02h-1Fh of page address.

Besides the normal Read command, the Random Data Output command (05h-E0h) can be used for read OTP data. However, the Cache Read command is not supported in the OTP area.

Besides the normal page program command, the Random Data Input command (85h) allows multi-data load in non-sequential address. After data load is completed, a program confirm command (10h) is issued to start the page program operation. The number of partial-page OTP program is 8 per each OTP page.

Figure 28. AC Waveforms for OTP Data Read

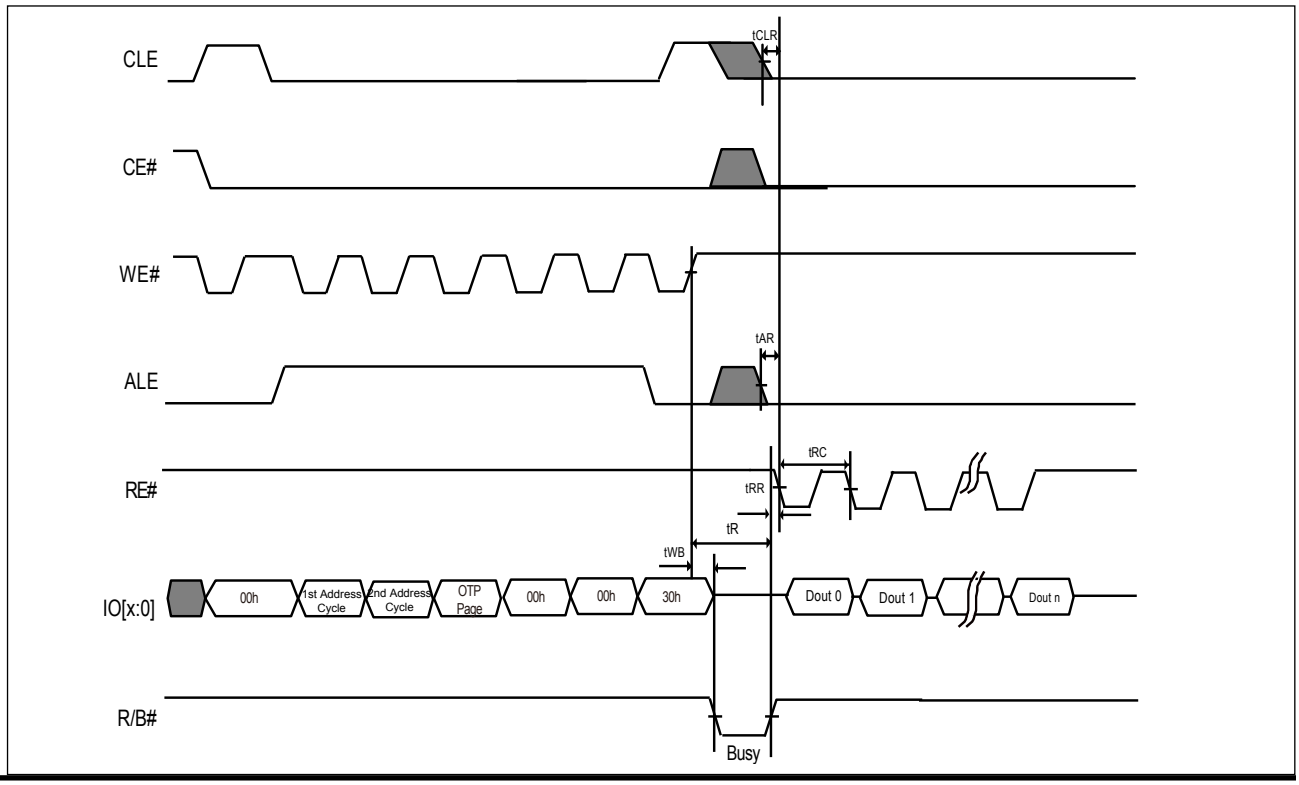


Figure 29. AC Waveforms for OTP Data Read with Random Data Output

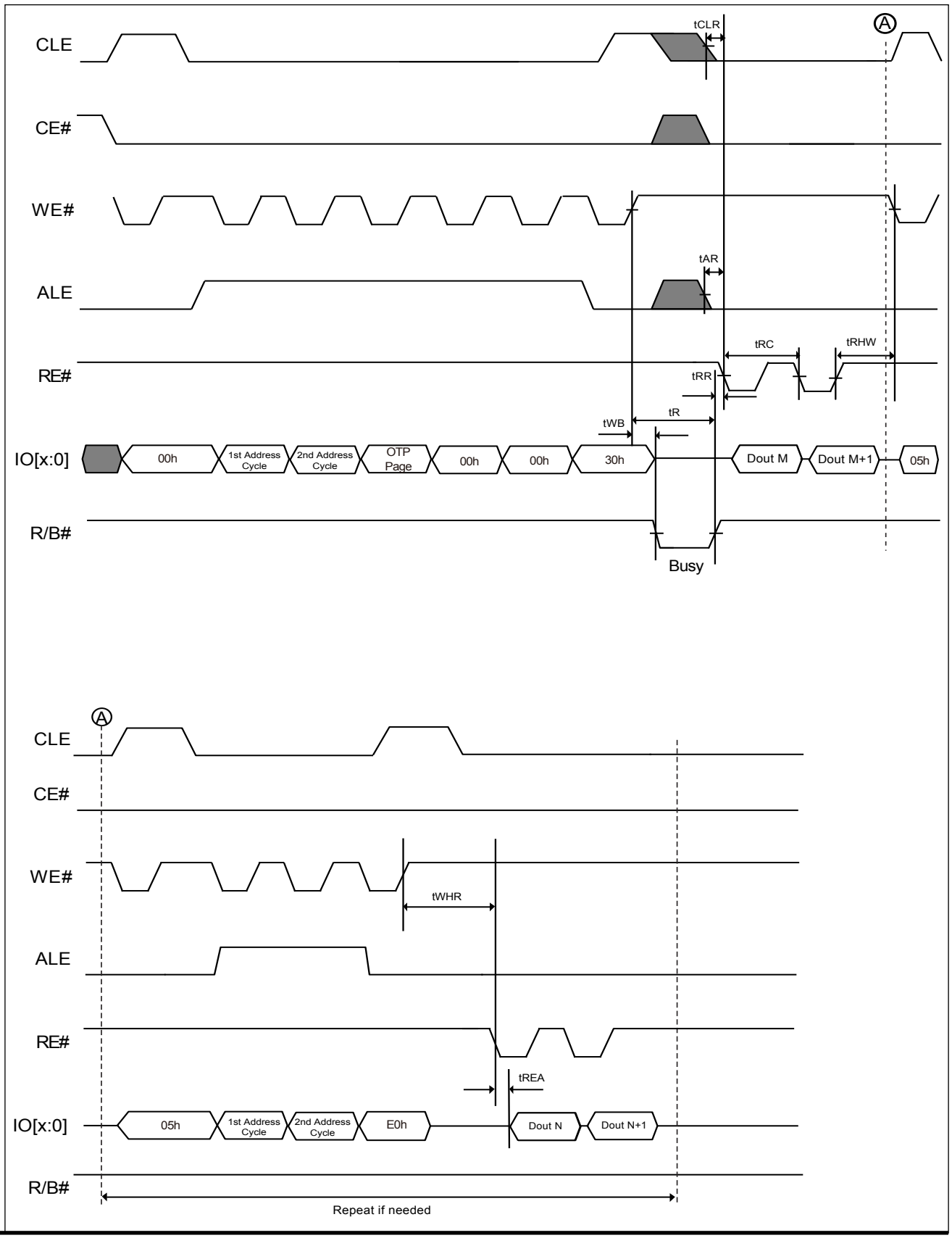


Figure 30. AC Waveforms for OTP Data Program

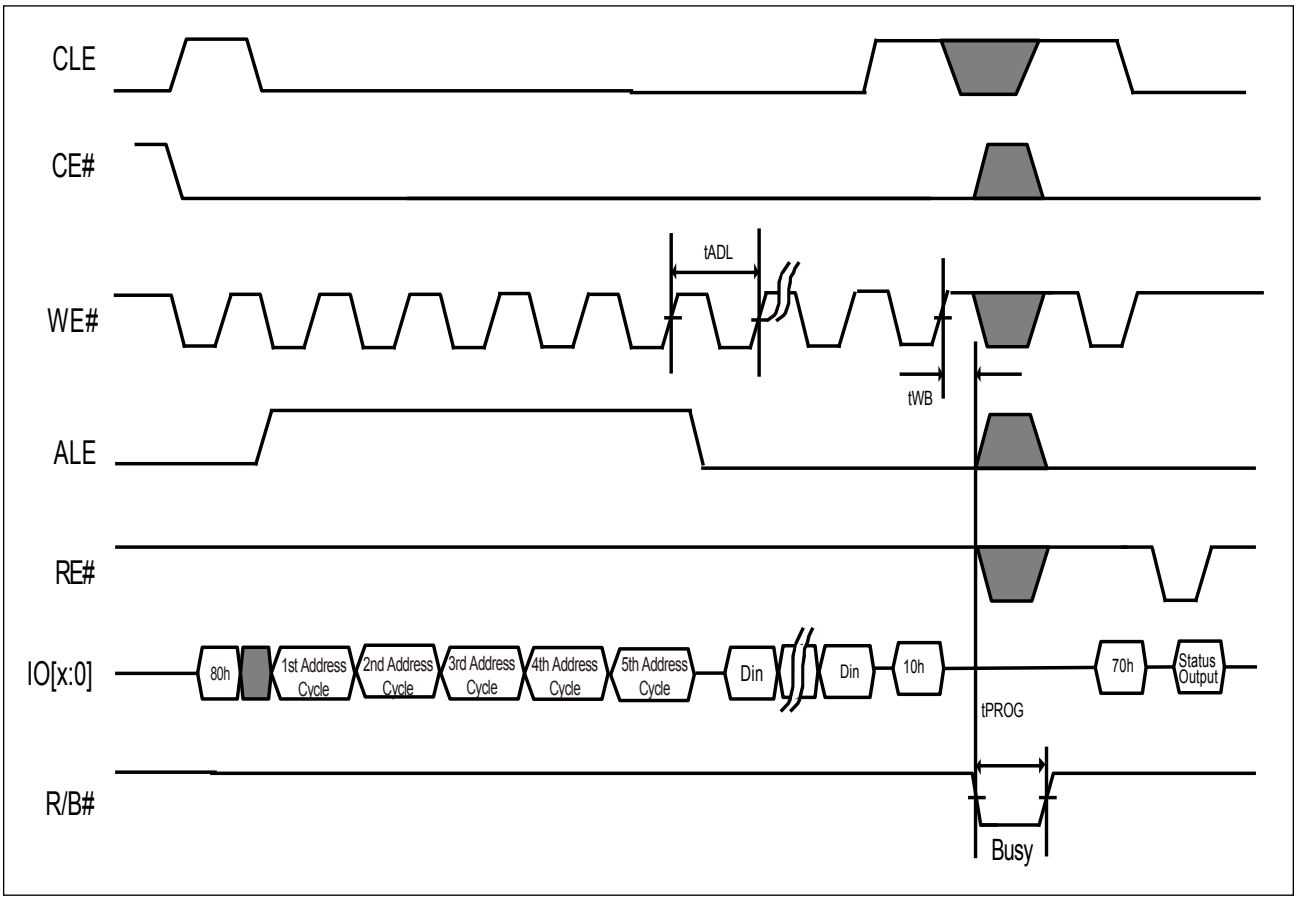
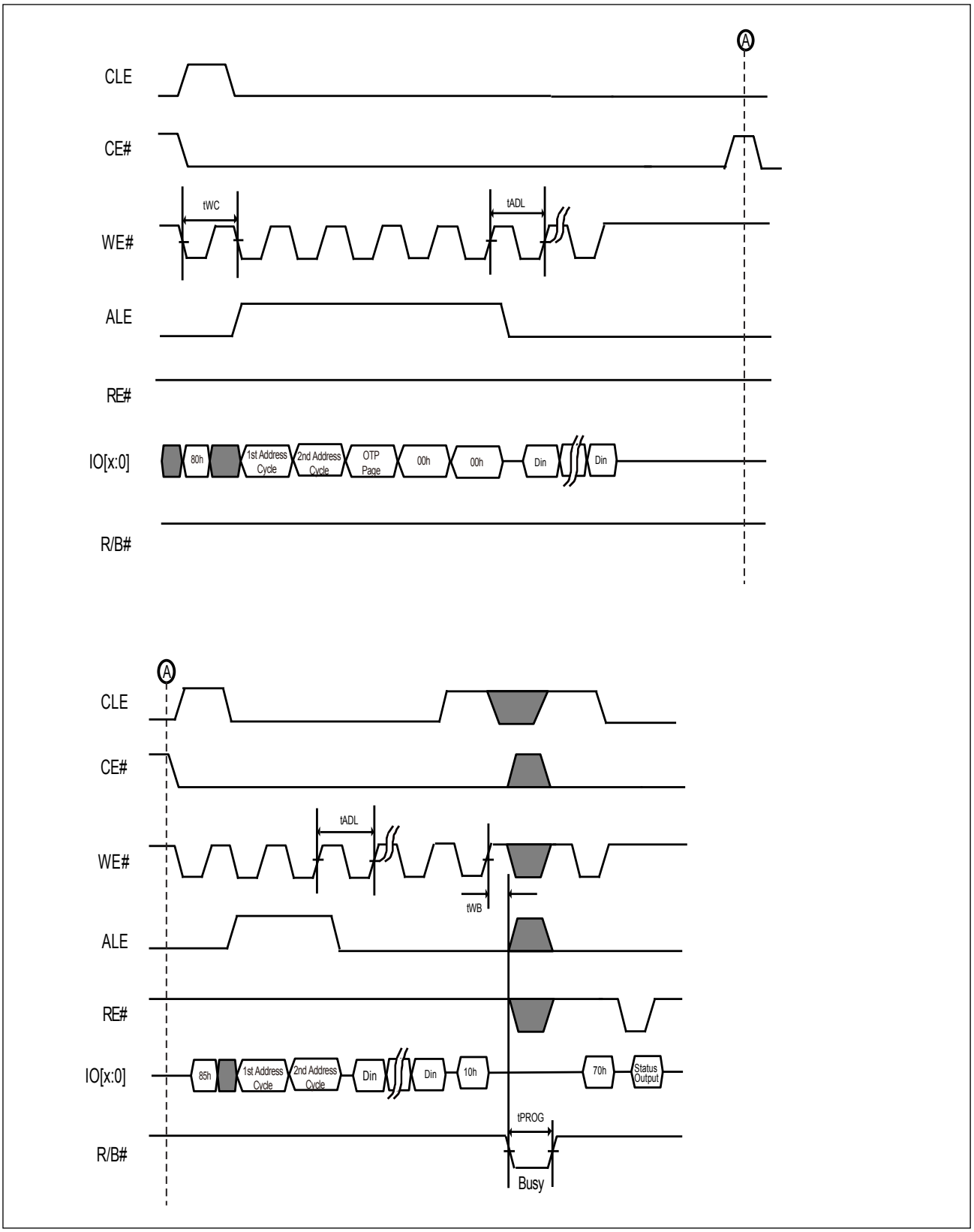


Figure 31. AC Waveforms for OTP Data Program with Random Data Input

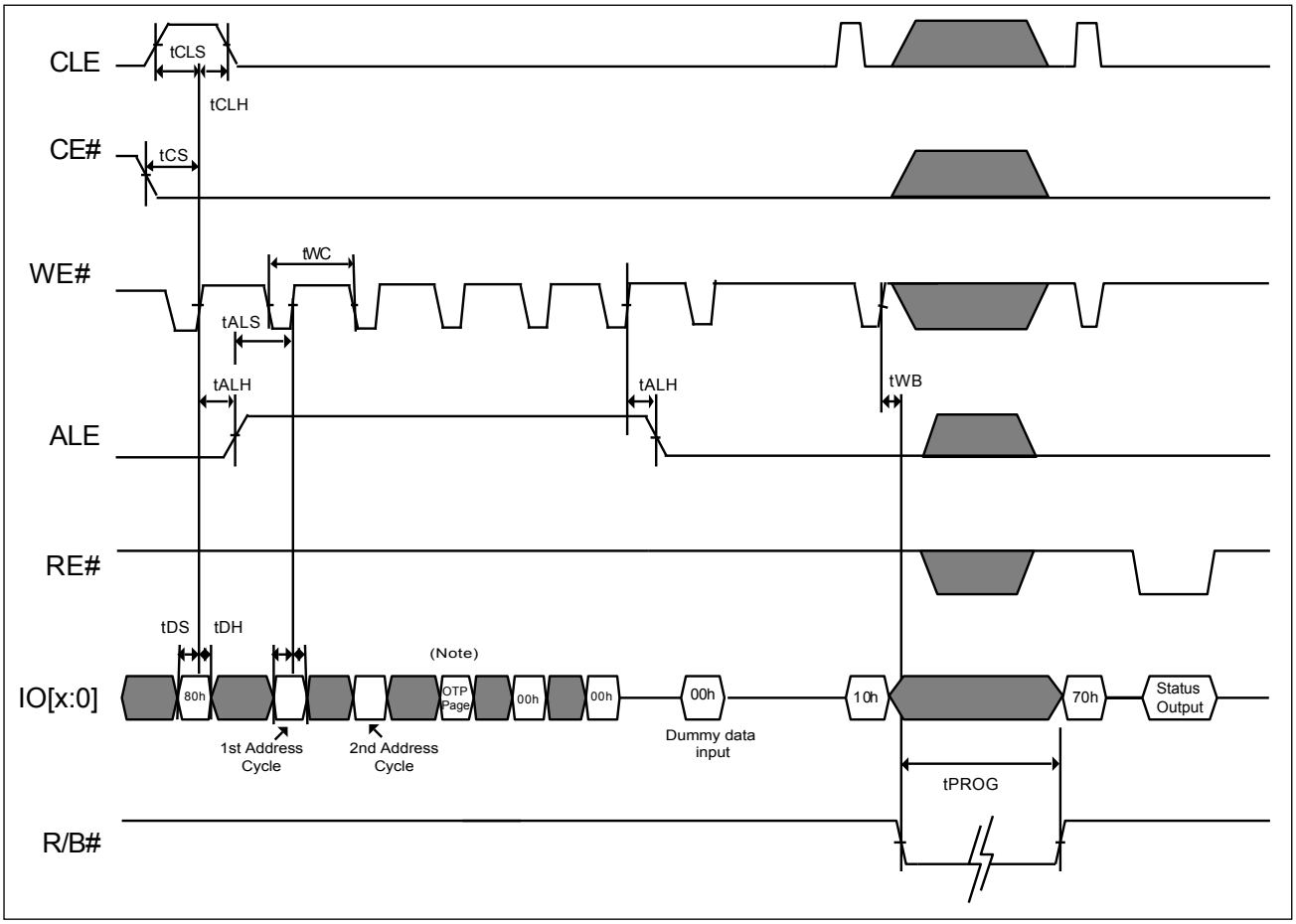


OTP Protection Operation

To prevent the further OTP data to be changed, the OTP protection mode operation is necessary. To enter the OTP protection mode, it can be done by using the Set Feature command (EFh) and followed by the feature address (90h) and then input the 03h to P1 and 00h to P2-P4 of sub-Feature Parameter data (please refer to the sub-Feature Parameter table). And then the normal page program command (80h-10h) with the address 00h before the 10h command is required.

The OTP Protection mode is operated by the whole OTP area instead of individual OTP page. Once the OTP protection mode is set, the OTP area cannot be programmed or unprotected again.

Figure 32. AC Waveforms for OTP Protection Operation



Note: *This adress cycle can be any value since the OTP protection protects the entire OTP area instead of individual OTP page.*

6-15. Two-Plane Operations

The 2Gb/4Gb NAND device is divided into two planes for performance improvement. In the two-plane operation, the NAND device may proceed the same type operation (for example: Program or Erase) on the two planes concurrent or overlapped by the two-plane command sets. The different type operations cannot be done in the two-plane operations; for example, it cannot be done to erase one plane and program the other plane concurrently.

The plane address A18 (for x8 bus) or A17 (for x16 bus) must be different from each selected plane address. The page address A12-A17(for x8 bus) or A11-A16 (for x16 bus) of individual plane must be the same for two-plane operation.

The Status Read command(70h) may check the device status in the two-plane operation, if the result is failed and then the Status Enhanced Read (78h) may check which plane is failed.

6-16. Two-plane Program (ONFI) and Two-plane Cache Program (ONFI)

The two-plane program command (80h-11h) may input data to cache buffer and wait for the final plane data input with command (80h-10h) and then transfer all data to NAND array. As for the two-plane cache program operation, after the prior two-plane program command (80h-11h) is the cache program command (80h-15h) for the overhead time reduction. Please refer to the waveforms of two-plane program and two-plane cache program for details. The random data input command (85h) can be also used in the two-plane program operation for changing the column address, please refer to the waveform of two-plane program with random data input.

Figure 33-1. AC Waveforms for Two-plane Program (ONFI)

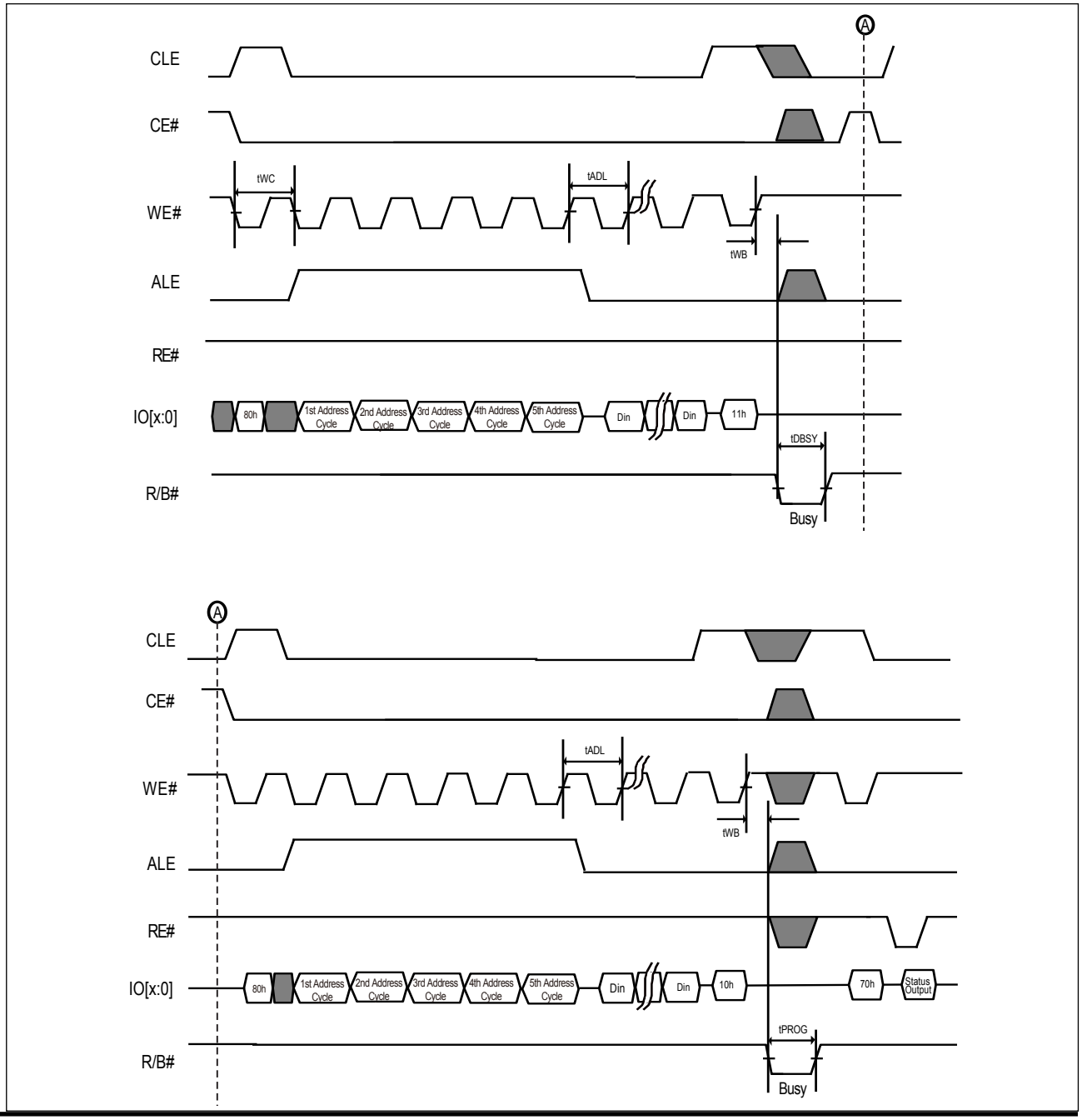


Figure 33-2. AC Waveforms for Page Program Random Data Two-plane (ONFI)

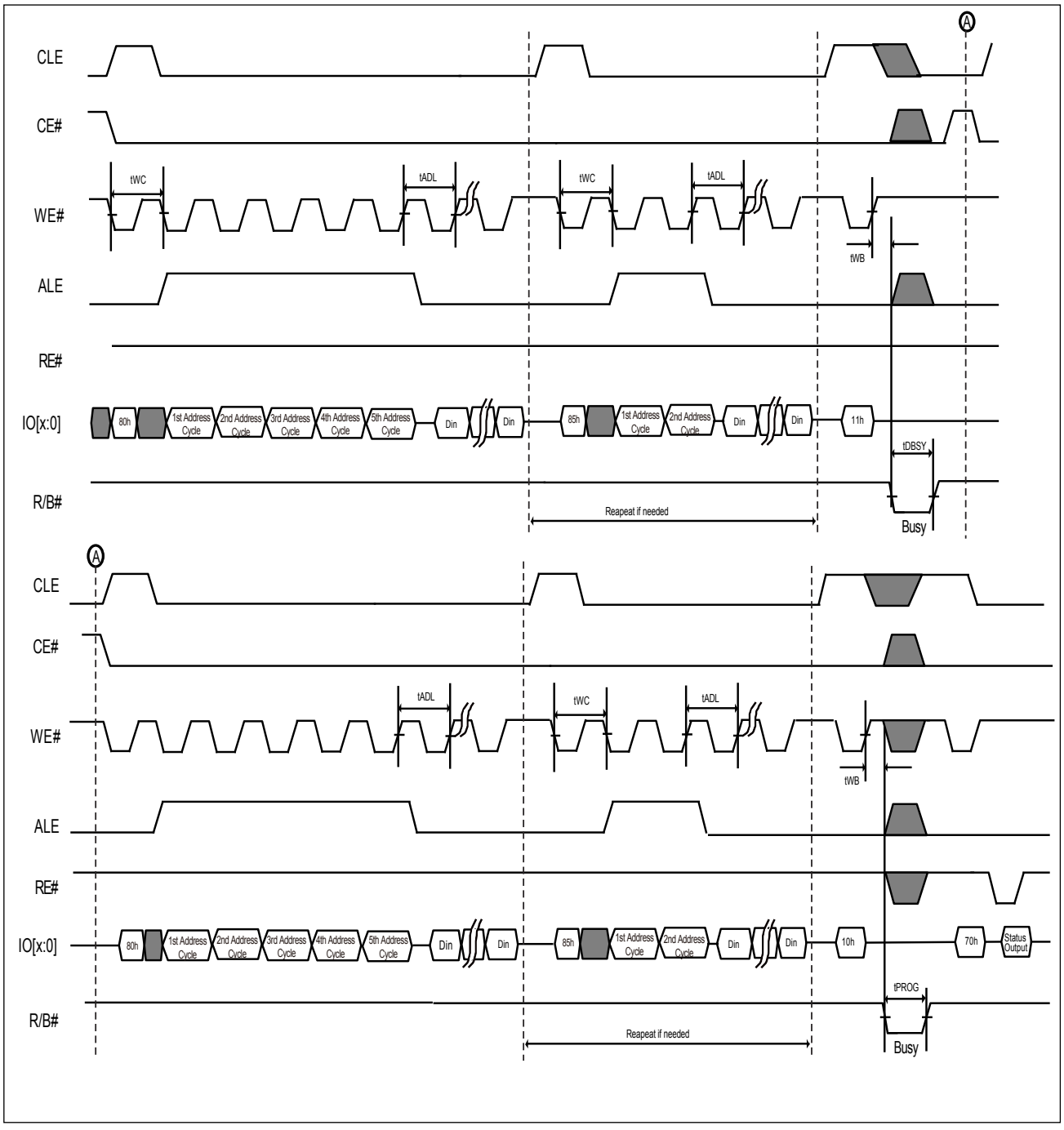
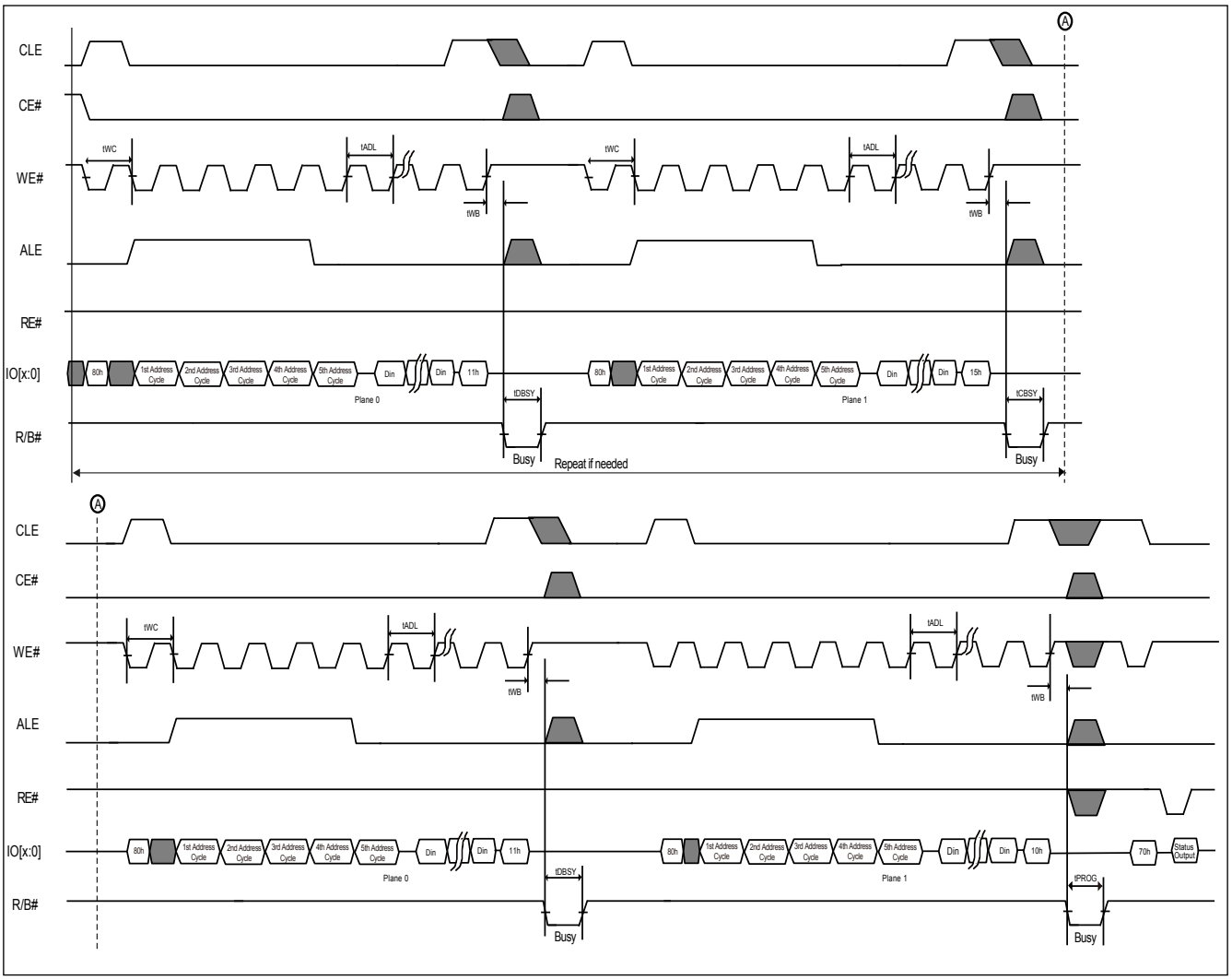


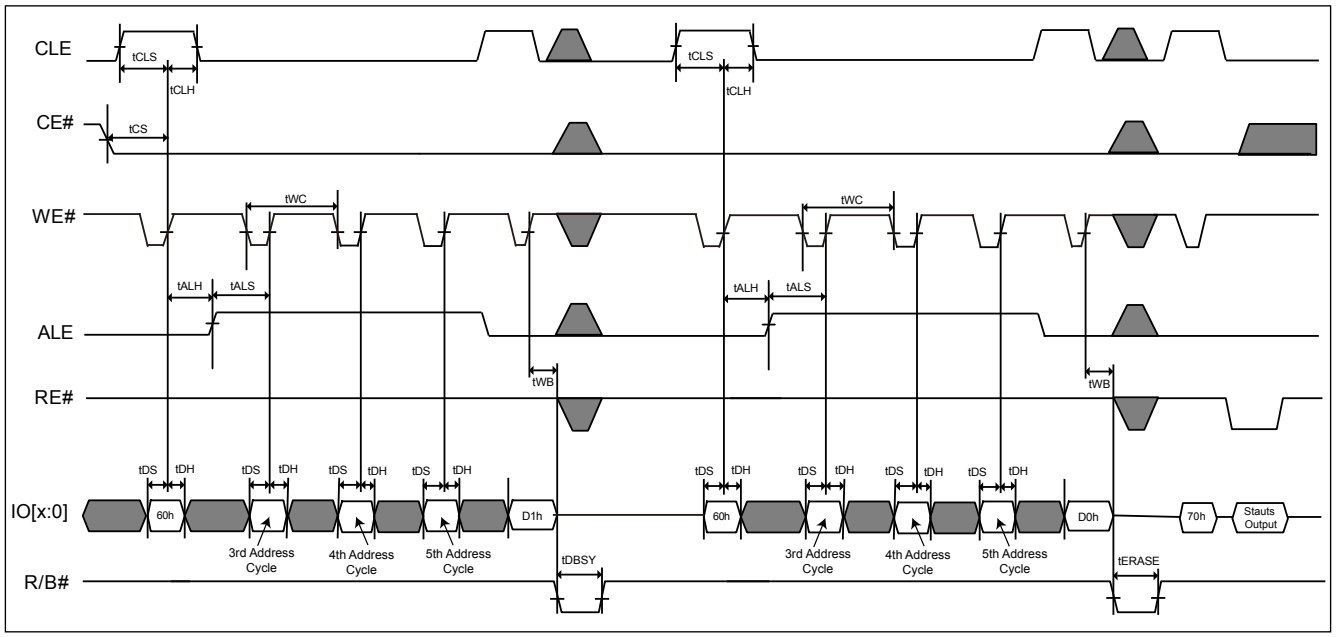
Figure 34. AC Waveforms for Two-plane Cache Program (ONFI)



6-17. Two-plane Block Erase (ONFI)

The two-plane erase command (60h-D1h) may erase the selected blocks in parallel from each plane, with setting the 1st and 2nd block address by (60h-D1h) & (60h-D0h) command and then erase two selected blocks from NAND array. Please refer to the waveforms of two-plane erase for details.

Figure 35. AC Waveforms for Two-plane Erase (ONFI)

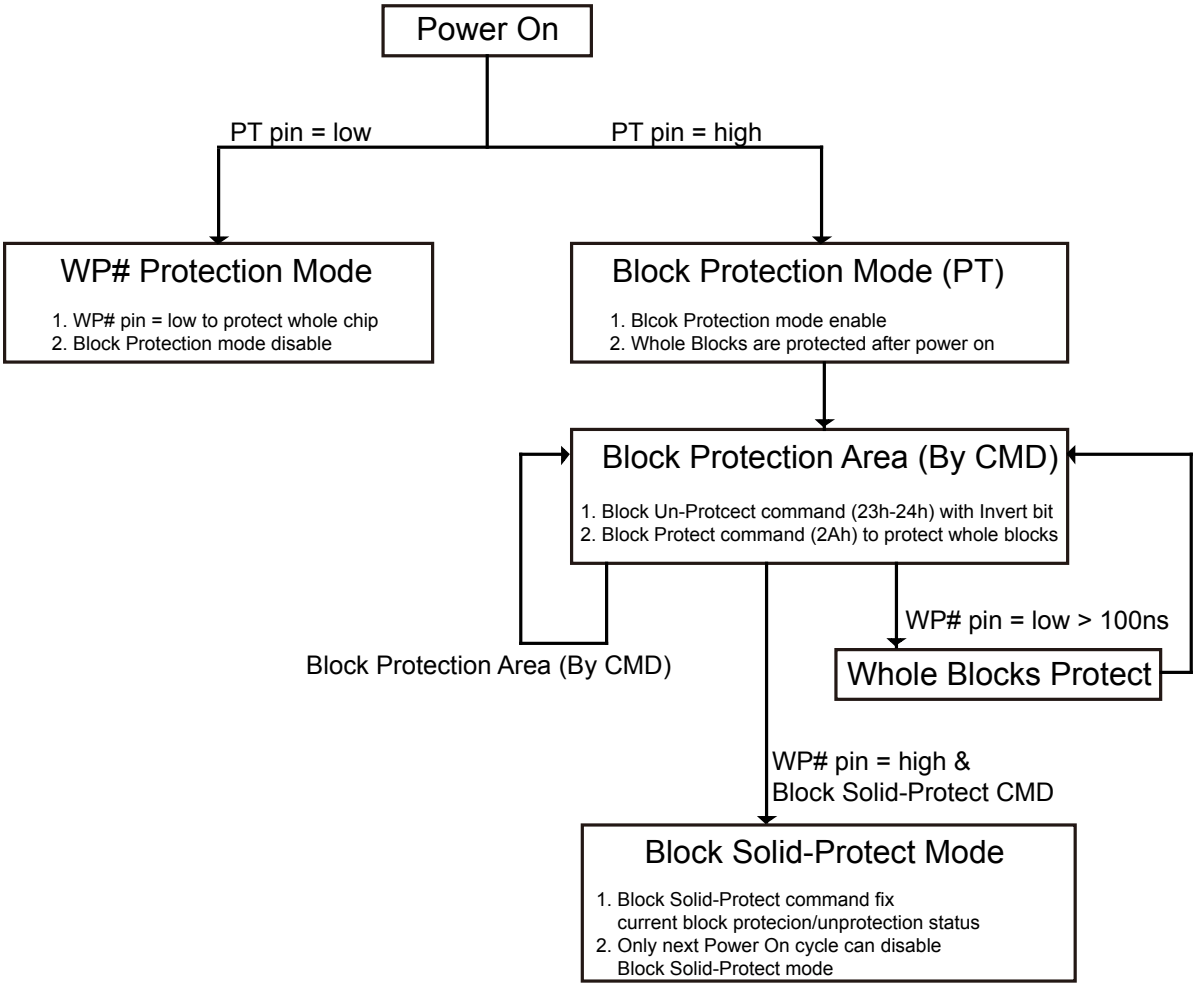


6-18. Block Protection

The block protect operation can protect the whole chip or selected blocks from erasing or programming. Through the PT pin at power-on stage, it decides the block protect command is enabled or disabled. At power-on, if the PT pin is connected to high, the related Block Protect command sets are enabled; in contrast, if the PT pin is low, all the block protect command sets are disabled. If the PT pin is connected to high at power-on, all the blocks are default to be protected from programming/erasing even the WP# is disabled, the block un-protect command is necessary to un-protect those selected blocks before those selected blocks to be updated. Once the selected blocks are un-protected, those blocks can be protected again. Besides the Block protect operation, there is “Block Solid-Protect” command (2Ch) may provide a solid block protection; once the block is solid-protected, the block is protected from programming or erasing and cannot be up-protected until next power cycle.

The functional block protection flow chart is shown in the figure below:

Figure 36. Block Protection Flow Chart



6-18-1. Block Un-Protect

When PT pin is connected to high at the power-on stage, all blocks are default to be protected from programming or erasing. The Block Un-Protect command set (23h-24h) may define the range of blocks to be un-protected. The Block Un-Protect Lower command (23h) may set the lower boundary address and followed by the Block Un-Protect Upper command (24h) setting the upper boundary address and the invert-bit to define the un-protect blocks range. The invert-bit defines the un-Protect block area, if the invert-bit is set to "0" which sets the un-Protected area is within the upper and lower boundary address; in contrast, the bit is set to "1" which means the un-protected area is outside the upper and lower boundary address. Please refer to the waveforms below for details.

Table 7-1. Address Cycle Definition of Block Un-Protect (For x8)

Address Cycle	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Block Address 1	A19	A18	L	L	L	L	L	Invert Bit[1]
Block Address 2	A27	A26	A25	A24	A23	A22	A21	A20
Block Address 3	L	L	L	L	L	L	A29	A28

Note 1*. The Invert bit is set by 24h command to decide the Un-protect range is inside or outside of the boundary. The bit can be H/L for 23h command.*

Table 7-2. Address Cycle Definition of Block Un-Protect (For x16)

Address Cycle	IO15-IO8	IO7	IO6	IO5	IO4	IO3	IO2	IO1	IO0
Block Address 1	L	A18	A17	L	L	L	L	L	Invert Bit [1]
Block Address 2	L	A26	A25	A24	A23	A22	A21	A20	A19
Block Address 3	L	L	L	L	L	L	L	A28	A27

Note 1*. The Invert bit is set by 24h command to decide the Un-protect range is inside or outside of the boundary. The bit can be H/L for 23h command.*

Figure 37. Invert-Bit to Define Un-Protected Area Options

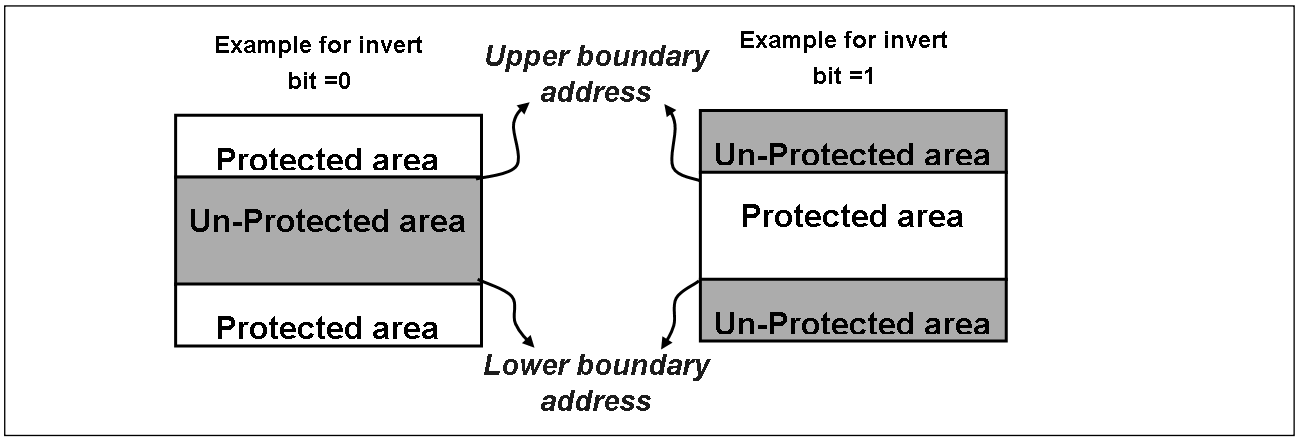
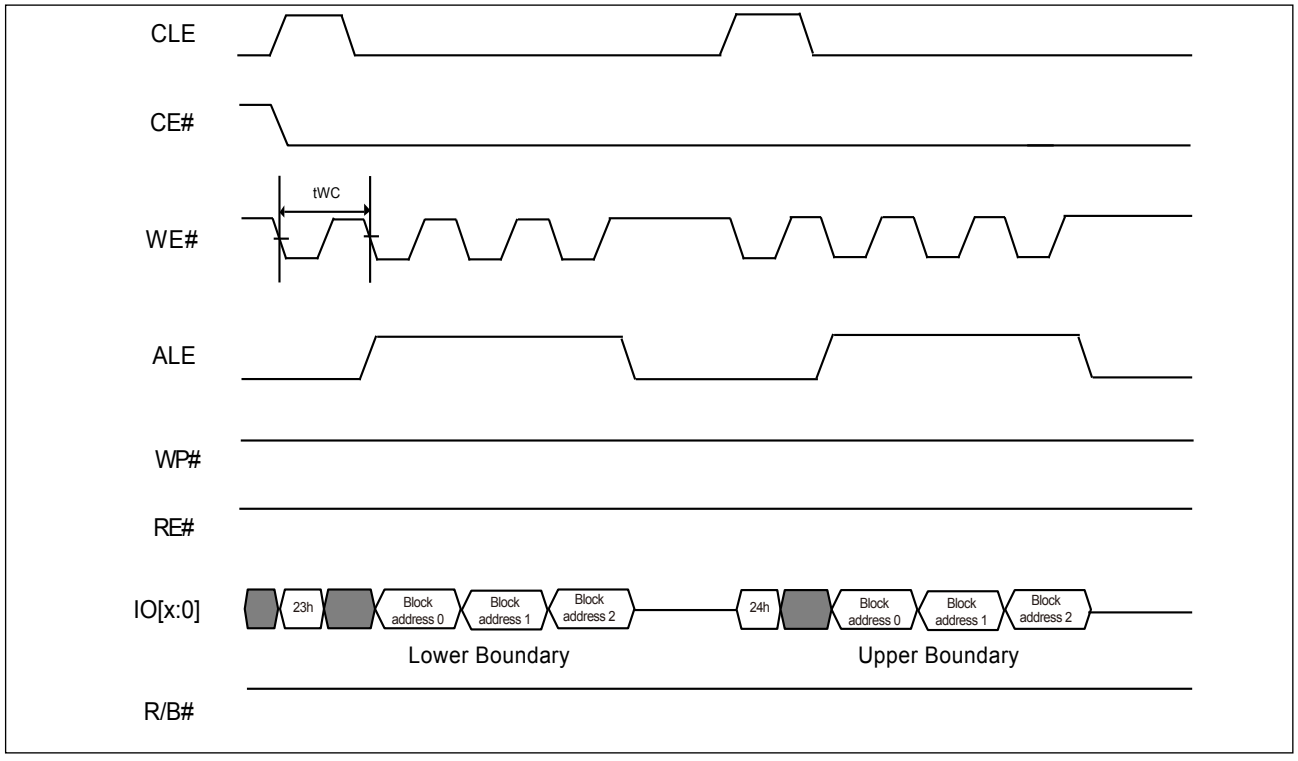


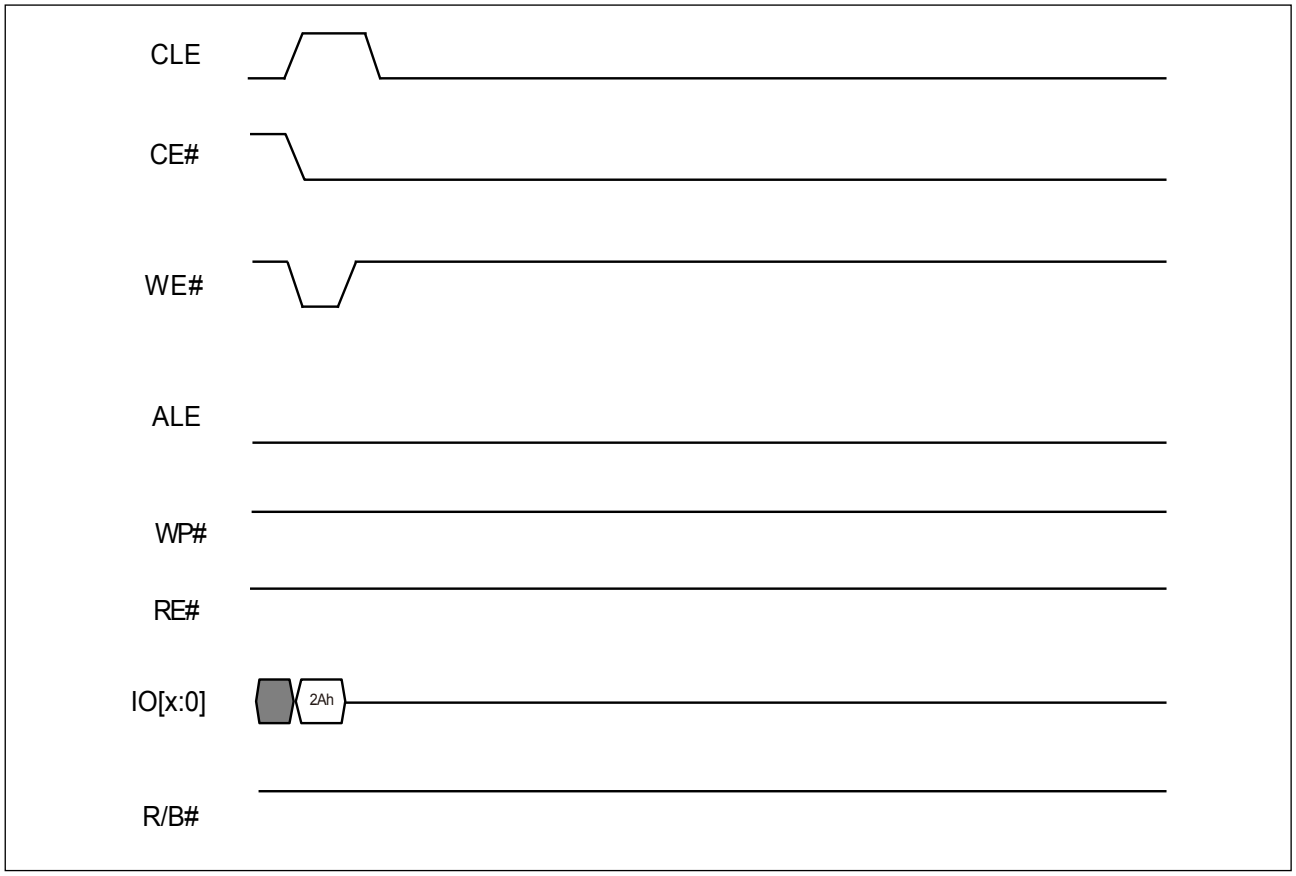
Figure 38. AC Waveforms for Block Unprotection



6-18-2. Block Protect

When some blocks are un-protected by the Block Un-Protect command set (23h-24h), those blocks can be protected again from the program/erase operation by writing the Block Protect command (2Ah), which may protect all blocks together.

Figure 39. AC Waveforms for Block Protection

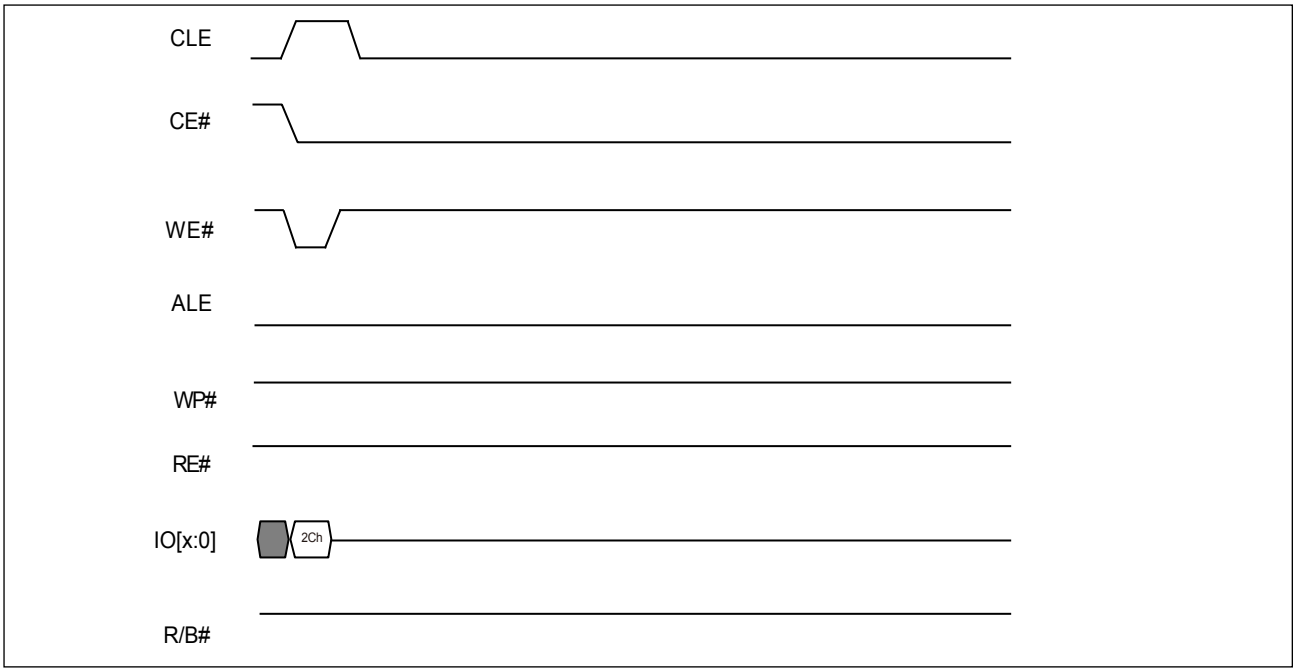


6-18-3. Block Solid-Protect

The Block Solid-Protect Command (2Ch) may firmly maintain the previous block protect status; which means the protected blocks cannot be un-protected and the un-protected blocks cannot be protected. Once the Block Solid-Protect command is set, only a new power cycle may change the states of blocks protection/un-protection. The WP# needs to be connected to high before writing the Block Solid-Protect command, and the command is valid only when the PT pin is connected to high.

The Block Solid-Protect command was issued, only the un-protected blocks may accept the program/erase operation. To program or erase the protected block, the R/B# keeps low for the time of tLPSY, and the Status Read command (70h) may get the 60h result.

Figure 40. AC Waveforms for Block Solid-Protect



6-18-4. Block Protection Status Read

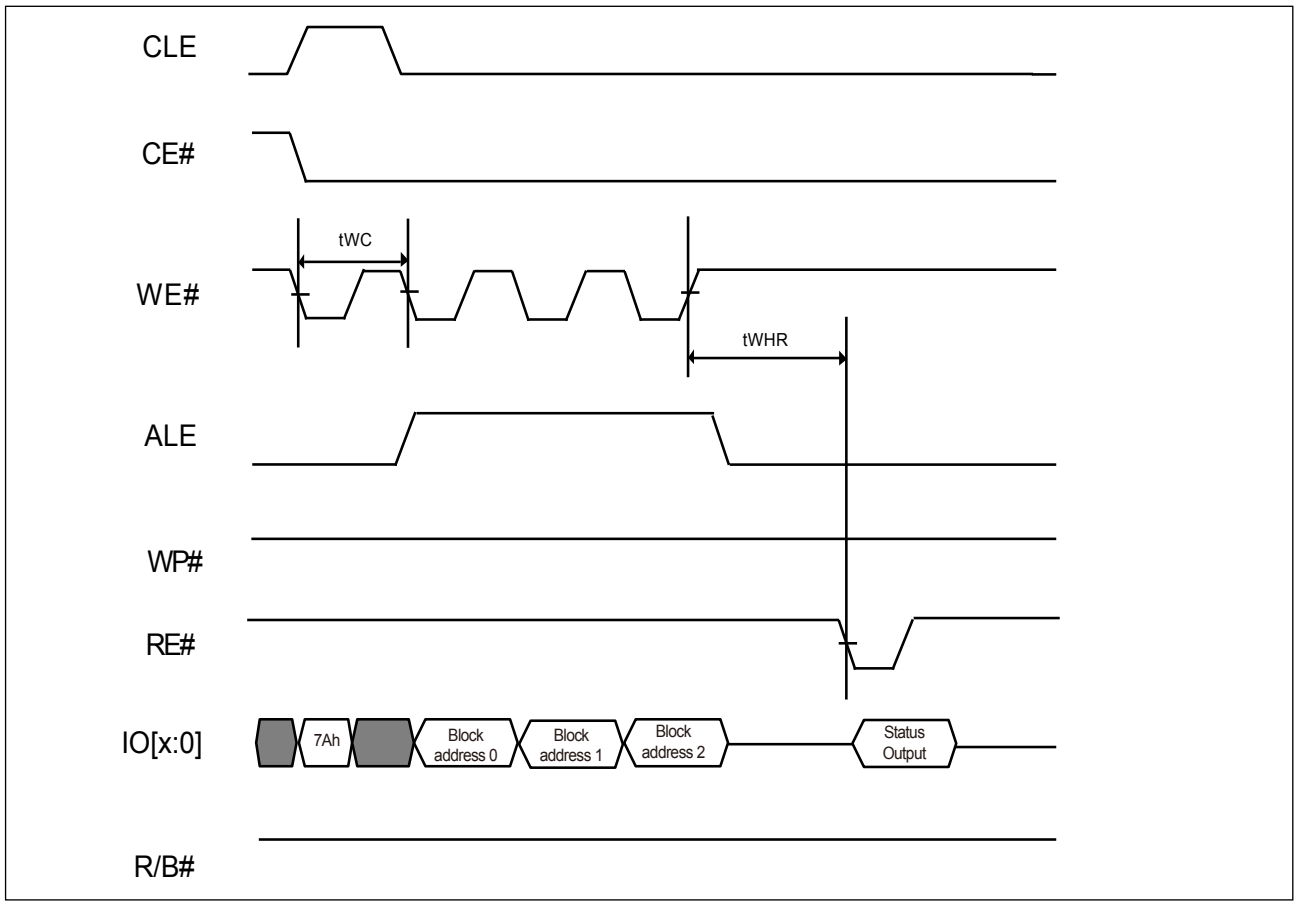
The Block Protection Status Read command (7Ah) may check the protect/un-protect status of individual blocks. The address cycle is referred to **Table 7-1.** and **7-2. Address Cycle Definition of Block Un-Protect**.

Table 8. The Block-Protection Status Output

Block-Protection Status	IO[15:3] or IO[7:3]	IO2(PT#)	IO1(SP#)	IO0(SP)
Block is protected, and device is solid-protected	x	0	0	1
Block is protected, and device is not solid-protected	x	0	1	0
Block is un-protected, and device is solid-protected	x	1	0	1
Block is un-protected, and device is not solid-protected	x	1	1	0

Note: *PT stands for Block Protection, SP stands for Solid-Protection.*

Figure 41. AC Waveforms for Block Protection Status Read



7. PARAMETERS

7-1. ABSOLUTE MAXIMUM RATINGS

Temperature under Bias	-50°C to +125°C
Storage temperature	-65°C to +150°C
All input voltages with respect to ground (Note 2)	-0.6V to 2.4V
VCC supply voltage with respect to ground (Note 2)	-0.6V to 2.4V
ESD protection	>2000V

Notes:

1. *The reliability of device may be impaired by exposing to extreme maximum rating conditions for long range of time.*
2. *Permanent damage may be caused by the stresses higher than the "Absolute Maximum Ratings" listed.*
3. *During voltage transitions, all pins may overshoot to VCC +1.0V or -1.0V for period up to 20ns. See the two waveforms as below.*

Figure 42. Maximum Negative Overshoot Waveform

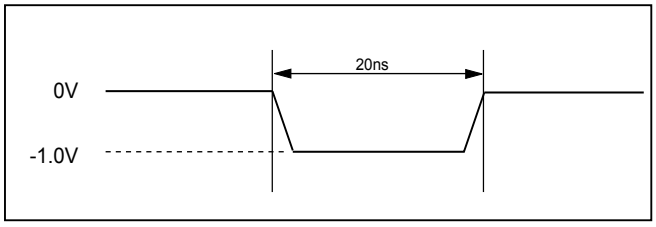


Figure 43. Maximum Positive Overshoot Waveform

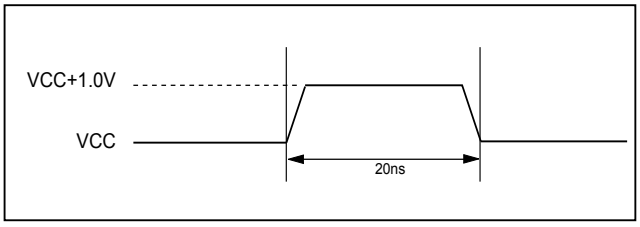


Table 9. Operating Range

Temperature	VCC	Tolerance
-40°C to +85°C	+1.8V	1.7 ~ 1.95V

Table 10. DC Characteristics

Symbol	Parameter	Test Conditions	Min.	Typical	Max.	Unit	Notes
VIL	Input low level		-0.3		0.2VCC	V	
VIH	Input high level		0.8VCC		VCC + 0.3	V	
VOL	Output low voltage	IOL= 100uA, VCC= VCC Min.			0.1	V	1
VOH	Output high voltage	IOH= -100uA, VCC= VCC Min.	VCC-0.1V			V	1
ISB1	VCC standby current (CMOS)	CE# = VCC -0.2V, WP# = 0/VCC		10	50	uA	
ISB2	VCC standby current (TTL)	CE# = VIH Min., WP# = 0/VCC			1	mA	
IST	Staggered power-up current	Rise time = 1ms, Line capacitance = 0.1uF		20	30	mA	2
ICC1	VCC active current (Sequential Read)	tRC Min., CE# = VIL, IOUT= 0mA		23	30	mA	
ICC2	VCC active current (Program)			23 *(Note3)*	30	mA	
ICC3	VCC active current (Erase)			15	30	mA	
ILI	Input leakage current	VIN= 0 to VCC Max.			+/- 10	uA	
ILO	Output leakage current	VOUT= 0 to VCC Max.			+/- 10	uA	
ILO (R/B#)	Output current of R/B# pin	VOL=0.2V	3	4		mA	1

Notes:

1. *The test can be initiated after VCC goes VCC (min) and performed under the condition of 1mS interval.*
2. *It is necessary to set ILO(R/B#) to be relaxed if the strength of R/B# pull-down is not set to full. And the VOL/VOH will be relaxed if the strength of I/O drive is not full.*
3. *The typical program current (ICC2) for two-plane program operation is 28mA.*

Table 11. Capacitance

TA = +25°C, F = 1 MHz

Symbol	Parameter	Typ.	Max.	Units	Conditions
CIN	Input capacitance		10	pF	VIN = 0 V
COUT	Output capacitance		10	pF	VOUT = 0 V

Table 12. AC Testing Conditions

Testing Conditions	Value	Unit
Input pulse level	0 to VCC	V
Output load capacitance	1TTL+CL(30)	pF
Input rise and fall time	2.5	ns
Input timing measurement reference levels	VCC/2	V
Output timing measurement reference levels	VCC/2	V

Table 13. Program and Erase Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
tPROG	Page programming time		320	600	us	
tCBSY (Program)	Dummy busy time for cache program		5	700	us	
tRCBSY (Read)	Dummy busy time for cache read		2	25	us	
tDBSY	The busy time for two-plane program/erase operation		0.5	1	us	
tFEAT	The busy time for Set Feature/ Get Feature			1	us	
tOBSY	The busy time for OTP program at OTP protection mode			30	us	
tPBSY	The busy time for program/erase at protected blocks			3	us	
NOP	Number of partial program cycles in same page			4	cycles	
tERASE (Block)	Block erase time		1	3.5	ms	

Table 14. AC Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
tCLS	CLE setup time	10			ns	1
tCLH	CLE hold time	5			ns	1
tCS	CE# setup time	20			ns	1
tCH	CE# hold time	5			ns	1
tWP	Write pulse width	12			ns	1
tALS	ALE setup time	10			ns	1
tALH	ALE hold time	5			ns	1
tDS	Data setup time	10			ns	1
tDH	Data hold time	5			ns	1
tWC	Write cycle time	25			ns	1
tWH	WE# high hold time	10			ns	1
tADL	Last address latched to data loading time during program operations	70			ns	1
tWW	WP# transition to WE# high	100			ns	1
tRR	Read to RE# falling edge	20			ns	1
tRP	Read pulse width	12			ns	1
tRC	Read cycle time	25			ns	1
tREA	RE# access time (serial data access)			22	ns	1
tCEA	CE# access time			25	ns	1
tRLOH	RE#-low to data hold time (EDO)	3			ns	
tOH	Data output hold time	15			ns	1
tRHZ	RE#-high to output-high impedance			60	ns	1
tCHZ	CE#-high to output-high impedance			50	ns	1
tCOH	CE# high to output hold time	15			ns	
tREH	RE# high hold time	10			ns	1
tIR	Output high impedance to RE# falling edge	0			ns	1
tRHW	RE# high to WE# low	60			ns	1
tWHR	WE# high to RE# low	80			ns	1
tR	The data transfering from array to buffer			25	us	1,2
tWB	WE# high to busy			100	ns	1
tCLR	CLE low to RE# low	10			ns	1
tAR	ALE low to RE# low	10			ns	1
tRST	Device reset time (Idle/ Read/ Program/ Erase)			5/5/10/500	us	1

Notes:

1*. ONFI Mode 4 compliant*

2*. The timing spec needs to be relaxed if the I/O drive strength is not full.*

8. OPERATION MODES: LOGIC AND COMMAND TABLES

Address input, command input and data input/output are managed by the CLE, ALE, CE#, WE#, RE# and WP# signals, as shown in **Table 15. Logic Table** below.

Program, Erase, Read and Reset are four major operations modes controlled by command sets, please refer to **Table 16-1** and **16-2**.

Table 15. Logic Table

Mode	CE#	RE#	WE#	CLE	ALE	WP#
Address Input (Read Mode)	L	H	↑	L	H	X
Address Input (Write Mode)	L	H	↑	L	H	H
Command Input (Read Mode)	L	H	↑	H	L	X
Command Input (Write Mode)	L	H	↑	H	L	H
Data Input	L	H	↑	L	L	H
Data Output	L	↓	H	L	L	X
During Read (Busy)	X	H	H	L	L	X
During Programming (Busy)	X	X	X	X	X	H
During Erasing (Busy)	X	X	X	X	X	H
Program/Erase Inhibit	X	X	X	X	X	L
Stand-by	H	X	X	X	X	0V/VCC

Notes:

1. *H = VIH; L = VIL; X = VIH or VIL*
2. *WP# should be biased to CMOS high or CMOS low for stand-by.*

Table 16-1. HEX Command Table

	First Cycle	Second Cycle	Acceptable While Busy
Read Mode	00H	30H	
Random Data Input	85H	-	
Random Data Output	05H	E0H	
Cache Read Random	00H	31H	
Cache Read Sequential	31H	-	
Cache Read End	3FH	-	
ID Read	90H	-	
Parameter Page Read (ONFI)	ECH	-	
Unique ID Read (ONFI)	EDH	-	
Set Feature (ONFI)	EFH	-	
Get Feature (ONFI)	EEH	-	
Reset	FFH	-	V
Page Program	80H	10H	
Cache Program	80H	15H	
Block Erase	60H	D0H	
Block Un-Protect Lower[2]	23H	-	
Block Un-Protect Upper[2]	24H	-	
Block Protect[2]	2AH	-	
Block Solid-Protect[2]	2CH	-	
Status Read	70H	-	V
Status Enhanced Read (ONFI)[1]	78H	-	V
Block Protection Status Read[2]	7AH	-	

Table 16-2. Two-plane Command Set

	First Cycle	Second Cycle	Third Cycle	Fourth Cycle
Two-plane Program (ONFI)	80H	11H	80H	10H
Two-plane Cache Program (ONFI)	80H	11H	80H	15H
Two-plane Block Erase (ONFI)	60H	D1H	60H	D0H

Caution: *None of the undefined command inputs can be accepted except for the command set in the above table.*

Notes: ***1.*** *The command set is not valid for 1Gb.*

2. *The IO15-IO8 should be "0" while writing command code for the x16 NAND device.*

8-1. R/B#: Termination for The Ready/Busy# Pin (R/B#)

The R/B# is an open-drain output pin and a pull-up resistor is necessary to add on the R/B# pin. The R/B# outputs the ready/busy status of read/program/ erase operation of the device. When the R/B# is at low, the device is busy for read or program or erase operation. When the R/B# is at high, the read/program/erase operation is finished.

Rp Value Guidence

The rise time of the R/B# signal depends on the combination of Rp and capacitive loading of the R/B# circuit. It is approximately two times constants (Tc) between the 10% and 90% points on the R/B# waveform.

$$T_C = R \times C$$

Where R = R_p (Resistance of pull-up resistor), and C = C_L (Total capacitive load)

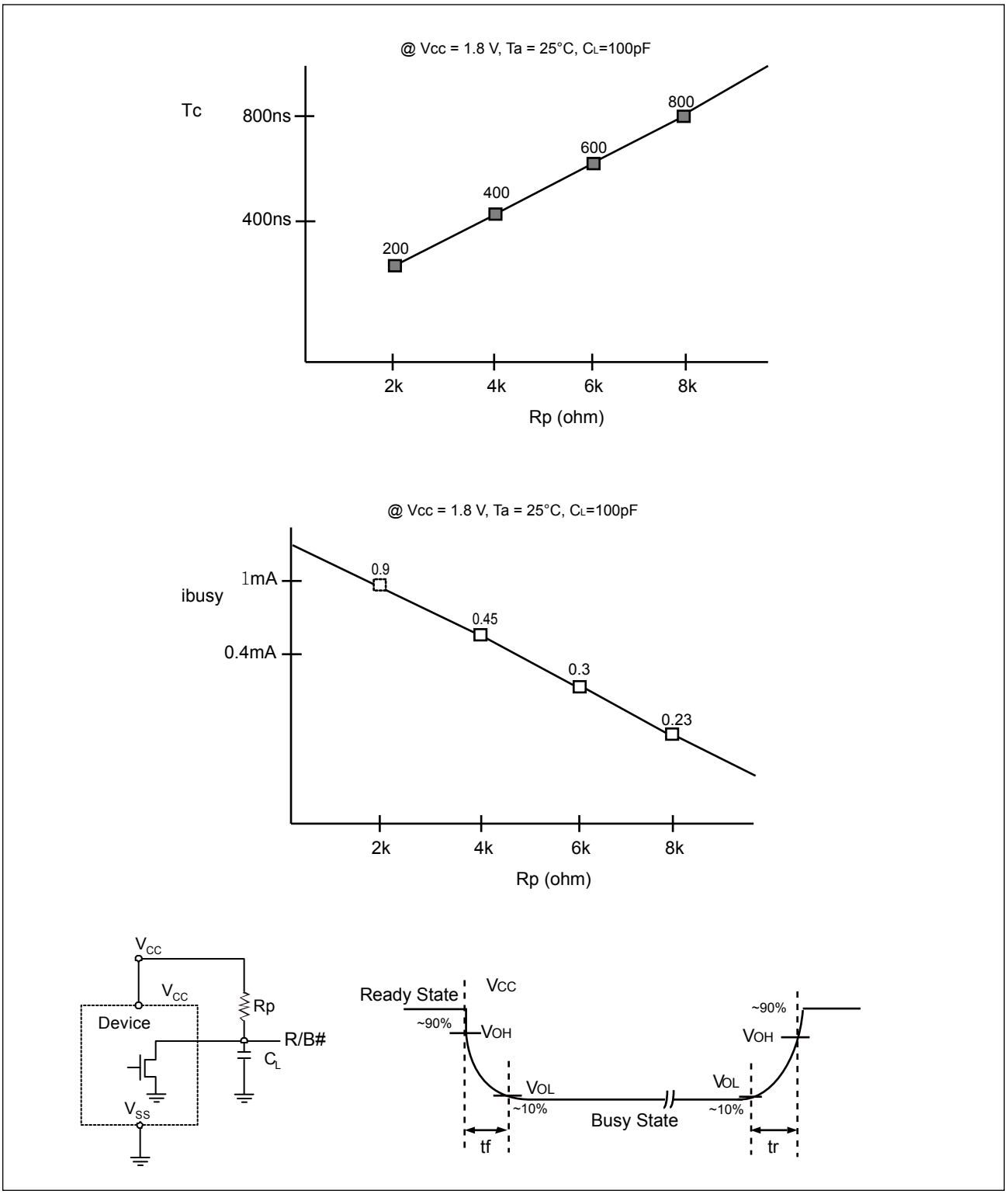
The fall time of the R/B# signal majorly depends on the output impedance of the R/B# signal and the total load capacitance.

$$Rp\ (Min.) = \frac{Vcc\ (Max.) - VOL\ (Max.)}{I_{OL} + \Sigma I_L}$$

Notes:

1. *Considering of the variation of device-by-device, the above data is for reference to decide the resistor value.*
2. *Rp maximum value depends on the maximum permissible limit of tr.*
3. *IL is the total sum of the input currents of all devices tied to the R/B pin.*

Figure 44. R/B# Pin Timing Information



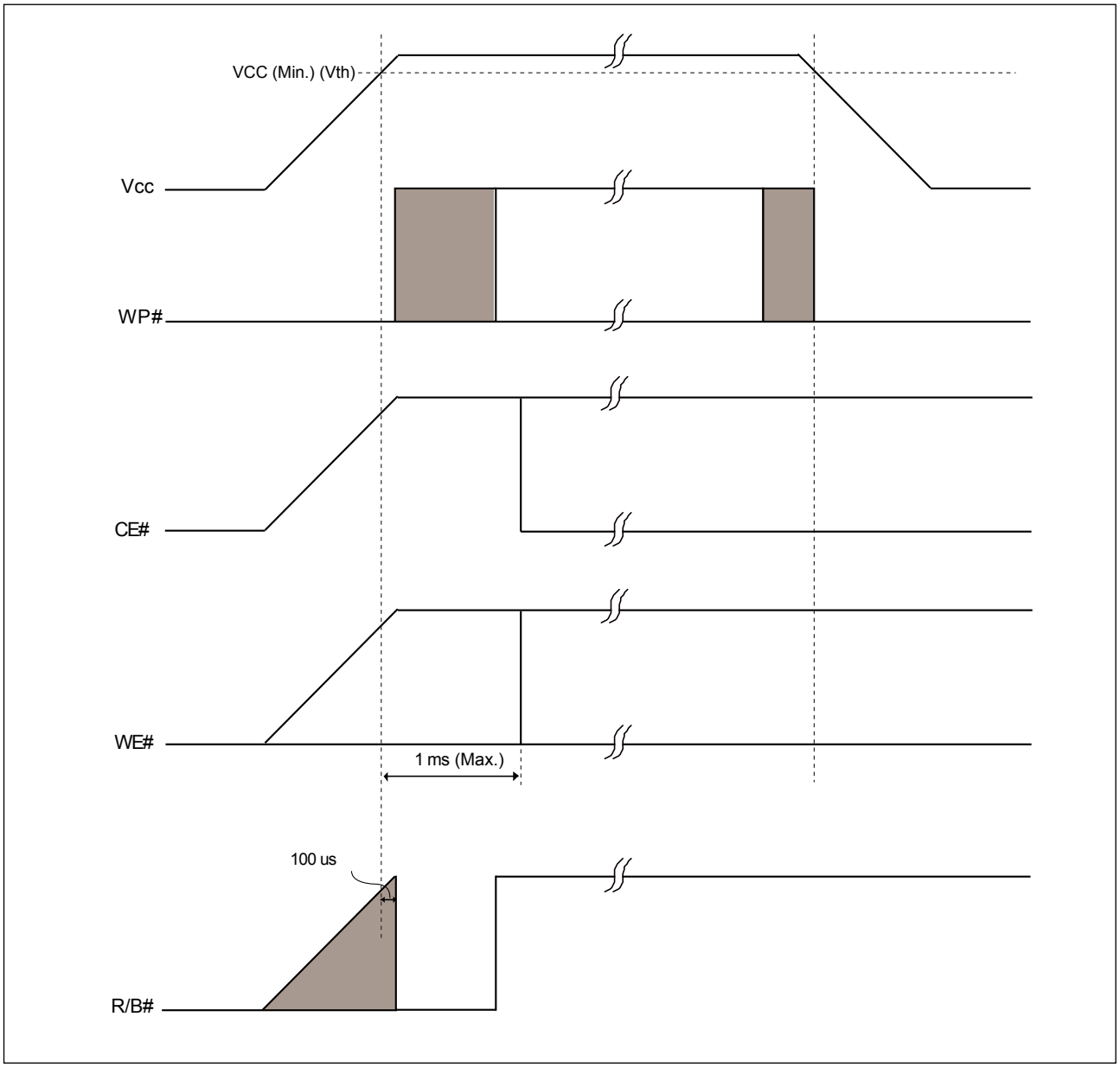
8-2. Power On/Off Sequence

After the Chip reaches the power on level (Vth = Vcc min.), the internal power on reset sequence will be triggered. During the internal power on reset period, no any external command is accepted. There are two ways to identify the termination of the internal power on reset sequence. Please refer to **Figure 43. Power On/Off Sequence**.

- R/B# pin
- Wait 1 ms

During the power on and power off sequence, it is recommended to keep the WP# = Low for internal data protection.

Figure 45. Power On/Off Sequence



8-2-1. WP# Signal

WP# going Low can cause program and erase operations automatically reset.

The enabling & disabling of the both operations are as below:

Figure 46-1. Enable Programming of WP# Signal

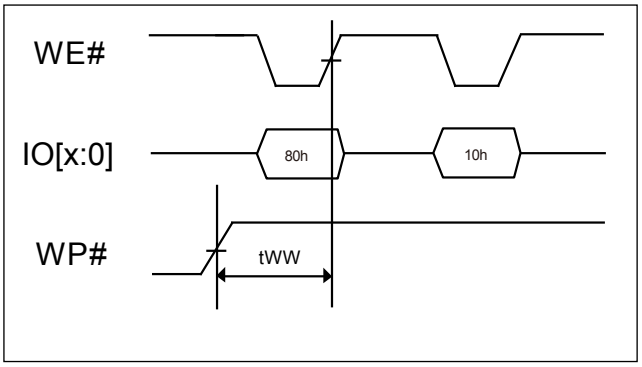


Figure 46-2. Disable Programming of WP# Signal

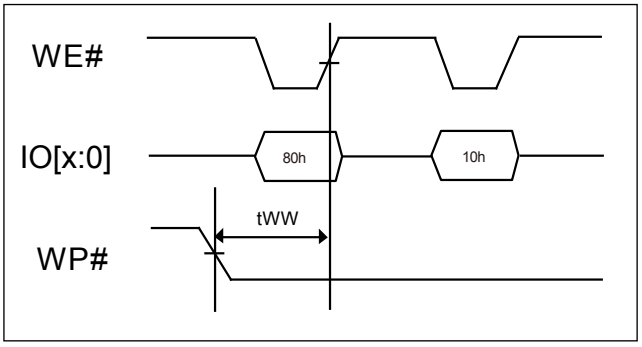


Figure 46-3. Enable Erasing of WP# Signal

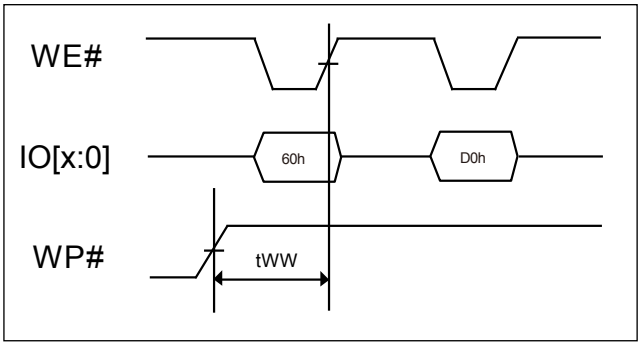
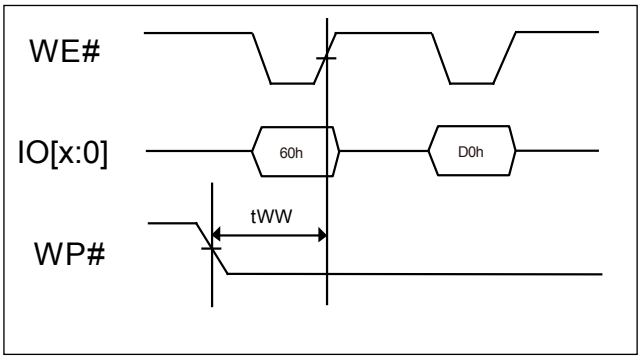


Figure 46-4. Disable Erasing of WP# Signal

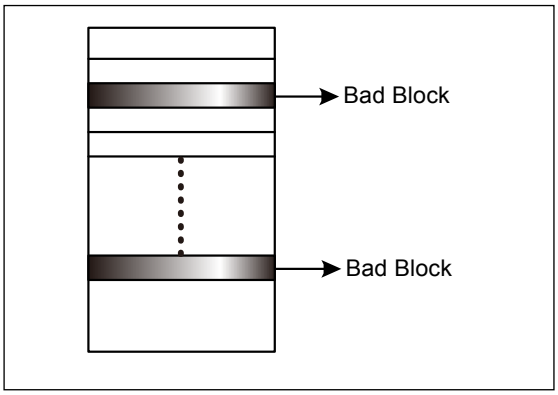


9. SOFTWARE ALGORITHM

9-1. Invalid Blocks (Bad Blocks)

The bad blocks are included in the device while it gets shipped. During the time of using the device, the additional bad blocks might be increasing; therefore, it is recommended to check the bad block marks and avoid using the bad blocks. Furthermore, please read out the bad block information before any erase operation since it may be cleared by any erase operation.

Figure 47. Bad Blocks



While the device is shipped, the value of all data bytes of the good blocks are FFh. The 1st byte of the 1st and 2nd page in the spare area for bad block will be 00h for x8; and 0000h for x16. The erase operation at the bad blocks is not recommended.

After the device is installed in the system, the bad block checking is recommended. The figure shows the brief test flow by the system software managing the bad blocks while the bad blocks were found. When a block gets damaged, it should not be used any more.

Due to the blocks are isolated from bit-line by the selected gate, the performance of good blocks will not be impacted by bad ones.

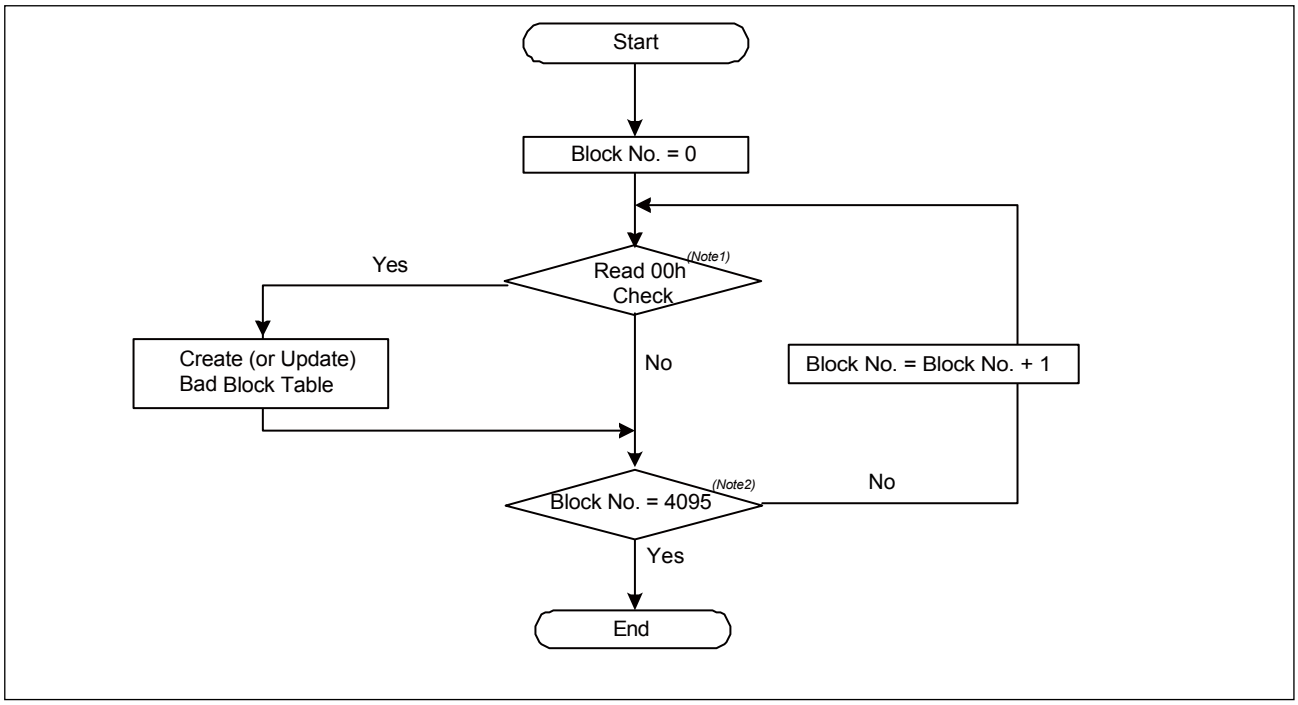
Table 17. Valid Blocks

	Density	Min.	Typ.	Max.	Unit	Remark
Valid (Good) Block Number	2Gb	2008		2048	Block	Block 0 is guaranteed to be good.
	4Gb	4016		4096	Block	

9-2. Bad Block Test Flow

Although the initial bad blocks are marked by the flash vendor, they could be inadvertently erased and destroyed by a user that does not pay attention to them. To prevent this from occurring, it is necessary to always know where any bad blocks are located. Continually checking for bad block markers during normal use would be very time consuming, so it is highly recommended to initially locate all bad blocks and build a bad block table and reference it during normal NAND flash use. This will prevent having the initial bad block markers erased by an unexpected program or erase operation. Failure to keep track of bad blocks can be fatal for the application. For example, if boot code is programmed into a bad block, a boot up failure may occur. The following section shows the recommended flow for creating a bad block table.

Figure 48. Bad Block Test Flow



Notes *1. Read 00h check is at the 1st bytes of the 1st and 2nd pages of the block spare area.*

2. The block No. = 2047 for 2Gb, 4095 for 4Gb

9-3. Failure Phenomena for Read/Program/Erase Operations

The device may fail during a Read, Program or Erase operation. The following possible failure modes should be considered when implementing a highly reliable system:

Table 18. Failure Modes

Failure Mode	Detection and Countermeasure	Sequence
Erase Failure	Status Read after Erase	Block Replacement
Programming Failure	Status Read after Program	Block Replacement
Read Failure	Read Failure	ECC

9-4. Program

It is feasible to reprogram the data into another page (Page B) when an error occurred in Page A by loading from an external buffer. Then create a bad block table or by using another appropriate scheme to prevent further system accesses to Page A.

Figure 49. Failure Modes

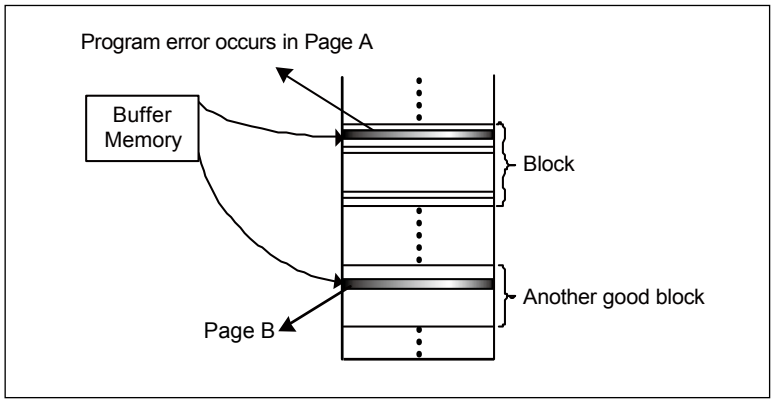
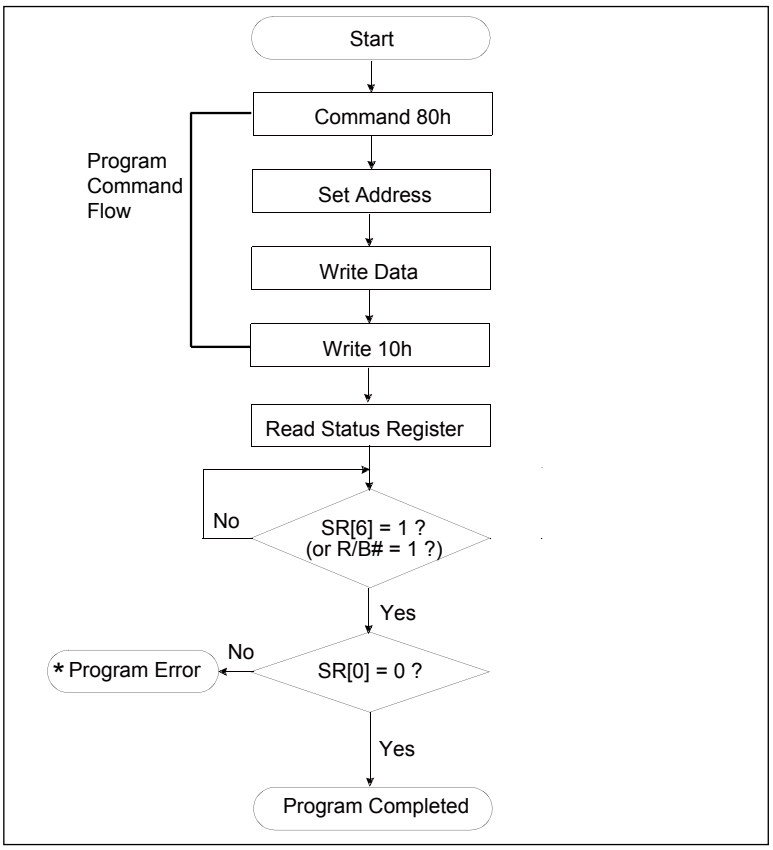


Figure 50. Program Flow Chart



9-5. Erase

To prevent future accesses to this bad block, it is feasible to create a table within the system or by using another appropriate scheme when an error occurs in an Erase operation.

Figure 51. Erase Flow Chart

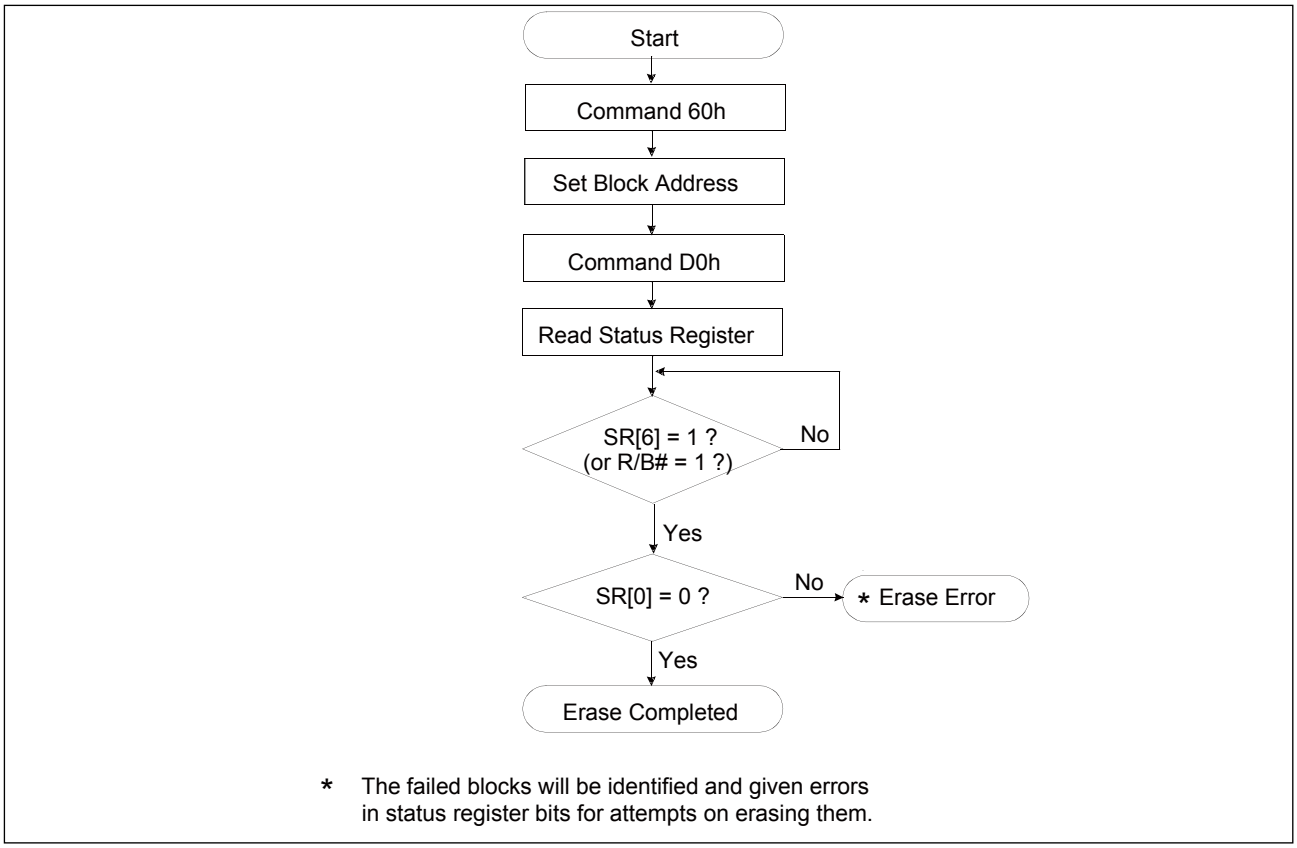
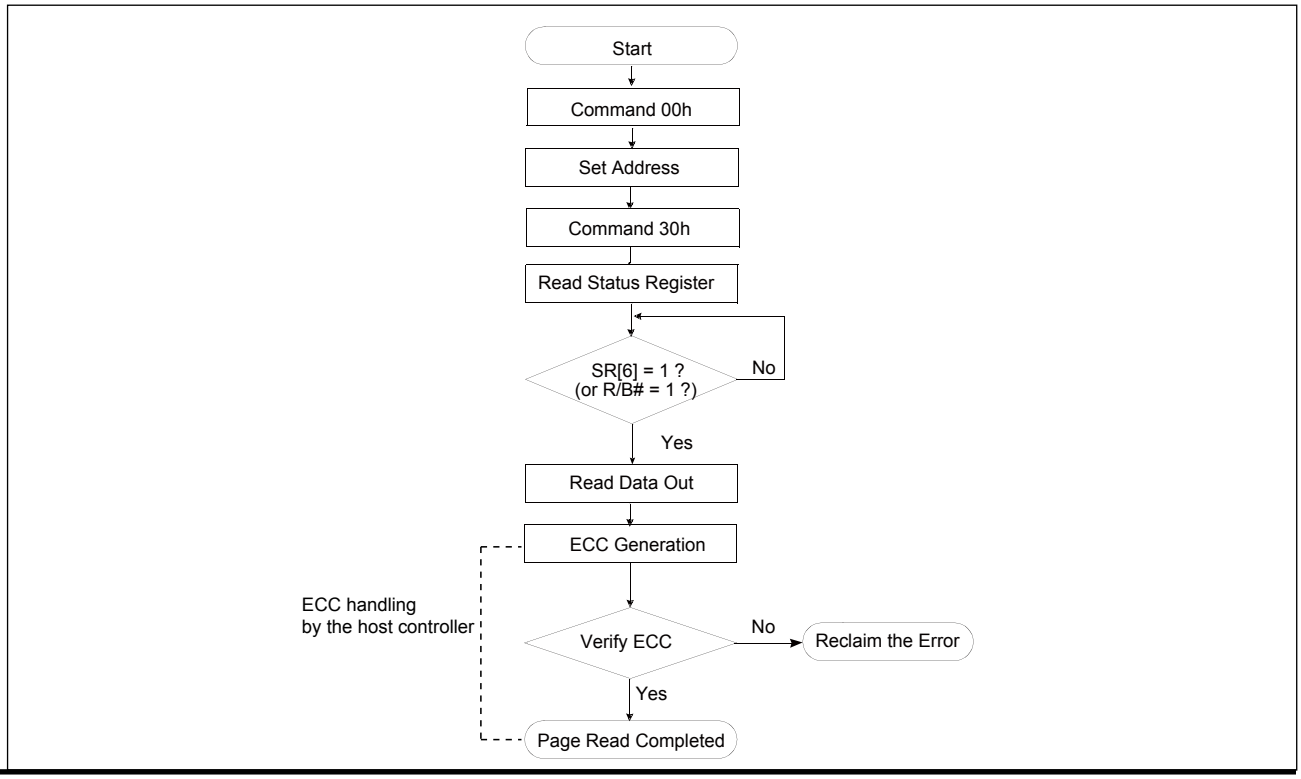
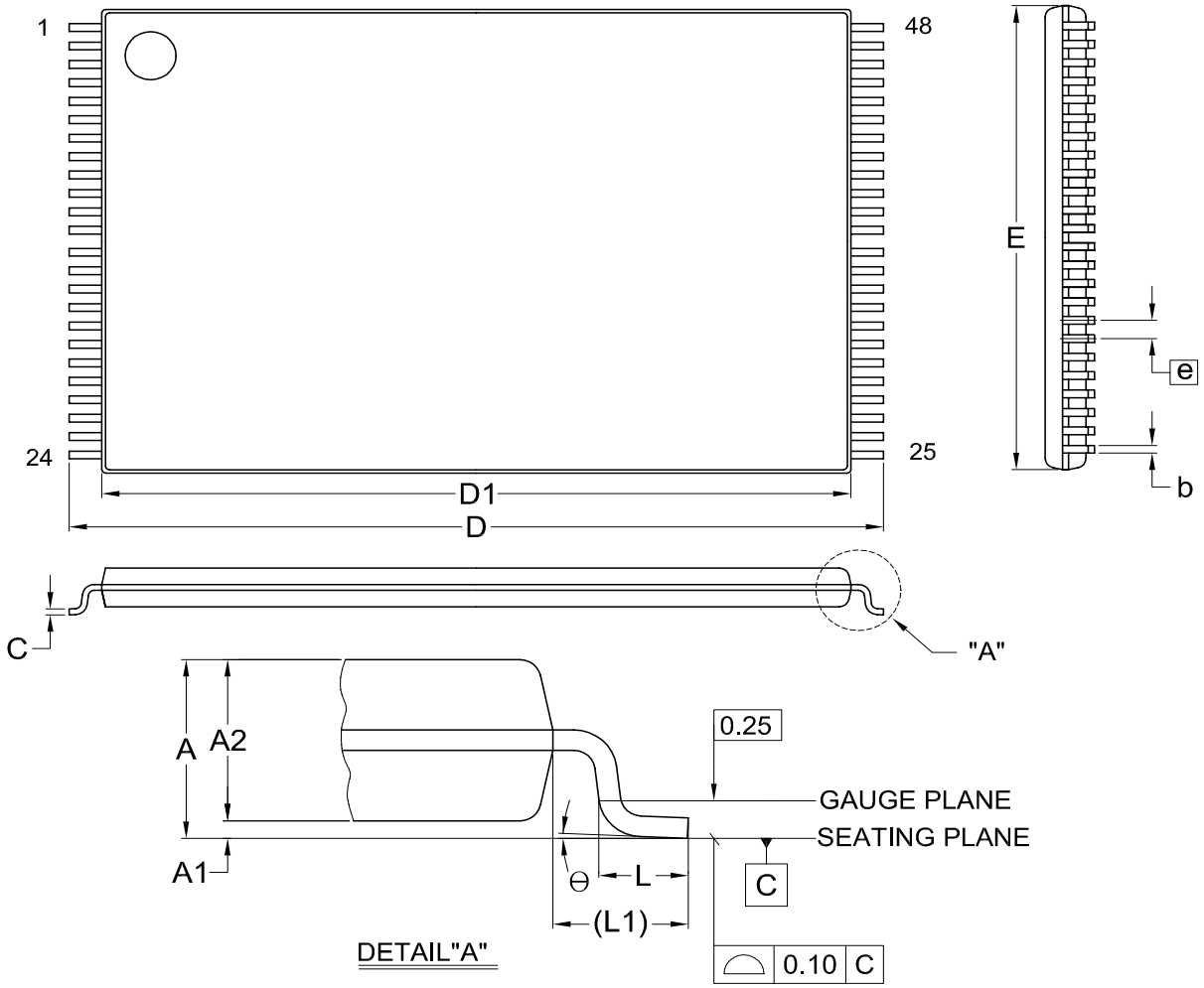


Figure 52. Read Flow Chart



10. PACKAGE INFORMATION

Title: Package Outline for TSOP(I) 48L (12X20mm)NORMAL FORM

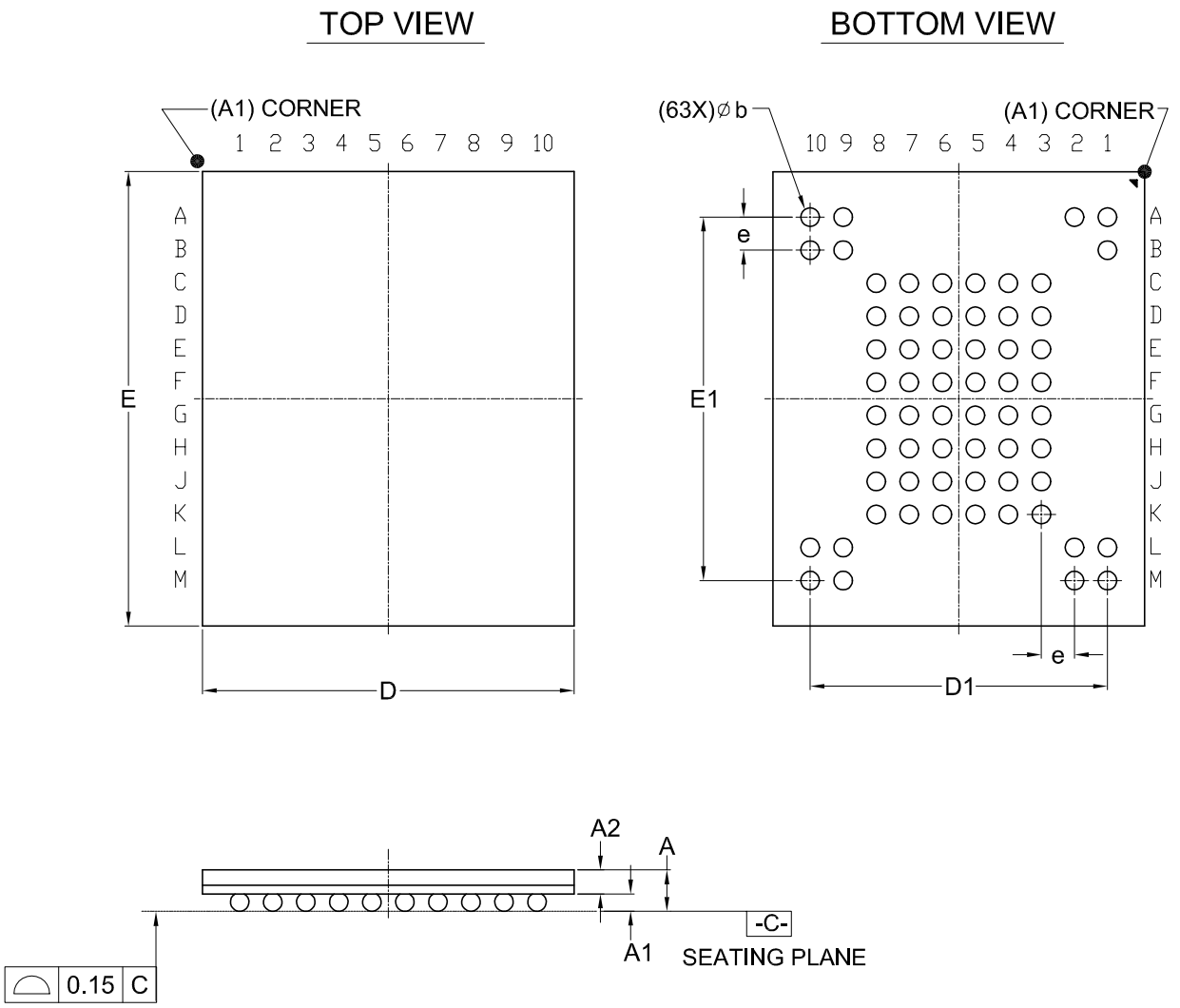


Dimensions (inch dimensions are derived from the original mm dimensions)

SYMBOL / UNIT		A	A1	A2	b	C	D	D1	E	e	L	L1	Θ
mm	Min.	—	0.05	0.95	0.17	0.10	19.80	18.30	11.90	—	0.50	0.70	0
	Nom.	---	0.10	1.00	0.20	0.13	20.00	18.40	12.00	0.50	0.60	0.80	5
	Max.	1.20	0.15	1.05	0.27	0.21	20.20	18.50	12.10	—	0.70	0.90	8
Inch	Min.	---	0.002	0.037	0.007	0.004	0.780	0.720	0.469	—	0.020	0.028	0
	Nom.	---	0.004	0.039	0.008	0.005	0.787	0.724	0.472	0.020	0.024	0.031	5
	Max.	0.047	0.006	0.041	0.011	0.008	0.795	0.728	0.476	—	0.028	0.035	8

DWG.NO.	REVISION	REFERENCE			ISSUE DATE
		JEDEC	EIAJ		
6110-1607	8	MO-142			2007/08/03

Title: Package Outline for 63-VFBGA (9x11x1.0mm, Ball-pitch: 0.8mm, Ball-diameter: 0.45mm)



Dimensions (inch dimensions are derived from the original mm dimensions)

SYMBOL / UNIT		A	A1	A2	b	D	D1	E	E1	e
mm	Min.	---	0.25	0.55	0.40	8.90	---	10.90	—	—
	Nom.	---	0.30	—	0.45	9.00	7.20	11.00	8.80	0.80
	Max.	1.00	0.40	—	0.50	9.10	---	11.10	—	—
Inch	Min.	—	0.010	0.022	0.016	0.350	---	0.429	—	—
	Nom.	—	0.012	—	0.018	0.354	0.283	0.433	0.346	0.031
	Max.	0.039	0.016	—	0.020	0.358	---	0.437	—	—

Dwg. No.	Revision	Reference			
		JEDEC	EIAJ		
6110-4267	0				

11. REVISION HISTORY

Rev. No.	Descriptions	Page	Date
0.01	1. Modified Bus to x8 and x16 in Feature page.	P6	MAY/21/2014
	2. Updated descriptions for Sec. 6-5. Page Program	P28	
	3. Added Notes for Vendor Blocks	P46	
	4. Modified AC waveforms for Fig. 32. OTP Protection	P57	
	5. Modified AC waveforms for Fig 34 .Two-plane Cache Program	P61	
	6. Updated Table 10. DC Table for VOL & VOH values.	P69	
	7. Updated Table 13. Program and Erase Characteristics Table	P70	
	8. Revised descriptions for Sec. 9-1. Invalid blocks.	P78	
	9. Updated descriptions for Sec. 9-2. Bad Block Test Flow	P79	
	10. Removed "Advanced Information" from Title .	P6	
	11. Added one part number: MX30UF2G28AB-TI	P9	
	12. Content Modifications	P7,14, 45, 62	
	13. Specifications improvement for the folllowing parameters: tPROG, tRCBSY, tERASE, VOH, VOL, ICC1, ICC2, ICC3, tRHW,	P6, 69, 70, 71	
1.0	1. Specifications improvement for the folllowing parameters: tPROG, tBERS and tRHZ.	P45, 71	MAY/29/2014
	2. Updated AC waveforms and added a note for Fig. 32. OTP Protection Operation.	P57	
	3. Added a note for AC waveforms for Sequence of Cache Program	P33	
1.1	1. Added a product statement for Ordering Information	P9	FEB/08/2017
	2. Added Figure 36. Block Protection Flow Chart	P63	
	3. Revised the bad block mark from non-FFh to 00h, and non-FFFFh to 0000h; also revised the page of bad block mark from 1st or 2nd page to 1st and 2nd page	P79/80	
	4. Aligned the term of "plane 1" & "plane 2" as "plane 0" & "plane 1"	P61	
	5. Added overshoot/undershoot waveforms	P69	
	6. Added the tRST=5us for the device reset time from idle	P72	
	7. Modifications of the power-on/off sequence: supplement the CE# signal, supplement the WE# single waveform with WE#=0 without toggle during the power-on period.	P77	

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